

Advances in atomic force microscopy

Franz J. Giessibl*

*Experimentalphysik VI, Electronic Correlations and Magnetism, Institute of Physics,
Augsburg University, 86135 Augsburg, Germany*

(Dated: September 23 2002, revised version February 17 2003, accepted for publication in
Reviews of Modern Physics)

Abstract

This article reviews the progress of atomic force microscopy (AFM) in ultra-high vacuum, starting with its invention and covering most of the recent developments. Today, dynamic force microscopy allows to image surfaces of conductors *and* insulators in vacuum with atomic resolution. The mostly used technique for atomic resolution AFM in vacuum is frequency modulation AFM (FM-AFM). This technique, as well as other dynamic AFM methods, are explained in detail in this article. In the last few years many groups have expanded the empirical knowledge and deepened the theoretical understanding of FM-AFM. Consequently, the spatial resolution and ease of use have been increased dramatically. Vacuum AFM opens up new classes of experiments, ranging from imaging of insulators with true atomic resolution to the measurement of forces between individual atoms.

*Electronic address: Franz.Giessibl@physik.uni-augsburg.de

Contents

I. INTRODUCTION	4
II. ATOMIC FORCE MICROSCOPY (AFM) PRINCIPLE	6
A. Relation to scanning tunneling microscopy (STM)	6
1. Tunneling current in STM	7
2. Experimental measurement and noise	7
B. Tip-sample forces F_{ts}	9
C. The force sensor (cantilever)	13
1. Cantilever tips	15
2. Measurement of cantilever deflection and noise	16
3. Thermal stability	17
D. Operating Modes of AFMs	18
1. Static AFM	18
2. Dynamic AFM	19
III. CHALLENGES FACED BY AFM WITH RESPECT TO STM	20
A. Stability	20
B. Non-monotonic imaging signal	21
C. Contribution of long-range forces	22
D. Noise in the imaging signal	22
IV. EARLY AFM EXPERIMENTS	23
V. THE RUSH FOR SILICON	26
VI. FREQUENCY MODULATION AFM (FM-AFM)	27
A. Experimental setup	27
B. Experimental parameters	29
VII. PHYSICAL OBSERVABLES IN FM-AFM	31
A. Frequency shift and conservative forces	31
1. Generic calculation	31

2. An intuitive expression for frequency shifts as a function of amplitude	33
3. Frequency shift for a typical tip-sample force	33
4. Deconvolution of forces from frequency shifts	35
B. Average tunneling current for oscillating tips	36
C. Damping and dissipative forces	37
VIII. NOISE IN FREQUENCY MODULATION AFM	39
A. Generic calculation	39
B. Noise in the frequency measurement	39
C. Optimal amplitude for minimal vertical noise	41
IX. APPLICATIONS OF CLASSIC FREQUENCY MODULATION AFM	42
A. Imaging	42
B. Spectroscopy	43
X. NEW DEVELOPMENTS	43
A. Dissipation measurements and theory	43
B. Off-resonance technique with small amplitudes	44
C. Dynamic mode with stiff cantilevers and small amplitudes	45
D. Dynamic lateral force microscopy	46
XI. SUMMARY AND CONCLUSIONS	47
XII. OUTLOOK	48
ACKNOWLEDGMENTS	49
References	49
Figures	65
Tables	85

I. INTRODUCTION

Imaging individual atoms has been elusive until the introduction of the Scanning Tunneling Microscope (STM) in 1981 by Binnig, Rohrer, Gerber, and Weibel (1982). This humble instrument has provided a breakthrough in our possibilities to investigate matter on the atomic scale: for the first time, the individual surface atoms of flat samples could be made visible in real space. Within one year of its invention, the STM has helped to solve one of the most intriguing problems in surface science: the structure of the Si(111)-(7×7) surface. The adatom layer of Si(111)-(7×7) was imaged with an STM by Binnig *et al.* (1983). This image, combined with X-ray- and electron-scattering data has helped Takayanagi, Tanishiro, Takahashi, and Takahashi (1985) to develop the Dimer-Adatom-Stacking fault (DAS)-model for Si(111)-(7×7). G. Binnig and H. Rohrer, the inventors of the STM were rewarded with the Nobel Prize in Physics in 1986. The historic events about the initial steps and the rapid success of the STM including the resolution of the silicon 7×7 reconstruction have been presented in the Nobel Prize lecture of Binnig and Rohrer (1987). The spectacular spatial resolution of the STM along with its intriguing simplicity has launched a sprawling research community with a significant impact on surface science (Mody, 2002). A large number of metals and semiconductors have been investigated on the atomic scale and marvelous images of the world of atoms have been created within the first few years after the inception of the STM. Today, the STM is an invaluable asset in the surface scientist's toolbox.

Despite the phenomenal success of the STM, it has a serious limitation. The STM requires electrical conduction of the sample material, because the STM uses the tunneling current which flows between a biased tip close to a sample. However, early STM experiments have shown that whenever the tip-sample distance is small enough that a current can flow, significant forces will act collaterally to the tunneling current. Soon it was speculated, that these forces could be put to good use in the atomic force microscope (AFM). The force microscope was invented by Binnig (1986) and shortly after its invention, Binnig, Quate, and Gerber (1986) introduced a working prototype while Binnig and Gerber spent a sabbatical at Stanford and the IBM Research Laboratory in Almaden, California. Binnig *et al.* (1986) were aware that even in STM operation, significant forces between single atoms are acting, and were confident that the AFM could ultimately achieve true atomic resolution, see Figure

1, adapted from Binnig *et al.* (1986). The STM can only image electrically conductive samples which limits its application to imaging metals and semiconductors. But even conductors – except for a few special materials, like highly oriented pyrolytic graphite (HOPG) – cannot be studied in ambient conditions by STM but have to be investigated in an ultra-high vacuum (UHV). In ambient conditions, the surface layer of solids constantly changes by adsorption and desorption of atoms and molecules. UHV is required for clean and well defined surfaces. Because electrical conductivity of the sample is not required in AFM, the AFM can image virtually any flat solid surface without the need for surface preparation. Consequently, thousands of AFMs are in use in universities, public and industrial research laboratories all over the world. The most of these instruments are operated in ambient conditions.

For studying surfaces on the atomic level, an ultra-high vacuum environment is required, where it is more difficult to operate an AFM. In addition to the experimental challenges of STM, the AFM faces four more substantial experimental complications which are summarized in section III. While Binnig, Quate, and Gerber (1986) have anticipated true atomic resolution capability of the AFM from the beginning, it has taken five years before atomic resolution on inert surfaces could be demonstrated (Giessibl, 1991; Giessibl and Binnig, 1992b; Ohnesorge and Binnig, 1993), see IV. Resolving reactive surfaces by AFM with atomic resolution took almost a decade from the invention of the AFM. The Si(111)-(7×7) surface, a touchstone of the AFMs feasibility as a tool for surface science, was resolved with atomic resolution by dynamic AFM (Giessibl, 1995). The new AFM mode has proven to work as a standard method, and in 1997 Seizo Morita from Osaka University in Japan initiated an international workshop about ‘non-contact AFM’. A year later, the “First International Workshop on Non-contact Atomic Force Microscopy (NC-AFM)” was held in Osaka, Japan with about 80 attendants. This meeting was followed in 1999 by the Pontresina (Switzerland) meeting with roughly 120 participants and the “Third International Conference on Non-contact Atomic Force Microscopy (NC-AFM)” in Hamburg, Germany in 2000 with more than 200 participants. The fourth meeting took place in September 2001 in Kyoto, Japan, and the 2002 conference met at McGill University in Montreal, Canada. The next meeting is scheduled for Ireland in Summer 2003. The proceedings for these workshops and conferences (Bennewitz *et al.*, 2000; Hoffmann, 2003; Morita and Tsukada, 1999; Schwarz *et al.*, 2001; Tsukada and Morita, 2002) and a recent review by Garcia and Perez (2002) are a rich

source of information for AFM and its role in surface science. Also, a multi-author book about NCAFM has recently become available (Morita *et al.*, 2002). The introduction of this book (Morita, 2002) covers interesting aspects of the history of the AFM. This review can only cover a part of the field, and the author must apologize to the colleagues whose work he was not able to treat in the depth it deserved in this review. However, many of these publications are listed in the bibliography and references therein.

II. ATOMIC FORCE MICROSCOPY (AFM) PRINCIPLE

A. Relation to scanning tunneling microscopy (STM)

The AFM is closely related to the STM, and it shares its key components, except for the probe tip. The principle of STM is explained very well in many excellent books and review articles, e.g. Binnig and Rohrer (1985, 1987, 1999); Chen (1993); Güntherodt and Wiesendanger (1991); Stroscio and Kaiser (1994); Wiesendanger (1994) and Wiesendanger (1998). Nevertheless, the key principle of STM is described here because the the additional challenges faced by AFM become apparent clearly in a direct comparison. Figure 2 shows the general setup of a scanning tunneling microscope (STM): a sharp tip is mounted on a scanning device (“xyz scanner”) which allows 3-dimensional positioning in x, y and z with subatomic precision. The tunneling tip is typically a wire that has been sharpened by chemical etching or mechanical grinding. W, Pt-Ir or pure Ir are often chosen as a tip material. A bias voltage V_t is applied to the sample and when the distance between tip and sample is in the range of several Ångströms, a tunneling current I_t flows between the tip and sample. This current is used as the feedback signal in a z -feedback loop.

In the “topographic mode”, images are created by scanning the tip in the xy -plane and recording the z -position required to keep I_t constant. In the “constant height mode”, the probe is scanned rapidly such that the feedback cannot follow the atomic corrugations. The atoms are then apparent as modulations of I_t which are recorded as a function of x and y . The scanning is usually performed in a raster fashion with a fast scanning direction (sawtooth or sinusoidal signal) and a slow scanning direction (sawtooth signal). A computer controls the scanning of the surface in the xy plane while recording the z -position of the tip (topographic mode) or I_t (constant height mode). Thus, a three dimensional image

$z(x, y, I_t \approx \text{const.})$ or $I_t(x, y, z \approx \text{const.})$ is created.

In the AFM, the tunneling tip is replaced by a force-sensing cantilever. The tunneling tip can also be replaced by an optical near-field probe, a microthermometer etc., giving rise to a whole family of scanning probe microscopes, see Wickramasinghe (1989).

1. Tunneling current in STM

In an STM, a sharp tip is brought close to an electrically conductive surface that is biased at a voltage V_t . When the separation is small enough, a current I_t flows between them. The typical distance between tip and sample under these conditions is a few atomic diameters, and the transport of electrons occurs by tunneling. When $|V_t|$ is small compared to the workfunction Φ , the tunneling barrier is roughly rectangular (see Fig. 3) with a width z and a height given by the workfunction Φ . According to elementary quantum mechanics, the tunneling current is given by:

$$I_t(z) = I_0 e^{-2\kappa_t z}. \quad (1)$$

I_0 is a function of the applied voltage and the density of states in both tip and sample and

$$\kappa_t = \sqrt{2m\Phi}/\hbar \quad (2)$$

where m is the mass of the electron and $\hbar$ is Planck's constant. For metals, $\Phi \approx 4 \text{ eV}$, thus $\kappa_t \approx 1 \text{ \AA}^{-1}$. When z is increased by one Ångström, the current drops by an order of magnitude. This strong distance dependence is pivotal for the atomic resolution capability of the STM. Most of the tunneling current is carried by the atom that is closest to the sample ("front atom"). If the sample is very flat, this front atom remains the atom that is closest to the sample during scanning in x and y and even relatively blunt tips yield atomic resolution easily.

2. Experimental measurement and noise

The tunneling current is measured with a current-to-voltage converter (see Fig. 4), a simple form of it consists merely of a single operational amplifier (OPA) with low noise and low input bias current, and a feedback resistor with a typical impedance of $R = 100 \text{ M}\Omega$

and small parasitic capacitance. The tunneling current I_t is used to measure the distance between tip and sample. The noise in the imaging signal (tunneling current in STM, force or some derived quantity in AFM) needs to be small enough such that the corresponding vertical noise δz is considerably smaller than the atomic corrugation of the sample. In the following, the noise levels for imaging signals and vertical positions are described by the root-mean-square (rms) deviation of the mean value and indicated by the prefix δ , i.e.

$$\delta\xi \equiv \sqrt{\langle (\xi - \langle \xi \rangle)^2 \rangle}. \quad (3)$$

To achieve atomic resolution with an STM or AFM, a first necessary condition is that the mechanical vibrations between tip and sample are smaller than the atomic corrugations. This condition is met by a microscope design emphasizing utmost stability and establishing proper vibration isolation, as described in Refs. Chen (1993); Kuk and Silverman (1988); Park and Barrett (1993). In the following, proper mechanical design and vibration isolation will be presumed and are not discussed further. The inherent vertical noise in an STM is connected to the noise in the current measurement. Figure 5 shows the qualitative dependence of the tunneling current I_t as a function of vertical distance z . Because the measurement of I_t is subject to noise, the vertical distance measurement is also subject to a noise level δz :

$$\delta z_{I_t} = \frac{\delta I_t}{\left| \frac{\partial I_t}{\partial z} \right|}. \quad (4)$$

It is shown below, that the noise in the current measurement δI_t is small and that $\frac{\partial I_t}{\partial z}$ is quite large, consequently the vertical noise in STM is very small.

The dominating noise source in the tunneling current is the Johnson noise of both the feedback resistor R in the current amplifier, the Johnson noise in the tunneling junction, and the input noise of the operational amplifier. The Johnson noise density of a resistor R at temperature T is given by :

$$n_R = \sqrt{4k_B T R} \quad (5)$$

(Horowitz and Hill, 1989, 2nd ed.) where k_B is the Boltzmann constant. In typical STMs, the tunneling current is of the order of $I_t \approx 100$ pA and measured with an acquisition bandwidth of $B \approx 1$ kHz, where B is roughly determined by the spatial frequency of features that are to be scanned times the scanning speed. Thus, for a spatial frequency of 4 Atoms per nm and a scanning speed of 250 nm/s, a bandwidth of $B = 1$ kHz is sufficient to map

each atom as a single sinusoidal wave. With a gain of $V/I = R = 100 \text{ M}\Omega$ and $T = 300 \text{ K}$, the rms voltage noise is $n_i\sqrt{B} = \sqrt{4k_BTRB} = 40\mu\text{V}$ at room temperature, corresponding to a current noise of $\delta I_t = 0.4 \text{ pA}$. With Eqs. 1 and 4, the vertical noise is

$$\delta z_{I_t} \approx \frac{\sqrt{4k_BTB/R}}{2\kappa_t|I_t|} \quad (6)$$

which amounts to a z -noise of 0.2 pm in the present example. Thus, in STM the thermal noise in the tunneling current is not critical, because it is much smaller than the required resolution. It is interesting to note that the noise in STM increases proportional to the square root of the required bandwidth B , a moderate rate compared to the $B^{1.5}$ dependence which holds for frequency modulation AFM (see Eq. 53).

The spectacular spatial resolution and relative ease of obtaining atomic resolution by STM rests on three properties of the tunneling current:

- As a consequence of the strong distance dependence of the tunneling current, even with a relatively blunt tip the chance is high that a single atom protrudes far enough out of the tip such that it carries the main part of the tunneling current;
- Typical tunneling currents are in the nano-ampere range - measuring currents of this magnitude can be done with a very good signal to noise ratio even with a simple experimental setup;
- Because the tunneling current is a monotonic function of the tip-sample distance, it is easy to establish a feedback loop which controls the distance such that the current is constant.

It is shown in the next section that none of these conditions is met in the case of the AFM and therefore, substantial hurdles had to be overcome before atomic resolution by AFM became possible.

B. Tip-sample forces F_{ts}

The AFM is similar to an STM, except that the tunneling tip is replaced by a force sensor. Figure 6 shows a sharp tip close to a sample. The potential energy between the tip and sample V_{ts} causes a z component of the tip-sample force $F_{ts} = -\frac{\partial V_{ts}}{\partial z}$ and a “tip-sample

spring constant" $k_{ts} = -\frac{\partial F_{ts}}{\partial z}$. Depending on the mode of operation, the AFM uses F_{ts} or some entity derived from F_{ts} as the imaging signal.

Unlike the tunneling current, which has a very short range, F_{ts} has long- and short-range contributions. We can classify the contributions by their range and strength. In vacuum, there are short range chemical forces (fractions of nm) and van-der-Waals, electrostatic and magnetic forces with a long range (up to 100 nm). In ambient conditions, also meniscus forces formed by adhesion layers on tip and sample (water or hydrocarbons) can be present.

A prototype of the chemical bond is treated in many textbooks on quantum mechanics (see e.g. Baym (1969)): the H_2^+ - ion as a model for the covalent bond. This quantum mechanical problem can be solved analytically and gains interesting insights into the character of chemical bonds. The Morse Potential (see e.g. Israelachvili (1991))

$$V_{Morse} = -E_{bond}(2e^{-\kappa(z-\sigma)} - e^{-2\kappa(z-\sigma)}) \quad (7)$$

describes a chemical bond with bonding energy E_{bond} , equilibrium distance σ and a decay length κ . With a proper choice of E_{bond} , σ and κ , the Morse potential is an excellent fit for the exact solution of the H_2^+ - problem.

The Lennard-Jones potential (see e.g. Ashcroft and Mermin (1981); Israelachvili (1991)):

$$V_{Lennard-Jones} = -E_{bond}\left(2\frac{z^6}{\sigma^6} - \frac{z^{12}}{\sigma^{12}}\right) \quad (8)$$

has an attractive term $\propto r^{-6}$ originating from the van-der-Waals interaction (see below) and a repulsive term $\propto r^{-12}$.

While the Morse potential can be used for a qualitative description of chemical forces, it lacks an important property of chemical bonds: anisotropy. Chemical bonds, especially covalent bonds show an inherent angular dependence of the bonding strength, see Coulson and McWeeny (1991); Pauling (1957). Empirical models which take the directionality of covalent bonds into account are the Stillinger-Weber potential (Stillinger and Weber, 1985), the Tersoff potential and others. For a review see Bazant and Kaxiras (1997) and references therein. The Stillinger-Weber potential appears to be a valid model for the interaction of silicon tips with silicon samples in AFM: *“Although the various terms [of the Stillinger-Weber potential] lose their physical significance for distortions of the diamond lattice large enough to destroy sp^3 hybridization, the SW potential seems to give a reasonable description of many states experimentally relevant, such as point defects, certain*

surface structures, and the liquid and amorphous states” (Bazant and Kaxiras, 1997). Using the Stillinger-Weber potential, subatomic features in Si images have been explained (Giessibl *et al.*, 2000). Qualitatively, these findings have been reproduced with *ab initio* calculations (Huang *et al.*, 2003). The Stillinger-Weber potential necessarily contains nearest and next nearest neighbor interactions. Unlike solids with a face centered cubic or body centered cubic lattice structure, solids which crystallize in the diamond structure are unstable when only next-neighbour interactions are taken into account. The nearest neighbor contribution of the Stillinger-Weber potential is

$$V_n(r) = E_{bond}A \left[B\left(\frac{r}{\sigma'}\right)^{-p} - \left(\frac{r}{\sigma'}\right)^{-q} \right] e^{\frac{1}{r/\sigma'-a}} \text{ for } r < a\sigma', \text{ else } V_{nn}(r) = 0. \quad (9)$$

The next nearest neighbor contribution is:

$$V_{nn}(\mathbf{r}_i, \mathbf{r}_j, \mathbf{r}_k) = E_{bond} [h(r_{ij}, r_{ik}, \theta_{jik}) + h(r_{ji}, r_{jk}, \theta_{ijk}) + h(r_{ki}, r_{kj}, \theta_{ikj})] \quad (10)$$

with

$$h(r_{ij}, r_{ik}, \theta_{jik}) = \lambda e^{\gamma(\frac{1}{r_{ij}/\sigma'-a} + \frac{1}{r_{ik}/\sigma'-a})} (\cos \theta_{jik} + \frac{1}{3})^2 \text{ for } r_{ij,ik} < a\sigma', \text{ else } 0. \quad (11)$$

Stillinger and Weber found optimal agreement with experimental data for the following parameters:

$$\begin{aligned} A &= 7.049556277 & p &= 4 & \gamma &= 1.20 \\ B &= 0.6022245584 & q &= 0 & \lambda &= 21.0 \\ E_{bond} &= 3.4723 \text{ aJ} & a &= 1.8 & \sigma' &= 2.0951 \text{ \AA} \end{aligned}$$

The equilibrium distance σ is related to σ' by $\sigma = 2^{1/6}\sigma'$. The potential is constructed in such a way to ensure that V_n and V_{nn} and all their derivatives with respect to distance vanish for $r > a\sigma' = 3.7718 \text{ \AA}$. The diamond structure is favoured by the SW potential because of the factor $(\cos \theta + \frac{1}{3})^2$ – this factor is zero when θ equals the tetraeder bond angle of $\theta = 109.47^\circ$.

With increasing computer power, it becomes more and more feasible to perform *ab initio* calculations for tip-sample forces, see e.g. Huang *et al.* (2003); Ke *et al.* (2001); Perez *et al.* (1997, 1998); Tobik *et al.* (2001).

The van-der-Waals interaction is caused by fluctuations in the electric dipole moment of atoms and their mutual polarization. For two atoms at distance z , the energy varies as

$1/z^6$ (Baym (1969)). Assuming additivity and disregarding the discrete nature of matter by replacing the sum over individual atoms by an integration over a volume with a fixed number density of atoms, the van-der-Waals interaction between macroscopic bodies can be calculated (“Hamaker (1937) approach”). This approach does not account for retardation effects due to the finite speed of light and is therefore only appropriate for distances up to several hundred Ångströms. For a spherical tip with radius R next to a flat surface (z is the distance between the plane connecting the centers of the surface atoms and the center of the closest tip atom) the van-der-Waals potential is given by Israelachvili (1991):

$$V_{vdW} = -\frac{A_H R}{6z}. \quad (12)$$

The van-der-Waals force for spherical tips is thus proportional to $1/z^2$, while for pyramidal and conical tips, a $1/z$ -force law holds (Giessibl, 1997). The “Hamaker constant” A_H depends on the type of materials (atomic polarizability and density) of the tip and sample. For most solids and interactions across vacuum, A_H is of the order of 1 eV. For a list of A_H for various materials, see French (2000); Krupp (1967). The van-der-Waals interaction can be quite large – the typical radius of an etched metal tip is 100 nm and with $z = 0.5$ nm, the van-der-Waals energy is ≈ -30 eV, and the corresponding force is ≈ -10 nN. Because of their magnitude, van-der-Waals forces are a major disturbance in force microscopy. Ohnesorge and Binnig (1993) have shown (see section IV) that the large background vdW forces can be reduced dramatically by immersing the cantilever in water.

A more modern approach to the calculation of van-der-Waals forces is described in Hartmann (1991).

When the tip and sample are both conductive and have an electrostatic potential difference $U \neq 0$, electrostatic forces are important. For a spherical tip with radius R , the potential energy is given by Sarid (1994, 2nd ed.). If the distance between a flat surface and a spherical tip with radius R is small compared to R , the force is approximately given by (see Law and Rieutord (2002); Olsson, Lin, Yakimov, and Erlandsson (1998)):

$$F_{electrostatic}(z) = -\frac{\pi\epsilon_0 R U^2}{d} \quad (13)$$

Like the van-der-Waals interaction, the electrostatic interaction can also cause large forces – for a tip radius of 100 nm, $U = 1$ V and $z = 0.5$ nm, the electrostatic force is ≈ -5.5 nN.

It is interesting to note that short-range van-der-Waals forces (energy $\propto 1/z^6$) add up to long-range overall tip-sample forces because of their additivity. The opposite effect can occur

with electrostatic forces: in ionic crystals, where adjacent atoms carry opposite charges, the envelope of the electrostatic field has a short-range exponential distance dependence (Giessibl, 1992).

More information about tip-sample forces can be found in Abdurixit *et al.* (1999); Ciraci *et al.* (1990); Drakova (2001); Foster *et al.* (2002); Garcia and Perez (2002); Israelachvili (1991); Ke *et al.* (2001, 2002); Perez *et al.* (1997, 1998); Sarid (1994, 2nd ed.); Shluger *et al.* (1997, 1999); Tobik *et al.* (2001); Tsukada *et al.* (2002) and references therein.

C. The force sensor (cantilever)

Tip-sample forces can vary strongly on the atomic scale, and Pethica (1986) has proposed that they even explain artifacts like giant corrugations apparent in STM experiments. However, it is difficult to isolate force effects in STM, and a dedicated sensor for detecting forces is needed. The central element of a force microscope and the major instrumental difference to the scanning tunneling microscope is the spring which senses the force between tip and sample. For sensing normal tip-sample forces, the force sensor should be rigid in two axes and relatively soft in the third axis. This property is fulfilled with a cantilever beam (‘cantilever’), and therefore the cantilever geometry is typically used for force detectors. A generic cantilever is shown in Fig. 7. For a rectangular cantilever with dimensions w, t and L (see Fig. 7), the spring constant k is given by (Chen, 1993):

$$k = \frac{Ywt^3}{4L^3}. \quad (14)$$

where Y is Young’s modulus. The fundamental eigenfrequency f_0 is given by (Chen, 1993):

$$f_0 = 0.162 \frac{t}{L^2} \sqrt{\frac{Y}{\rho}} \quad (15)$$

where ρ is the mass density of the cantilever material.

The properties of interest are the stiffness k , the eigenfrequency f_0 , the quality factor Q , the variation of the eigenfrequency with temperature $\partial f_0 / \partial T$ and of course the chemical and structural composition of the tip. The first AFMs were mostly operated in the static contact mode (see below), and for this mode the stiffness of the cantilever should be less than the interatomic spring constants of atoms in a solid (Rugar and Hansma, 1990), which amounts to $k \leq 10 \text{ N/m}$. This constraint on k was assumed to hold for dynamic AFM as

well. It turned out later that in dynamic AFM, k -values exceeding hundreds of N/m help to reduce noise and increase stability (Giessibl *et al.*, 1999). The Q -factor depends on the damping mechanisms present in the cantilever. For micromachined cantilevers operated in air, Q is mainly limited by viscous drag and typically amounts to a few hundred while in vacuum, internal and surface effects in the cantilever material are responsible for damping and Q reaches hundreds of thousands.

The first cantilevers were made from a gold foil with a small diamond tip attached to it (Binnig, 1986). Simple cantilevers can even be cut from household aluminum foil (Rugar and Hansma, 1990) and etched tungsten wires (McClelland *et al.*, 1987). Later, silicon micromachining technology was employed to build cantilevers in parallel production with well defined mechanical properties. The first micromachined cantilevers were built at Stanford in the group of Calvin F. Quate. Initially, mass produced cantilevers were built from SiO_2 and Si_3N_4 (Albrecht *et al.*, 1990). Later, cantilevers with integrated tips were machined from silicon-on-insulator wafers (Akamine *et al.*, 1990). The most common cantilevers in use today are built from all-silicon with integrated tips pointing in a [001] crystal direction and go back to Wolter, Bayer, and Greschner (1991) at IBM Sindelfingen, Germany. Figures 8 and 9 show the type of cantilevers which are mainly used today: micromachined silicon cantilevers with integrated tips. Tortonese, Barrett, and Quate (1993) have built a self-sensing cantilevers with integrated tips and a built-in deflection measuring scheme utilizing the piezoresistive effect in silicon (see Fig. 10).

In dynamic AFM, some requirements for the force sensor are similar to the desired properties of the time keeping element in a watch: utmost frequency stability over time and temperature changes and little energy consumption. Around 1970, the watch industry was revolutionized with the introduction of quartz tuning forks as frequency standards in clocks (Momosaki, 1997; Walls, 1985). Billions of these devices are now manufactured annually, and the deviations of even low cost watches are no more than a few seconds a week. Experimental studies of using quartz based force sensors were done soon after the invention of the AFM. Güthner *et al.* (1989) and Güthner (1992) have used tuning forks as force sensors in acoustic near field microscopy and Karrai and Grober (1995) have used a tuning fork to control the distance between the optical near field probe and the surface in a scanning near-field-optical microscope. Bartzke *et al.* (1993) has proposed the 'needle sensor', a force sensor based on a quartz bar oscillator. Rychen *et al.* (1999) and Hembacher *et al.* (2002)

have demonstrated the use of quartz tuning forks at low temperature and other applications of quartz tuning forks as force sensors can be found in Edwards *et al.* (1997); Rensen *et al.* (1999); Ruiter *et al.* (1997); Todorovic and Schulz (1998); Tsai and Lu (1998); Wang (1998). Quartz tuning forks have many attractive properties, but their geometry is a decisive disadvantage for using them as force sensors. The great benefit of the fork geometry is the high Q -factor which is a consequence of the presence of an oscillation mode where both prongs oscillate opposite to each other. The dynamic forces necessary to keep the two prongs oscillating cancel in this case exactly. However, this only works if the eigenfrequency of both prongs matches precisely. The mass of the tip mounted on one prong and the interaction of this tip with a sample breaks the symmetry of tuning fork geometry. This problem can be avoided by fixing one of the two beams and turning the fork symmetry into a cantilever symmetry, where the cantilever is attached to a high-mass substrate with a low-loss material. Figure 11 shows a quartz cantilever based on a quartz tuning fork (Giessibl, 1996, 1998, 2000). Quartz tuning forks are available in several sizes. We found optimal performance with the type of tuning forks used in Swatch wristwatches. In contrast to micromachined silicon cantilevers, the quartz forks are large. Therefore, a wide selection of tips can be mounted onto a tuning fork with the mere help of tweezers and a stereoscopic microscope - sophisticated micromachining equipment is not needed. Tips made from tungsten, diamond, silicon, iron, cobalt, samarium, CoSm permanent magnets and iridium have been built in our laboratory for various purposes. Figure 12 shows a quartz cantilever oriented for lateral force detection (see section X.D) (Giessibl *et al.*, 2002). Piezoelectric sensors based on thin films of materials with much higher piezoelectric constants than quartz (Itoh *et al.*, 1996) are also available. However, these devices lack the very low internal dissipation and high frequency stability of quartz. The general advantage of piezoelectric sensors versus piezoresistive sensors is that the latter dissipate power in the mW range, while electric dissipation is negligible in piezoelectric sensors. Therefore, piezoelectric sensors are preferred over piezoresistive schemes for low temperature applications.

1. Cantilever tips

For atomic-resolution AFM, the front atom of the tip should ideally be the only atom which interacts strongly with the sample. In order to reduce the forces caused by the shaft

of the tip, the tip radius should be as small as possible, see section II.B. Cantilevers made of silicon with integrated tips are typically oriented such that the tip points in the $[001]$ crystal direction. Due to the anisotropic etching rates of Si and SiO_2 , these tips can be etched such that they develop a very sharp apex (Marcus *et al.*, 1990), as shown in Fig. 13. Recently, it has turned out that not only the sharpness of a tip is important for AFM, but also the coordination of the front atom. Tip and sample can be viewed as two giant molecules (Chen, 1993). In chemical reactions between two atoms or molecules, the chemical identity and the spatial arrangement of both partners plays a crucial role. For AFM with true atomic resolution, the chemical identity and bonding configuration of the front atom is therefore critical. In $[001]$ oriented silicon tips, the front atom exposes two dangling bonds (if bulk termination is assumed), and the front atom has only two connecting bonds to the rest of the tip. If we assume bulk termination, it is immediately evident that tips pointing in the $[111]$ direction are more stable, because then the front atom has *three* bonds to the rest of the tip, see Figs. 14. In a simple picture where only nearest-neighbor interactions are contributing significantly to the bonding energy, the front atom of a $[111]$ oriented silicon tip has $3/4$ of the bulk atomic bonding energy. For a $[111]$ oriented metal tip with fcc bulk structure, the bonding energy of the front atom has only $3/12$ of the bulk value. This trivial picture might explain, why silicon can be imaged with atomic resolution using positive frequency shifts (i.e. repulsive forces) with a $[111]$ silicon tip (to be discussed below). Even if the (111) sidewalls of these tips reconstruct to e.g. Si 7×7 , the front atom is fixed by three bonds and a very stable tip should emerge. Figure 15 shows a tip with $[111]$ orientation. The tip is cleaved from a silicon wafer. Experiments show, that these tips can come very close to a surface without getting damaged (Giessibl *et al.*, 2001b).

2. Measurement of cantilever deflection and noise

In the first AFM, the deflection of the cantilever was measured with an STM - the backside of the cantilever was metalized, and a tunneling tip was brought close to it to measure the deflection (Binnig *et al.*, 1986). While the tunneling effect is very sensitive to distance variations, this method has a number of drawbacks:

- It is difficult to position a tunneling tip such that it aligns with the very small area at the end of the cantilever.

- The tunneling tip exerts forces on the cantilever and it is impossible to distinguish between forces caused by cantilever-sample and cantilever-tunneling tip interactions.
- When the cantilever is deflected, the lateral position of the tip on the backside of the cantilever is shifted. The atomic roughness of the cantilever backside along with the lateral motion results in a nonlinear deflection signal.

Subsequent designs used optical (interferometer, beam-bounce) or electrical methods (piezoresistive, piezoelectric) for measuring the cantilever deflection. The deflection of silicon cantilevers is most commonly measured by optical detection through an interferometer or by bouncing a light beam off the cantilever and measuring its deflection (“beam bounce method”). For detailed descriptions of these techniques, see Sarid (1994, 2nd ed.), optical detection techniques are discussed extensively in Howald (1994). The deflection of piezoresistive cantilevers is usually measured by making them part of a Wheatstone bridge, see Tortonese *et al.* (1993).

The deflection of the cantilever is subject to thermal drift and other noise factors. This can be expressed in a plot of the deflection noise density versus frequency. A typical noise density is plotted in Fig. 16, showing a $1/f$ dependence for low frequency that merges into a constant noise density (“white noise”) above the “ $1/f$ corner frequency”. This $1/f$ noise is also apparent in macroscopic force sensing devices, such as scales. Typically, scales have a reset or zero button, which allows the user to reset the effects of long-term drift. Machining AFMs from materials with low thermal expansion coefficients like Invar or operation at low temperatures helps to minimize $1/f$ noise.

3. Thermal stability

A change in temperature can cause bending of the cantilever and a change in its eigenfrequency. In this respect, quartz is clearly superior to silicon as a cantilever material, as quartz can be cut along specific crystal orientations such that the variation of oscillation frequency of a tuning fork or cantilever is zero for a certain temperature T_0 . For quartz cut in the X+5° direction, $T_0 \approx 300$ K, see e.g. Momosaki (1997). This cannot be accomplished with silicon cantilevers. In the dynamic operating modes (see section VI), drifts in f_0 , caused by variations in temperature, add to the vertical noise. The eigenfrequency (see Eq. 27)

is determined by the spring constant and the effective mass of the cantilever. The spring constant changes with temperature, due to thermal expansion and the change of Young's modulus Y with temperature. Changes of the effective mass due to picking up a few atoms from the sample or transferring some atoms from the tip to the sample are insignificant, because a typical cantilever contains at least 10^{14} atoms. The resonance frequency of a cantilever is given in Eq. 15. With the velocity of sound in the cantilever material $v_s = \sqrt{Y/\rho}$, Eq. 15 can be expressed as (Chen, 1993):

$$f_0 = 0.162 v_s \frac{t}{L^2}. \quad (16)$$

The temperature dependence of the eigenfrequency is then given by

$$\frac{1}{f_0} \frac{\partial f_0}{\partial T} = \frac{1}{v_s} \frac{\partial v_s}{\partial T} - \alpha \quad (17)$$

where α is the thermal expansion coefficient. For silicon oriented along the [110]-crystal direction (see Fig. 7), $\frac{1}{v_s} \frac{\partial v_s}{\partial T} = -5.5 \times 10^{-5} K^{-1}$ and $\alpha = 2.55 \times 10^{-6} K^{-1}$ at $T = 290$ K (Kuchling, 1982; Landolt-Börnstein, 1982). The resulting relative frequency shift for (rectangular) silicon cantilevers is then $-5.8 \times 10^{-5} K^{-1}$. This is a large noise source in classical FM-AFM, where relative frequency shifts can be as small as $-6 \text{ Hz}/151 \text{ kHz} = -4 \times 10^{-5}$ (see row 5 in Table I) and a temperature variation of $\Delta T = +0.69$ K causes an equal shift in resonance frequency. The drift of f_0 with temperature is much smaller for cantilevers made of quartz. Figure 17 shows a comparison of typical frequency variations as a function of temperature for silicon and quartz. The data for silicon is calculated with Eq. 17, the quartz data is taken from Momosaki (1997). As can be seen, quartz is remarkably stable at room temperature compared to silicon. Less significant noise sources, like the thermal fluctuation of A , are discussed in Giessibl *et al.* (1999). Hembacher *et al.* (2002) have measured the frequency variations of a quartz tuning fork sensor from room temperature to 5 K.

D. Operating Modes of AFMs

1. Static AFM

In AFM, the force F_{ts} which acts between the tip and sample is used as the imaging signal. In the static mode of operation, the force translates into a deflection $q' = F_{ts}/k$ of the cantilever. Because the deflection of the cantilever should be significantly larger than

the deformation of the tip and sample, restrictions on the useful range of k apply. In the static mode, the cantilever should be much softer than the bonds between the bulk atoms in tip and sample. Interatomic force constants in solids are in a range from 10 N/m to about 100 N/m - in biological samples, they can be as small as 0.1 N/m. Thus, typical values for k in the static mode are 0.01 – 5 N/m. The eigenfrequency f_0 should be significantly higher than the desired detection bandwidth, i.e. if 10 lines per second are recorded during imaging a width of say 100 atoms, f_0 should be at least $10 \times 2 \times 100 \text{ s}^{-1} = 2 \text{ kHz}$ in order to prevent resonant excitation of the cantilever.

Even though it has been demonstrated that atomic resolution is possible with static AFM (Giessibl and Binnig, 1992b; Ohnesorge and Binnig, 1993; Schimmel *et al.*, 1999), the method can only be applied in certain cases. The magnitude of $1/f$ -noise can be reduced by low temperature operation (Giessibl (1992)), where the coefficients of thermal expansion are very small or by building the AFM of a material with a low thermal expansion coefficient. The long-range attractive forces have to be cancelled by immersing tip and sample in a liquid (Ohnesorge and Binnig (1993)) or by partly compensating the attractive force by pulling at the cantilever after jump-to-contact has occurred (Giessibl (1991, 1992); Giessibl and Binnig (1992b)). Jarvis *et al.* (1997, 1996) have introduced a method to cancel the long-range attractive force with an electromagnetic force applied to the cantilever.

While the experimental realization of static AFM is difficult, the physical interpretation of static AFM images is simple: The image is a map $z(x, y, F_{ts} = \text{const.})$.

2. Dynamic AFM

In the dynamic operation modes, the cantilever is deliberately vibrated. The cantilever is mounted onto an actuator to allow an external excitation of an oscillation. There are two basic methods of dynamic operation: amplitude modulation (AM) - and frequency modulation (FM) operation. In AM-AFM (Martin, Williams, and Wickramasinghe, 1987), the actuator is driven by a fixed amplitude A_{drive} at a fixed frequency f_{drive} where f_{drive} is close to but different from f_0 . When the tip approaches the sample, elastic and inelastic interactions cause a change in both the amplitude and the phase (relative to the driving signal) of the cantilever. These changes are used as the feedback signal. The change in amplitude in AM mode does not occur instantaneously with a change in the tip-sample interaction, but on

a timescale of $\tau_{AM} \approx 2Q/f_0$. With Q -factors reaching 100000 in vacuum, the AM mode is very slow. Albrecht, Grutter, Horne, and Rugar (1991) solved this problem by introducing the frequency modulation (FM) mode, where the change in the eigenfrequency occurs within a single oscillation cycle on a timescale of $\tau_{FM} \approx 1/f_0$.

Both AM and FM modes were initially meant to be “non-contact” modes, i.e. the cantilever was far away from the surface and the net force between the front atom of the tip and the sample was clearly attractive. The AM mode was later used very successfully at a closer distance range in ambient conditions involving repulsive tip-sample interactions (“Tapping Mode” Zhong *et al.* (1993)) and Erlandsson *et al.* (1997) obtained atomic resolution on Si in vacuum with an etched tungsten cantilever operated in AM mode in 1996. Using the FM mode in vacuum, the resolution was improved dramatically (Giessibl (1994); Giessibl and Trafas (1994)) and finally atomic resolution (Giessibl (1995)) was obtained. A detailed description of the FM-mode is given in section VI.

III. CHALLENGES FACED BY AFM WITH RESPECT TO STM

In a scanning tunneling microscope, a tip has to be scanned across a surface with a precision of pico-meters while a feedback mechanism adjusts the z - position such that the tunneling current is constant. This task seems daunting and the successful realization of STM is an amazing accomplishment. Yet, implementing an AFM capable of atomic resolution poses even more obstacles. Some of these challenges become apparent when comparing the characteristics of the physical observables used in the two types of microscopes. Figure 18 is a plot of tunneling current and tip sample force as a function of distance. For experimental measurements of force and tunneling current, see e.g. Schirmeisen *et al.* (2000). The tunneling current is a monotonic function of the tip-sample distance and increases sharply with decreasing distance. In contrast, the tip-sample force has long- and short-range components and is not monotonic.

A. Stability

Van-der-Waals forces in vacuum are always attractive, and if chemical bonding between tip and sample can occur the chemical forces are also attractive for distances greater than the

equilibrium distance. Because the tip is mounted on a spring, approaching the tip can cause a sudden “jump-to-contact” when the stiffness of the cantilever is smaller than a certain value.

This instability occurs in the quasistatic mode if

$$k < \max\left(-\frac{\partial^2 V_{ts}}{\partial z^2}\right) = k_{ts}^{\max} \quad (18)$$

(Burnham and Colton, 1989; McClelland *et al.*, 1987; Tabor and Winterton, 1969). The jump to contact can be avoided even for soft cantilevers by oscillating it at a large enough amplitude A :

$$kA > \max(-F_{ts}) = F_{ts}^{\max} \quad (19)$$

(Giessibl, 1997). If hysteresis occurs in the $F_{ts}(z)$ -relation, the energy ΔE_{ts} needs to be supplied to the cantilever for each oscillation cycle. If this energy loss is large compared to the intrinsic energy loss of the cantilever, amplitude control can become difficult (see the discussion after Eq. 47). An new conjecture regarding k and A is then

$$\frac{k}{2}A^2 \geq \Delta E_{ts} \frac{Q}{2\pi}. \quad (20)$$

The validity of these criteria is supported by an analysis of the values of k and A for many NC-AFM experiments with atomic resolution in table I.

Fulfilment of the stability criteria thus requires either the use of large amplitudes, cantilevers with large spring constants, or both. However, using large amplitudes has critical disadvantages, which are discussed in chapter VIII.

B. Non-monotonic imaging signal

The magnitude of the tunneling current increases continuously as the tip-sample distance decreases, i.e. the tunneling current is a strictly monotonic decreasing function of the distance (see Fig. 5 on page 66). This property allows a simple implementation of a feedback loop: the tunneling current is fed into a logarithmic amplifier to produce an error signal that is linear with the tip-sample distance.

In contrast, the tip-sample force is not monotonic. In general, the force is attractive for large distances and upon decreasing the distance between tip and sample, the force turns

repulsive (see Fig. 18). Stable feedback is only possible on a branch of the force curve, where it is monotonic.

Because the tunneling current is monotonic for the whole distance range and the tip-sample force is not monotonic, it is much easier to establish a z -distance feedback loop for STMs than for AFMs.

C. Contribution of long-range forces

The force between tip and sample is composed of many contributions: electrostatic-, magnetic-, van-der-Waals- and chemical forces in vacuum. In ambient conditions there are also meniscus forces. While electrostatic-, magnetic- and meniscus forces can be eliminated by equalizing the electrostatic potential between tip and sample, using nonmagnetic tips and vacuum operation, the van-der-Waals forces cannot be switched off. For imaging by AFM with atomic resolution, it is desirable to filter out the long-range force contributions and only measure the force components which vary at the atomic scale. In STM, the rapid decay of the tunneling current with distance naturally blocks contributions of tip atoms that are further distant to the sample, even for fairly blunt tips. In contrast, in *static* AFM, long- and short-range forces add up to the imaging signal. In *dynamic* AFM, attenuation of the long-range contributions is achieved by proper choice of the cantilever's oscillation amplitude A , see section VII.A.3.

D. Noise in the imaging signal

Forces can be measured by the deflection of a spring. However, measuring the deflection is not a trivial task and is subject to noise, especially at low frequencies ($1/f$ noise). In static AFM, the imaging signal is given by the dc deflection of the cantilever, which is subject to $1/f$ noise. In dynamic AFM, the low-frequency noise is discriminated if the eigenfrequency f_0 is larger than the $1/f$ corner frequency. With a bandpass filter with a center frequency around f_0 only the white noise density is integrated across the bandwidth B of the bandpass filter.

Frequency modulation AFM, described in detail in chapter VI, helps to overcome

three of these four challenges. The non-monotonic force vs. distance relation is a remaining complication for AFM.

IV. EARLY AFM EXPERIMENTS

The first description of the AFM by Binnig *et al.* (1986) already lists several possible ways to operate the microscope: contact and non-contact, static and dynamic modes. Initially, AFMs were mainly operated in the static contact mode. However, soon after the invention of the AFM, Dürig, Gimzewski, and Pohl (1986) have measured the forces acting during tunneling in STM in UHV with a dynamic technique. In these experiments, the interaction between a tungsten STM tip and a thin film of Ag condensed on a metal cantilever was studied. The thermally excited oscillation of the metal cantilever was observed in the spectrum of the tunneling current, and the force gradient between tip and sample caused a shift in the resonance frequency of the cantilever. In a later experiment, Dürig, Züger, and Pohl (1990) used Ir tips and an Ir sample. While variations of the force on atomic scale were not reported in these experiments, it was shown that both repulsive (W tip, Ag sample) and attractive forces (Ir tip, Ir sample) of the order of a few nN can act during STM operation.

G. Binnig, Ch. Gerber, and others started the IBM Physics Group at the Ludwig-Maximilian-Universität in Munich. The author joined this group in May 1988 and helped to build a low-temperature UHV AFM to probe the resolution limits of AFM. If atomic resolution was possible, we thought that the best bet would be to try it at low temperatures in order to minimize the detrimental effects of thermal noise. The microscope was fitted to a quite complex vacuum system which was designed by G. Binnig, Ch. Gerber and T. Heppell with colleagues (VG Special Systems Hastings, England). Because it was anticipated that the design of the instrument had to go through many iterations which involves the breaking of the vacuum, the vacuum system was designed in an effort to keep the bake-out time short and to allow rapid cooling to 4 K, see Giessibl, Gerber, and Binnig (1991). Our instrument could resolve atoms in STM mode on graphite at $T = 4$ K in 1989, but AFM operation with atomic resolution was not possible yet. As AFM test samples, we used ionic crystals and in particular alkali halides. Alkali halides can be viewed as consisting of hard spheres which are charged by plus/minus one elementary charge (Ashcroft and Mermin (1981)). These materials are easily prepared by cleaving in vacuum, where large (001) planes with fairly

low step densities develop.

In late 1989, E. Meyer *et al.* (1990b) has shown quasiautomic resolution on LiF(001) in ambient conditions. The AFM images were explained with the ‘contact-hard-spheres-model’ by Meyer *et al.* (1990a), which assumes that the front atom of the tip and the sample atoms are hard spheres. Also in 1990, G. Meyer and Amer (1990) published a paper about the successful imaging of NaCl in UHV at room temperature with quasiautomic resolution. Quasiautomic resolution means that the images reflect atomic periodicities, but no atomic defects. The images appear to arise from a tip which has several or possibly many atomic contacts (minitips) spaced by one or several surface lattice vectors. This hypothesis is supported by the common observation in contact AFM that the resolution appears to improve after the tip is scanned for a while. Wear can cause the tip to develop a set of minitips which are spaced by multiple sample surface lattice vectors, yielding a quasi-atomic resolution. This mechanism is not observed and not expected to occur in today’s non-contact AFM experiments.

In both contact- AFM experiments (E. Meyer *et al.* and G. Meyer *et al.*), only one type of ion was apparent in the force microscope images. In 1990, we improved our 4K UHV instrument by mounting the whole vacuum system on air legs and adding a vibration insulation stage directly at the microscope. The major experimental challenge was the detection of the cantilever deflection. Like in the first AFM by Binnig (1986), tunneling detection was used to measure the deflection of a micromachined ‘V’-shaped cantilever with a spring constant of $k = 0.37 \text{ N/m}$ after Albrecht *et al.* (1990). The cantilever was made from SiO_2 and plated with a thin gold film for electrical conductance. The tunneling tip had to be adjusted to an area of a few μm^2 before the microscope was inserted into the low temperature vacuum system. As it turned out later, successful tunneling between the platinum coated tungsten tip and the gold plated cantilever was only possible if the tip had drifted towards the fixed end of the cantilever beam during cooling the instrument from room temperature to 4 K. When the tunneling tip was adjacent to the free end of the cantilever jump-to-contact between tunneling tip and cantilever occurred and stable tunneling conditions were hard to achieve. However, if the tunneling tip meets the cantilever at a distance $L_{\text{tunneling}}$ from the fixed end of the cantilever with total length L , the effective stiffness of the cantilever increases by a factor of $(L/L_{\text{tunneling}})^3$ (see Eq. 14) and jump-to-contact is less likely to occur. Endurance was critical, because only in one of about ten cooling cycles all parts

of the complicated microscope worked. KBr (cleaved in situ) was used as a sample. After the sample was approached to the cantilever, jump-to-contact occurred and the sample area where the cantilever had landed was destroyed. After jump-to-contact occurred, the pressure on the tip region was released by pulling back the sample such that cantilever still stayed in contact with the sample, however the repulsive force between the front atom of the cantilever and the sample was reduced to ≈ 1 nN. With the reduced tip-sample force, the sample was moved laterally to an undisturbed area, and atomic resolution was immediately obtained. In summer 1991, we finally succeeded in obtaining true atomic resolution on KBr. Figure 19 shows the KBr (001) surface imaged in contact mode. Both ionic species are visible, because repulsive forces are used for imaging. The small bumps are attributed as K^+ ions and the large bumps as Br^- ions. Today even with refined non-contact AFM, only one atomic species appears as a protrusion in images of ionic crystals. Most likely, the dominant interaction between front atom and sample in non-contact AFM is electrostatic, so the charge of the front atom determines if cations or anions appear as protrusions, see e.g. Livshits *et al.* (1999a,b); Shluger *et al.* (1999). Figure 20 shows atomic resolution on KBr with linear singularities and atomic defects. This image was obtained by scanning an area of $5\text{ nm} \times 5\text{ nm}$ for a while and then doubling the scan size to $10\text{ nm} \times 10\text{ nm}$. The fast scanning direction was horizontal, the slow scanning direction vertical from bottom to top. In the lower section in Fig. 20 (region 1) the scan size was $5\text{ nm} \times 5\text{ nm}$. Region 2 is a transition area, where the x - and y -scan widths were continuously increased to 10 nm (an analog scan electronics was used where the widths of both scanning axes are independently controlled by a potentiometer in real time). In region 3, the scan size was set at $10\text{ nm} \times 10\text{ nm}$. Initially, we interpreted the singularity as a monoatomic step (Binnig (1992)). However, the height difference between the central area in Fig. 20 and the surrounding area is much smaller than a single step ($3.3\text{ \AA}$). Therefore, today it appears that the central area is a ‘scan window’, i.e. a region slightly damaged by the pressure of the scanning cantilever. Even scanning at very small loads of a nN or so has disturbed the surface slightly and created a depressed area with a $\sqrt{3} \times \sqrt{3}$ R 45° superstructure on the KBr surface. The presence of atomic defects (green arrows in Fig. 20), linear defects and superstructures strengthened our confidence in true atomic resolution capability of the AFM. However, the experimental difficulties with low-temperature operation, sample preparation, tunneling detection etc. were quite impractical for routine measurements.

In 1993, Ohnesorge and Binnig (1993) pursued a different method to cancel the damaging long-range forces. The long-range attractive forces which cause jump-to-contact were reduced by immersing the cantilever and sample into a liquid, as explained by Israelachvili (1991). Ohnesorge and Binnig (1993) achieved true atomic resolution by AFM across steps on Calcite in repulsive *and* attractive mode. True atomic resolution of inert surfaces by AFM had thus been clearly established. However, the enigmatic icon of atomic resolution microscopy, Si(111)-(7×7) remained an unsolved challenge. Even experts in experimental AFM were convinced that this goal is impossible to reach because of silicons high reactivity and the strong bonds that are formed between cantilever tips and the Si surface.

V. THE RUSH FOR SILICON

Imaging the Si (111)-(7×7) reconstruction has been crucial for the success of the STM, and therefore imaging silicon by AFM with atomic resolution has been a goal for many AFM researchers. However, so far atomic resolution had not been obtained on reactive surfaces. The ions in alkali-halides form more or less closed noble gas shells and are therefore inert. In contrast, Silicon is known to form strong covalent bonds with a cohesive energy of roughly 2 eV per bond. The jump-to-contact problem outlined in section III.A is even more severe for silicon, and using silicon cantilevers on silicon samples in contact mode in vacuum has proven not to work. At Park Scientific Instruments, the frequency modulation technique pioneered by Albrecht *et al.* (1991) was used at that time in ambient conditions, and it was tempting to incorporate the technique into our newly designed UHV microscope (‘AutoProbe VP’). Marco Tortonese had developed piezoresistive cantilevers during his time as a graduate student in Cal Quate’s group in Stanford and made them available to us. In vacuum, the piezoresistive cantilevers have excellent Q -values and were thus predestined for using them in the FM mode. In late 1993, Giessibl and Trafas (1994) observed single steps and kinks on KBr using the FM method (see Fig. 21). Also in 1993, Giessibl (1994) observed atomic rows on Si (111)-(7×7) and in May 1994 (Giessibl, 1995), the first clear images of the 7×7 pattern appeared (see Fig. 22).

A different route had been pursued in the group of H.-J. Güntherodt: Howald, Lüthi, Meyer, Güthner, and Güntherodt (1994) have coated the tip of the cantilever with PTFE (poly-tetra-fluoro-ethylen) and found that atomic steps and even the

Si(111) 7×7 unit cell periodicity could be imaged in contact mode in vacuum (see Fig. 23). Erlandsson *et al.* (1997) could show that atomic resolution on Si(111) 7×7 is also possible with the amplitude modulation technique (see Fig. 24).

VI. FREQUENCY MODULATION AFM (FM-AFM)

A. Experimental setup

In FM-AFM, a cantilever with eigenfrequency f_0 and spring constant k is subject to controlled positive feedback such that it oscillates with a constant amplitude A (Albrecht *et al.*, 1991; Dürig *et al.*, 1992) as shown in Fig. 25. The deflection signal first enters a bandpass filter. Then the signal splits in three branches: one branch is phase shifted, routed through an analog multiplier and fed back to the cantilever via an actuator; one branch is used to compute the actual oscillation amplitude, this signal is used to calculate a gain input g for the analog multiplier and one branch is used to feed a frequency detector. The frequency f is determined by the eigenfrequency f_0 of the cantilever and the phase shift φ between the mechanical excitation generated at the actuator and the deflection of the cantilever. If $\varphi = \pi/2$, the loop oscillates at $f = f_0$.

Forces between tip and sample cause a change in $f = f_0 + \Delta f$. The eigenfrequency of a harmonic oscillator is given by $(k^*/m^*)^{0.5}/(2\pi)$, where k^* is the effective spring constant and m^* is the effective mass. If the second derivative of the tip-sample potential $k_{ts} = \frac{\partial^2 V_{ts}}{\partial z^2}$ is constant for the whole range covered by the oscillating cantilever, $k^* = k + k_{ts}$. If $k_{ts} \ll k$, the square root can be expanded as a Taylor series and the shift in eigenfrequency is approximately given by:

$$\Delta f = \frac{k_{ts}}{2k} f_0. \quad (21)$$

The case where k_{ts} is not constant is treated in the next chapter. By measuring the frequency shift Δf , the tip-sample force gradient can be determined.

The oscillator circuit is a critical component in FM-AFM. The function of this device is understood best by analyzing the cantilever motion. The cantilever can be treated as a damped harmonic oscillator that is externally driven. For sinusoidal excitations $A_{drive} e^{i2\pi f_{drive} t}$ and a quality factor $Q \gg 1$, the response of the oscillation amplitude of

the cantilever is given by

$$\frac{A}{A_{drive}} = \frac{1}{1 - f_{drive}^2/f_0^2 + i f_{drive}/(f_0 Q)}. \quad (22)$$

The absolute value of the amplitude is given by

$$|A| = \frac{|A_{drive}|}{\sqrt{(1 - f_{drive}^2/f_0^2)^2 + f_{drive}^2/(f_0^2 Q^2)}} \quad (23)$$

and the phase angle between the driving and resulting signals is

$$\varphi = \arctan\left[\frac{f_{drive}}{Q f_0 (1 - f_{drive}^2/f_0^2)}\right] \quad (24)$$

In the case of a closed feedback loop as shown in Fig. 25, the driving frequency cannot be chosen freely anymore but is determined by f_0 of the cantilever, the phase shift φ and the tip-sample forces. The purpose of the oscillator circuit is to provide controlled positive feedback (with a phase angle of $\varphi = \pi/2$) such that the cantilever oscillates at a constant amplitude. This requirement is fulfilled with the setup shown in Fig. 25.

The cantilever deflection signal is first routed through a bandpass filter which cuts off the noise from unwanted frequency bands. The filtered deflection signal branches into an rms-to-dc converter and a phase shifter (see Horowitz and Hill (1989, 2nd ed.)). The rms-to-dc chip computes a dc signal which corresponds to the rms-value of the amplitude. This signal is added to the inverted setpoint rms amplitude, yielding the amplitude error signal. The amplitude error enters a proportional (P) and optional integral (I) controller and the resulting signal g is multiplied with the phase shifted cantilever deflection signal q'' with an analog multiplier chip. This signal drives the actuator. The phase shifter is adjusted so that the driving signal required for establishing the desired oscillation amplitude is minimal; φ is exactly $\pi/2$ in this case. Dürig *et al.* (1992) and Gauthier *et al.* (2002b, 2001) have analyzed the stability issues related to this forced motion.

The filtered cantilever deflection signal is fed into a frequency-to-voltage converter. Initially, analog circuits were used as frequency to voltage converters (Albrecht *et al.*, 1991). Recently, commercial digital phase-locked-loop (PLL) detectors (Nanosurf, 2002) and analog quartz-stabilized PLLs (Kobayashi *et al.*, 2001) became available which are more precise and more convenient. The PLL allows to set a reference frequency f_{ref} and outputs a signal which is proportional to the difference between the input frequency f and the reference frequency f_{ref} . This signal $\Delta f = f - f_{ref}$ is used as the imaging signal in FM-AFM. Some

researchers use the PLLs oscillator signal to drive the cantilever. The advantage is the greater spectral cleanliness of the PLL oscillator signal. A disadvantage is that the cantilever drive loop becomes more convoluted, and once the PLL is out of lock, the oscillation of the cantilever stops.

B. Experimental parameters

While it was believed initially that the net force between the front atom of the tip and the sample has to be attractive when atomic resolution is desired, theoretical (Jarvis *et al.*, 2001; Sokolov *et al.*, 1999) and experimental evidence (Giessibl *et al.*, 2001a,b) suggests that atomic resolution even on highly reactive samples is possible with repulsive forces. Nevertheless, the dynamic modes are commonly still called “non-contact” modes. For atomic studies in vacuum, the FM-mode is now the preferred AFM technique.

FM-AFM was introduced by Albrecht, Grutter, Horne, and Rugar (1991) in magnetic force microscopy. In these experiments, Albrecht *et al.* imaged a thin film CoPtCr magnetic recording disk (Fig. 7a in Albrecht *et al.* (1991)) with a cantilever with a spring constant $k \approx 10 \text{ N/m}$, eigenfrequency $f_0 = 68\,485 \text{ Hz}$, amplitude $A = 5 \text{ nm}$, a Q value of 40000 (Albrecht (2000)) and a tip with a thin magnetic film coverage. The noise level and imaging speed was enhanced significantly compared to amplitude modulation techniques. In 1993, the frequency modulation method was implemented in the prototype of a commercial STM/AFM for ultra-high vacuum (Giessibl and Trafas, 1994). Initial experiments on KCl yielded excellent resolution and soon after, the Si (111)-(7 $\times$ 7) surface was imaged with true atomic resolution for the first time (Giessibl, 1995). FM-AFM has five operating parameters:

1. The spring constant of the cantilever k .
2. The eigenfrequency of the cantilever f_0 .
3. The Q -value of the cantilever Q .
4. The oscillation amplitude A .
5. The frequency shift of the cantilever Δf .

The first three parameters are determined by the type of cantilever that is used, while the latter two parameters can be freely adjusted. The initial parameters which provided true

atomic resolution ($k = 17 \text{ N/m}$, $f_0 = 114 \text{ kHz}$, $Q = 28\,000$, $A = 34 \text{ nm}$, $\Delta f = -70 \text{ Hz}$) were found empirically. Surprisingly, the amplitude necessary for obtaining good results was very large compared to atomic dimensions. The necessity of using large amplitudes for obtaining good results seems counterintuitive, because the tip of the cantilever spends only a small fraction during an oscillation cycle in close vicinity to the sample. In hindsight, it appears that the large amplitudes were required to prevent instabilities of the cantilever oscillation (see section III.A). Apparently, the product between spring constant and amplitude (column “ $kA[\text{nN}]$ ” in Table I) has to be larger than $\approx 100 \text{ nN}$ to provide a sufficiently strong withdrawing force. In the experiments conducted in 1994 (see rows 1 and 2 in Table I), this condition was not met, and correspondingly, the resolution was not quite atomic yet. An additional lower-threshold condition for A is proposed: $E = \frac{1}{2}kA^2$ (column “ $E[\text{keV}]$ ” in Table I) should be large compared to ΔE_{ts} defined in Eq. 44. This condition is required for maintaining stable oscillation amplitudes as exemplified below. As shown in Table I, atomic resolution on silicon and other samples was reproduced by other groups with similar operating parameters $\Delta f \approx -100 \text{ Hz}$, $k \approx 20 \text{ N/m}$, $f_0 \approx 200 \text{ kHz}$ and $A \approx 10 \text{ nm}$. Several commercial vendors now offer FM-AFMs that operate with these parameters (Jeol, 2002; Omicron, 2002).

The use of high- Q cantilevers with a stiffness of $k \approx 20 \text{ N/m}$ oscillating with an amplitude of $A \approx 10 \text{ nm}$ has enabled many groups to routinely achieve atomic resolution by FM-AFM. As shown in table I, this mode is used in many laboratories now and we therefore call it the “classic” FM-AFM mode. While the operating parameters of the classic FM-AFM mode provide good results routinely, it was not proved initially that these parameters yield optimal resolution. The search space for finding the optimal parameters was not completely open, because micromachined cantilevers were only available with a limited selection of spring constants. A theoretical study has shown later (Giessibl *et al.*, 1999), that the optimal amplitudes are in the Å-range, requiring spring constants of the order of a few hundred N/m, much stiffer than the spring constant of commercially available cantilevers. This result has been verified experimentally by achieving unprecedented resolution with a cantilever with $k = 1800 \text{ N/m}$ and sub-nm oscillation amplitudes (Giessibl *et al.*, 2001a, 2000). Eguchi and Hasegawa (2002) have also achieved extremely high resolution with a silicon cantilever with a stiffness of 46.0 N/m and an oscillation amplitude of only 2.8 nm .

VII. PHYSICAL OBSERVABLES IN FM-AFM

A. Frequency shift and conservative forces

1. Generic calculation

The oscillation frequency is the main observable in FM-AFM and it is important to establish a connection between frequency shift and the forces acting between tip and sample. While the frequency can be calculated numerically (Anczykowski *et al.*, 1996), an analytic calculation is important for finding the functional relationships between operational parameters and the physical tip-sample forces. The motion of the cantilever (spring constant k , effective mass m^*) can be described by a weakly disturbed harmonic oscillator. Figure 26 shows the deflection $q'(t)$ of the tip of the cantilever: it oscillates with an amplitude A at a distance $q(t)$ to a sample. The closest point to the sample is $q = d$ and $q(t) = q'(t) + d + A$. The Hamiltonian of the cantilever is:

$$H = \frac{p^2}{2m^*} + \frac{kq'^2}{2} + V_{ts}(q) \quad (25)$$

where $p = m^* dq'/dt$. The unperturbed motion is given by:

$$q'(t) = A \cos(2\pi f_0 t) \quad (26)$$

and the frequency is:

$$f_0 = \frac{1}{2\pi} \sqrt{\frac{k}{m^*}}. \quad (27)$$

If the force gradient $k_{ts} = -\frac{\partial F_{ts}}{\partial z}$ is constant during the oscillation cycle, the calculation of the frequency shift is trivial:

$$\Delta f = f_0 \frac{k_{ts}}{2k}. \quad (28)$$

However, in classic FM-AFM k_{ts} varies orders of magnitude during one oscillation cycle and a perturbation approach as shown below has to be employed for the calculation of the frequency shift.

The first derivation of the frequency shift in FM-AFM (Giessibl, 1997) utilized canonical perturbation theory (see e.g. Goldstein (1980)). The result of this calculation is:

$$\Delta f = -\frac{f_0}{kA^2} \langle F_{ts} q' \rangle. \quad (29)$$

where the pointed brackets indicate averaging across one oscillation cycle.

The applicability of first-order perturbation theory depends on the magnitude of the perturbation, i.e. on the ratio between V_{ts} and the energy of the oscillating cantilever $E = H_0$. In FM-AFM, E is typically in the range of several keVs (see table I), while V_{ts} is only a few electron volts and first order perturbation theory yields results for Δf with excellent precision.

An alternate approach to the calculation of Δf has been followed by Baratoff (1997), Dürig (1999a,b) and Livshits *et al.* (1999a). This approach also derives the magnitude of the higher harmonics and the constant deflection of the cantilever.

This method involves solving Newton's equation of motion for the cantilever (effective mass μ^* , spring constant k):

$$\mu^* \frac{d^2 q'}{dt^2} = -kq' + F_{ts}(q'). \quad (30)$$

The cantilever motion is assumed to be periodic, therefore it is expressed as a Fourier series with fundamental frequency f :

$$q'(t) = \sum_{m=0}^{\infty} a_m \cos(m2\pi ft). \quad (31)$$

Insertion into Eq. 30 yields:

$$\sum_{m=0}^{\infty} a_m \left[-(m2\pi f)^2 \mu^* + k \right] \cos(m2\pi ft) = F_{ts}(q'). \quad (32)$$

Multiplication by $\cos(l2\pi ft)$ and integration from $t = 0$ to $t = 1/f$ yields:

$$a_m \left[-(m2\pi f)^2 \mu^* + k \right] \pi(1 + \delta_{m0}) = 2\pi f \int_0^{1/f} F_{ts}(q') \cos(m2\pi ft) dt \quad (33)$$

by making use of the orthogonality of the angular functions

$$\int_0^{2\pi} \cos(mx) \cos(lx) dx = \pi \delta_{ml} (1 + \delta_{m0}). \quad (34)$$

If the perturbation is weak, $q'(t) \approx A \cos(2\pi ft)$ with $f = f_0 + \Delta f$, $f_0 = \frac{1}{2\pi} \sqrt{\frac{k}{\mu^*}}$ and $|\Delta f| \ll f_0$. To first order, the frequency shift is given by:

$$\Delta f = -\frac{f_0^2}{kA} \int_0^{1/f_0} F_{ts}(q') \cos(2\pi f_0 t) dt = -\frac{f_0}{kA^2} \langle F_{ts} q' \rangle \quad (35)$$

which of course equals the result of the Hamilton-Jacobi method.

The results of these calculations are also applicable for amplitude modulation AFM (Bielefeldt and Giessibl (1999)). Hölscher *et al.* (1999a) have also used a canonical perturbation theory approach and extended it to show that the frequency shift as a function of

amplitude for inverse power forces can be expressed as a rational function for *all* amplitudes, not just in the large amplitude limes. Sasaki and Tsukada have obtained a similar result to Eq. 29 with a different type of perturbation theory (Sasaki and Tsukada, 1998, 1999; Tsukada *et al.*, 2002).

2. An intuitive expression for frequency shifts as a function of amplitude

For small amplitudes, the frequency shift is a very simple function of the tip-sample forces – it is proportional to the tip-sample force gradient k_{ts} . For large amplitudes, the frequency shift is given by the rather complicated expressions Eq. 29 and Eq. 35. With integration by parts, these complicated formulas transform into a very simple expression that resembles Eq. 28 (Giessibl, 2001).

$$\Delta f(z) = f_0 \frac{\langle k_{ts}(z) \rangle}{2k} \quad (36)$$

with

$$\langle k_{ts}(z) \rangle = \frac{1}{\frac{\pi}{2}A^2} \int_{-A}^A k_{ts}(z - q') \sqrt{A^2 - q'^2} dq'. \quad (37)$$

This expression is closely related to Eq. 28: the constant k_{ts} of Eq. 28 is replaced by a weighted average $\langle k_{ts} \rangle$, where the weight function $w(q', A)$ is a semi circle with radius A divided by the area of the semicircle $\Gamma = \pi A^2/2$ (see Fig. 27). For $A \rightarrow 0$, the semicircular weight function with its normalization factor $2/\pi A^2$ is a representation of Dirac's Delta function. Figure 28 shows the convolution with the proper normalization factor, and it is immediately apparent from this figure how the use of small amplitudes increases the weight of the short-range atomic forces over the unwanted long-range forces. The amplitude in FM-AFM allows to tune the sensitivity of the AFM to forces of various ranges.

3. Frequency shift for a typical tip-sample force

The interaction of a macroscopic tip of an AFM with a sample is a complicated many-body problem and F_{ts} cannot be described by a simple function. However, quite realistic model forces can be constructed from linear combinations of the following basic types: a) inverse-power forces, b) power forces and c) exponential forces. Analytic expressions for the frequency shift as a function of tip-sample distance z and amplitude A are listed in

Giessibl and Bielefeldt (2000). A typical tip-sample force is composed of long range contributions and short range contributions. This force can be approximated by a long-range van-der-Waals component and a short-range Morse type interaction:

$$F_{ts}(z) = \frac{C}{z + \sigma} + 2\kappa E_{bond}(-e^{-\kappa(z-\sigma)} + e^{-2\kappa(z-\sigma)}). \quad (38)$$

C depends on the tip angle and the Hamaker constant of tip and sample, and E_{bond} , σ and κ are the bonding energy, equilibrium distance and decay length of the Morse potential respectively. With the results derived in Giessibl and Bielefeldt (2000), the resulting frequency shift is:

$$\begin{aligned} \Delta f(z, A) = & \frac{f_0}{kA} \frac{C}{z + \sigma} \left[F_1^{1,1/2}\left(\frac{-2A}{z + \sigma}\right) - F_2^{1,3/2}\left(\frac{-2A}{z + \sigma}\right) \right] \\ & - f_0 \frac{2\kappa E_{bond}}{kA} \left\{ e^{-\kappa z} \left[M_1^{1/2}(-2\kappa A) - M_2^{3/2}(-2\kappa A) \right] \right. \\ & \left. + e^{-2\kappa z} \left[M_1^{1/2}(-4\kappa A) - M_2^{3/2}(-4\kappa A) \right] \right\}. \end{aligned} \quad (39)$$

where $F_c^{a,b}(z)$ is the Hypergeometric Function and $M_b^a(z)$ is Kummer's Function (Abramowitz and Stegun, 1970, 9th ed.).

Equation 39 describes the frequency shift as a function of amplitude and tip-sample distance. For small amplitudes, the frequency shift is independent of the amplitude and proportional to the tip-sample force gradient k_{ts} (Eq. 28). For amplitudes that are large compared to the range of the tip-sample force, the frequency shift is a function of the amplitude $\Delta f \propto A^{-1.5}$. If amplitudes larger than the range of the relevant forces are used, it is helpful to introduce a “normalized frequency shift” γ defined by:

$$\gamma(z, A) := \frac{kA^{3/2}}{f_0} \Delta f(z, A). \quad (40)$$

For large amplitudes, $\gamma(z, A)$ asymptotically approaches a constant value (see Fig. 2 in Ref. Giessibl and Bielefeldt (2000)), i.e. $\lim_{A \rightarrow \infty} \gamma(z, A) \equiv \gamma_{lA}(z)$. The normalized frequency shift is calculated from the tip-sample force with

$$\gamma_{lA}(z) = \frac{1}{\sqrt{2\pi}} \int_0^\infty \frac{F_{ts}(z + z')}{\sqrt{z'}} dz'. \quad (41)$$

The normalized frequency shift helps to characterize AFM experiments and has a similar role as the tunneling impedance in STM on metals. Hölcher *et al.* (2000) have performed

frequency shift versus distance measurements with a silicon cantilever on a graphite surface with amplitudes ranging from 54 Å to 180 Å and verified the concept of the normalized frequency shift $\gamma = \Delta f \times k \times A^{3/2} / f_0$ as the pertinent imaging parameter in classic FM-AFM (see Fig. 29). Five frequency shift curves taken with amplitudes ranging from 54 Å to 180 Å match precisely when rescaled using the normalized frequency shift. Thus, for small amplitudes the frequency shift is very sensitive to short-range forces, because short-range forces have a very strong force gradient, while for large amplitudes, long-range forces contribute heavily to the frequency shift. Figure 30 shows the tip-sample force defined in Eq. 38 and the corresponding force gradient and normalized frequency shift γ_{IA} . The parameters for the short-range interaction are adopted from Perez *et al.* (1998): $\kappa = 12.76 \text{ nm}^{-1}$, $E_{bond} = 2.273 \text{ eV}$ and $\sigma = 2.357 \text{ Å}$. The force gradient is vanishing for $z > 6 \text{ Å}$, while the normalized frequency shift for large amplitudes reaches almost half its maximum at this distance. The dependence of the frequency shift with amplitude shows that *small amplitudes increase the sensitivity to short-range forces!* The possibility of adjusting the amplitude in FM-AFM compares to tuning an optical spectrometer to a passing wavelength. When short-range interactions are to be probed, the amplitude should be in the range of the short-range forces. While using amplitudes in the Å-range has been elusive with conventional cantilevers because of the instability problem described in subsection III.A, stiff sensors such as the qPlus sensor displayed in Fig. 11 are suited well for small-amplitude operation.

4. Deconvolution of forces from frequency shifts

Frequency shifts can be measured with high accuracy and low noise, while the measurement of dc-forces is subject to large noise. However, forces and not frequency shifts are of primary physical interest. A number of methods have been proposed to derive forces from the frequency shift curves.

The first type of methods requires the relation of frequency shift versus distance $\Delta f(z)$ over the region of interest. Because force and frequency shift are connected through a convolution, a deconvolution scheme is needed to connect forces (or force gradients) to the frequency shift and vice versa. Giessibl (1997) has proposed to build a model force composed from basic functions (inverse power- and exponential forces) and fit the parameters (range and strength) of the model force such that its corresponding frequency shift matches the

experimental frequency shift. Gotsmann *et al.* (1999) have proposed a numerical algorithm and Dürig (1999b) has invented an iterative scheme for force deconvolution. Giessibl (2001) has proposed a simple and intuitive matrix method to deconvolute forces from frequency shifts.

The second type of spectroscopy methods requires to know the frequency as a function of cantilever amplitude $\Delta f(A)$. Hölscher *et al.* (1999b) and Hölscher (2002) have modified the method elucidated in §12 of Landau's textbook on classical mechanics (Landau and Lifshitz, 1990, 13th ed.) to recover the interaction potential from the dependence of the oscillation period $T = 1/f$ from energy $E = kA^2/2$.

For the third type, invented by Dürig (2000), the full tip-sample potential curve can be recovered within the z -interval covered by the cantilever motion if the amplitudes and phases of all the higher harmonics of the cantilever motion are known. This method is very elegant because, in principle, the higher harmonics can be measured in real time which obliterates the need to take time consuming $\Delta f(z)$ or $\Delta f(A)$ spectra. Dürig's method is particularly promising for small-amplitude operations, because then the first few harmonics at $2f, 3f, \dots$ already contain characteristic information about the tip sample potential.

B. Average tunneling current for oscillating tips

When the tip of the cantilever and the sample are both conductive, simultaneous STM and FM-AFM operation is possible, i.e. the tunneling current I_t as well as the frequency shift can be recorded while scanning the surface. In most cases, the bandwidth of the tunneling current-preamplifier is much smaller than the oscillation frequency f_0 of typical cantilevers. The measured tunneling current is given by the time-average over one oscillation cycle. With the exponential distance dependence $I_t(z) = I_0 e^{-2\kappa_t z}$ (see Eq. 1) we find:

$$\langle I_t(z, A) \rangle = I_0 e^{-2\kappa_t z} M_1^{1/2}(-4\kappa_t A) \quad (42)$$

where $M_b^a(\zeta)$ is the Kummer Function (Abramowitz and Stegun, 1970, 9th ed.). When $\kappa_t A \gg 1$,

$$\langle I_t(z, A) \rangle \approx I_t(z, 0) / \sqrt{4\pi\kappa_t A}. \quad (43)$$

Figure 31 shows the dependence of the tunneling current as a function of the product

between κ_t and A . For $A = 5 \text{ nm}$ and $\kappa_t = 1 \text{ \AA}^{-1}$, the average tunneling current is $\approx 1/25$ of the value when the cantilever does not oscillate. Because the noise of the current measurement decreases with an increasing average tunneling current, the use of small amplitudes improves the quality of simultaneous STM and FM-AFM measurements.

It is noted that Eq. 43 is an upper threshold. When using large amplitudes ($\kappa_t A \gg 1$), the tunneling current vs. time is a series of Gaussian functions spaced by $1/f$ where f is the oscillation frequency of the cantilever. Especially when using cantilevers with large eigenfrequencies, the tunneling current varies very rapidly with time. Because of slew-rate and bandwidth limitations, typical tunneling preamplifiers are unable to convert these rapid current variations in output voltage swings. Thus, the experimental average current can even become smaller than given by Eq. 43.

C. Damping and dissipative forces

Conservative tip-sample forces cause a frequency shift. A non-conservative component in the tip-sample force, that is a hysteresis in the force versus distance graph

$$\Delta E_{ts}(\vec{x}) = \oint_{\Lambda} \vec{F}_{ts}(\vec{x} + \vec{x}') d\vec{x}', \quad (44)$$

where Λ is the trajectory of the oscillating cantilever, causes energy loss in the motion of the cantilever. This energy loss is measurable. The cantilever itself already dissipates energy (internal dissipation). When the tip of the cantilever is far from the sample, the damping of the cantilever is due to internal dissipation and the energy loss per oscillation cycle is given by:

$$\Delta E_{CL} = 2\pi \frac{E}{Q} \quad (45)$$

where $E = kA^2/2$ is the energy of the cantilever and Q is its quality factor. When the phase angle between the excursion of the actuator and the excursion of the cantilever is exactly $\varphi = \pi/2$, the cantilever oscillates at frequency f_0 and the driving signal is $A_{drive} = Ae^{i\pi/2}/Q$. Hence, the driving amplitude and dissipation are connected:

$$|A_{drive}| = |A| \frac{\Delta E_{CL}}{2\pi E}. \quad (46)$$

When the tip oscillates close to the sample, additional damping occurs and the driving signal A_{drive} is increased by the oscillator control electronics to A'_{drive} for maintaining a constant

amplitude A where

$$|A'_{drive}| = |A| \frac{\Delta E_{CL} + \Delta E_{ts}}{2\pi E} = |A| \left(\frac{1}{Q} + \frac{\Delta E_{ts}}{2\pi E} \right). \quad (47)$$

Equation 47 has an important implication on the optimal Q factor of the cantilever. While a high Q factor results in low frequency noise (see Eq. 50), Eq. 47 shows that the Q value of the cantilever should not be much higher than the ratio $2\pi E/\Delta E_{ts}$. If Q is much higher than this value, it is difficult for the oscillator circuit to maintain a constant amplitude, because small changes in ΔE_{ts} require a major correction in the control output g .

Measuring the damping signal yields the dissipation in the approach and retract phases of the oscillating tip where

$$\Delta E_{ts} = 2\pi \frac{E}{Q} \left(\frac{|A'_{drive}|}{|A_{drive}|} - 1 \right). \quad (48)$$

The ratio $|A'_{drive}|/|A_{drive}|$ is easily accessible in the dc input (g) of the analog multiplier chip in Fig. 25 – an increase in the tip-sample dissipation ΔE_{ts} is reflected in an increased gain signal g' in the oscillator electronics and $g'/g = |A'_{drive}|/|A_{drive}|$. Several authors have recorded this signal simultaneously with the frequency shift and thus measured both elastic and non-elastic interaction forces simultaneously, see e.g. Bammerlin *et al.* (1997); Hug and Baratoff (2002); Lüthi *et al.* (1997); Ueyama *et al.* (1998).

Physical origins of dissipation are discussed in Abdurixit *et al.* (1999); Dürig (1999a); Gauthier *et al.* (2002a); Giessibl *et al.* (2002); Hoffmann *et al.* (2001a); Hug and Baratoff (2002).

It is noted, that dispersions in the oscillator circuit and in the actuator assembly can lead to artifacts in the interpretation of damping data, because $|A_{drive}| = |A|/Q$ only holds for $f = f_0$. Anczykowski *et al.* (1999) have introduced a method that yields the correct dissipation energy even for cases where the phase angle between actuator and cantilever is not $\varphi = \pi/2$.

Mechanical resonances in the actuator assembly are likely to occur at the high resonance frequencies of conventional cantilevers. These resonances can cause sharp variations of the phase with frequency and thus create artifacts in the measurement of ΔE_{ts} . A self-oscillation technique for cantilevers (Giessibl and Tortonese (1997)) helps to avoid these resonances.

VIII. NOISE IN FREQUENCY MODULATION AFM

A. Generic calculation

The vertical noise in FM-AFM can be calculated in the same fashion as in the STM case (see Fig. 5); it is given by the ratio between the noise in the imaging signal and the slope of the imaging signal with respect to z :

$$\delta z = \frac{\delta \Delta f}{\left| \frac{\partial \Delta f}{\partial z} \right|}. \quad (49)$$

Figure 32 shows a typical frequency shift versus distance curve. Because the distance between the tip and sample is measured indirectly through the frequency shift, it is clearly evident that the noise in the frequency measurement $\delta \Delta f$ translates into vertical noise δz and is given by the ratio between $\delta \Delta f$ and the slope of the frequency shift curve $\Delta f(z)$ (Eq. 49). Low vertical noise is obviously obtained for a low-noise frequency measurement and a steep slope of the frequency shift curve. Additional boundary conditions apply: if the force between front atom and surface is too large, the front atom or larger sections of tip or sample can shear off. It is interesting to note, that in FM-AFM the noise will increase again upon further reducing the tip-sample distance when approaching the minimum of the $\Delta f(z)$ curve. Because the frequency shift is not monotonic with respect to z , stable feedback of the microscope is only possible either on the branch of Δf with positive slope or on the one with negative slope. In FM-AFM with atomic resolution, the branch with positive slope is usually chosen. However, when using very small amplitudes, it is also possible to work on the branch with negative slope (see Giessibl *et al.* (2001b)).

It is of practical importance to note that the minimum of the frequency versus distance curve shown in Fig. 32 is a function of the lateral tip position. Directly over a sample atom, the minimum can be very deep. However, at other sample sites there may be small negative frequency shift. Imaging can only be performed with frequency shift setpoints which are reachable on every (x, y) position on the imaged sample area, otherwise a tip crash occurs.

B. Noise in the frequency measurement

Equation 49 shows that the accuracy of the frequency shift measurement determines directly the vertical resolution in FM-AFM. What is the accuracy of the measurement of

the oscillation frequency of the cantilever? Martin *et al.* (1987), McClelland *et al.* (1987) have studied the influence of thermal noise on the cantilever and Albrecht *et al.* (1991) and Smith (1995) have calculated the thermal limit of the frequency noise. Leaving aside prefactors of the order of π , all these authors come to a similar conclusion, namely that the square of the relative frequency noise is given by the ratio between the thermal energy of the cantilever ($k_B T$) and the mechanical energy stored in it ($0.5kA^2$), divided by its quality factor Q and multiplied by the ratio between bandwidth B and cantilever eigenfrequency f_0 . Specifically, Albrecht *et al.* (1991) find

$$\frac{\delta f_0}{f_0} = \sqrt{\frac{k_B T B}{\pi k A^2 f_0 Q}}. \quad (50)$$

Albrecht *et al.* (1991) support Eq. 50 with measurements on the dependence of δf_0 with Q (Fig. 5 in Albrecht *et al.* (1991)) and A (Fig. 6 in Albrecht *et al.* (1991)) and clearly state, that Eq. 50 only contains the thermal cantilever noise and disregards the noise of the deflection sensor. Correspondingly, the frequency noise becomes larger than predicted by Eq. 50 for large Q - values in Fig. 5 of Albrecht *et al.* (1991). This deviations are traced to interferometer noise, e.g. noise in the cantilever's deflection sensor. Albrecht *et al.* (1991) do not provide measurements of δf_0 as a function of bandwidth B . Equation 50 predicts a $B^{0.5}$ -dependence. However, theoretical arguments by Dürig *et al.* (1997) and an analysis and measurements by Giessibl (2002) indicate a $B^{1.5}$ -dependence of frequency noise. The following analysis shows the reasons for that.

The frequency is given by the inverse of the time lag Ξ between two consecutive zero-crossings of the cantilever with positive velocity. However, the deflection of the cantilever q' is subject to a noise level $\delta q'$ as shown in Fig. 33. The deflection noise $\delta q'$ has two major contributions: thermal excitation of the cantilever outside of its resonance frequency and instrumental noise in the measurement of the deflection q' . The oscillation period Ξ can only be measured with an rms accuracy $\delta \Xi$. The uncertainty of the time of the zero-crossing is $\delta \Xi/2$, where $\delta \Xi/2$ is given by the ratio between the cantilever deflection noise and the slope of the $q'(t)$ curve:

$$\frac{\delta \Xi}{2} = \frac{\delta q'}{2\pi f_0 A}. \quad (51)$$

Because $f_0 = 1/\Xi$, $\delta f_0/f_0 = \delta \Xi/\Xi$ and

$$\frac{\delta f_0}{f_0} = \frac{\delta q'}{\pi A}. \quad (52)$$

Equation 52 only applies to frequency changes on a timescale of $1/f_0$. When measuring frequency variations on a longer timescale, more zero crossings can be used to determine the frequency change and the precision of the frequency measurement increases. The output of the frequency detector (phase-locked-loop, see Fig. 25) typically has a low-pass filter with bandwidth $B_{FM} \ll f_0$, thus the effective frequency noise is smaller than the value after Eq. 52 (see Ref. Giessibl (2002)). With $\delta q' = n_{q'} \sqrt{B_{FM}}$, we find

$$\delta f = \frac{n_{q'}}{\pi A} B_{FM}^{3/2}. \quad (53)$$

The scaling law $\delta f \propto B_{FM}^{3/2}$ has first been found by Dürig *et al.* (1997). The deflection noise density $n_{q'}$ has two major contributors: a) thermal noise of the cantilever and b) detector noise. Because the two noise sources are statistically independent, we find

$$n_{q'} = \sqrt{n_{q' thermal} + n_{q' detector}} \quad (54)$$

with

$$n_{q' thermal} = \sqrt{\frac{2k_B T}{\pi k f_0 Q}} \quad (55)$$

after Becker (1969). The detector deflection noise density $n_{q' detector}$ is determined by the physical setup of the deflection sensor and describes the quality of the deflection sensor. For practical purposes, it can be assumed to be constant for frequencies around f_0 . Good interferometers reach deflection noise densities of $100 \text{ fm}/\sqrt{\text{Hz}}$.

In summary, the frequency noise is proportional to the deflection noise density times $B^{1.5}$ and inversely proportional to the amplitude. While Eq. 55 suggests the use of cantilevers with infinitely high Q , Eq. 47 and the discussion after it imply that Q should not be significantly larger than the ratio between the energy stored in the cantilever and the energy loss per oscillation cycle due to the tip-sample interaction. If Q is much higher than this value, controlling the amplitude of the cantilever can become difficult and instabilities are likely to occur. Frequency noise is discussed in greater depth and compared to experimental noise measurements in Giessibl (2002).

C. Optimal amplitude for minimal vertical noise

Both the nominator and denominator in the generic FM AFM noise (Eq. 49) are functions of the amplitude – the frequency noise is proportional to $1/A$, the slope of the frequency shift

curve is constant at first and drops as $A^{-1.5}$ for large amplitudes. Thus, there is a minimal noise for amplitudes in the order of the range λ of the tip sample force F_{ts} (Giessibl *et al.*, 1999):

$$A_{optimal} \approx \lambda. \quad (56)$$

Here, we calculate the vertical noise for a specific example. We consider a tip-sample interaction given by a Morse potential with a depth of -2.15 eV, a decay length of $\kappa = 1.55 \text{ \AA}^{-1}$ and an equilibrium distance of $\sigma = 2.35 \text{ \AA}$. As a cantilever, we consider a qPlus sensor as shown in Fig. 11 with $k = 1800 \text{ N/m}$ and $n_{q'} = 100 \text{ fm}/\sqrt{\text{Hz}}$, operated with $B_{FM} = 100 \text{ Hz}$. Figure 34 shows the vertical noise as a function of amplitude for a fixed closest tip-sample distance of $z_{min} = 4 \text{ \AA}$. Minimum noise occurs for $\log A/\text{m} = -9.9$, i.e. for $A \approx 1.26 \text{ \AA}$, and for $A = 340 \text{ \AA}$, the noise is about one order of magnitude larger. For chemical forces, $\lambda \approx 1 \text{ \AA}$. However, operating a conventional cantilever with amplitudes in the $\text{\AA}$ -range close to a sample is impossible because of the jump-to-contact problem (section III.A). The cantilever spring constant k needs to be at least a few hundred N/m to enable operation with amplitudes in the $\text{\AA}$ -range.

IX. APPLICATIONS OF CLASSIC FREQUENCY MODULATION AFM

A. Imaging

Shortly after the first demonstration of true atomic resolution of Si by AFM, Güthner (1996); Kitamura and Iwatsuki (1995); Lüthi *et al.* (1996); Nakagiri *et al.* (1997) succeeded in imaging Si with atomic resolution using FM-AFM with similar parameters. In November 1994, Patrin (1995) succeeded in imaging KCl, an insulator with FM-AFM (see Fig. 35). Other semiconductors (Morita and Sugawara, 2002; Sugawara *et al.*, 1995), more ionic crystals (Bammerlin *et al.*, 1997; Bennewitz *et al.*, 2002a; Reichling and Barth, 1999, 2002), metal oxides (Barth and Reichling, 2002; Fukui and Iwasawa, 2002; Fukui *et al.*, 1997; Hosoi *et al.*, 2002; Pang and Thornton, 2002; Raza *et al.*, 1999), metals (Loppacher *et al.*, 1998; Minobe *et al.*, 1999), organic monolayers (Gotsmann *et al.*, 1998; Yamada, 2002), adsorbed molecules (Sasahara and Onishi, 2002; Sugawara, 2002) and even a film of Xenon physisorbed on graphite (Allers *et al.*, 1998) have been imaged with atomic resolution. FM-AFM can also be used for high-resolution Kelvin probe microscopy by studying the influence

of electrostatic forces on the image (Arai and Tomitori, 2002; Kitamura and Iwatsuki, 1998). Classic frequency modulation AFM provided a new tool to study problems which were not accessible by STM. Sugawara *et al.* (1995) has imaged defects in InP. While InP can be imaged by STMs, the bias voltage which is required in STM caused the defects to move. By FM-AFM, a zero-bias operation is possible which allowed to study the defects without moving them by the electric field. Yokoyama *et al.* (1999) at the same group imaged Ag on Si by FM-AFM. In Fig. 38, the α -Al₂O₃ surface in its $\sqrt{31} \times \sqrt{31}$ R + 9° high temperature reconstruction is imaged by FM-AFM. This data demonstrates the use of FM-AFM for the surface science of insulators (see also Pethica and Egdell (2001)).

B. Spectroscopy

At room temperature, lateral and vertical thermal drift usually prevents to perform spectroscopy experiments directly over a specific atom, and frequency versus distance measurements suffer from thermal drift (Giessibl, 1995). However, at low temperatures, it is possible to perform spectroscopic measurements (Allers *et al.*, 2002). Hölscher *et al.* (1999b) have performed frequency versus distance measurements with a silicon cantilever and a graphite sample with several different amplitudes and used their deconvolution algorithm to calculate the tip sample potential.

In 2001, Lantz *et al.* (2001) have performed spectroscopy over specific atomic sites on the silicon surface. Figure 39 shows three distinct sites in the silicon 7×7 unit cell, where frequency shift data was collected. Figure 40 shows the corresponding frequency shift data and the corresponding forces, calculated with the algorithm proposed by Dürig (1999b). This is a significant breakthrough, because the measured forces are mainly caused by the interaction of two single atoms (see also the perspective by de Lozanne (2001)).

X. NEW DEVELOPMENTS

A. Dissipation measurements and theory

Already in 1991, Denk and Pohl (1991) used FM-AFM and recorded the drive signal required to maintain a constant cantilever amplitude. In the distance regime covered by their early experiment, they found that the major dissipation mechanism is due to ohmic losses of

currents which are induced by the variable capacitance (due to oscillation) of the tip-sample assembly in connection with a constant tip-sample bias voltage. They obtained dissipation images on semiconductor heterostructures with a feature size of some 10 nm and coined the term ‘scanning dissipation microscopy’. Lüthi *et al.* (1997) have recorded the damping signal in atomic resolution experiments on silicon. Today, a number of theories have been proposed to explain the energy loss in dynamic AFM (Dürig, 1999a; Gauthier and Tsukada, 1999; Kantorovich, 2001; Sasaki and Tsukada, 2000). Recently, also dissipative *lateral* forces have been studied, see Pfeiffer *et al.* (2002) and below.

B. Off-resonance technique with small amplitudes

Pethica has early identified the problem of the long-range background forces and has searched for a way to minimize them (AFM challenge number 3, see III). In dynamic force microscopy, the contribution of various force components F_i with a corresponding range λ_i to the imaging signal is a function of the cantilever oscillation amplitude A . For $A \gg \lambda$, the imaging signal is proportional to $\sum_i F_i \sqrt{\lambda_i}$, while for $A \ll \lambda$, the imaging signal is proportional to $\sum_i F_i / \lambda_i$, see section VII.A. Thus, for small amplitudes the imaging signal is proportional to the force gradient and the weight of short-range forces is much larger than the weight of long-range forces. This has been used in an off-resonance technique by Hoffmann, Oral, Grimble, Özer, Jeffrey, and Pethica (2001b). In this technique, a tungsten cantilever with $k \approx 300$ N/m is oscillated at a frequency far below its resonance frequency with an amplitude A_0 of the order of 0.5 Å. When the cantilever comes close to the sample, the oscillation amplitude changes according to

$$A = \frac{A_0}{1 + k_{ts}/k} \quad (57)$$

with a tip-sample stiffness k_{ts} . Two other AFM challenges, namely the instability problem and the $1/f$ -noise problem are also solved because of the stiff cantilever and the dynamic mode. Conceptually, this small amplitude off-resonance technique is very attractive due to its simplicity in implementation and interpretation. A lock-in technique can be used to measure A , which improves the signal to noise ratio. The quality of the images presented is so far not as good as the quality of classic or small amplitude FM-AFM data, possibly because the scanning speed is slow and thermal drift is a problem. Ongoing work has

to show whether the image quality issues are just due to technical imperfections or more fundamental reasons. Atomic dissipation processes (Hoffmann *et al.*, 2001a) and force versus distance data (Oral *et al.*, 2001) have been measured with the technique.

C. Dynamic mode with stiff cantilevers and small amplitudes

Intuitively, the amplitudes which are used in classic FM-AFM are much too large: if a silicon atom was magnified to the size of an orange, the average distance of the cantilever used in classic non-contact AFM mode would amount to 15 m. The necessity of such large amplitudes has been outlined in section III. Intuitively, it was clear that greater sensitivity to short-range forces is achieved with small amplitudes. It was even planned to use the thermal amplitude (Giessibl, 1994) to enhance short-range force contributions. However, empirical findings showed that because of the stability issues outlined above, large amplitudes had to be used with the relatively soft cantilevers that were available. Similar detours were taken in the development of the STM in several aspects - the first STMs were insulated from external vibrations by levitation on superconducting magnets and the first STM tips were fabricated using complicated mechanical and chemical preparation techniques, while later STMs used much simpler systems for vibration insulation and tip preparation, see (Binnig, 1997, p. 59).

In FM-AFM, it was finally shown that small amplitudes do work - however only if extremely stiff cantilevers are used. After the theoretical proof of the benefits of using small amplitudes with stiff cantilevers (Giessibl *et al.*, 1999), we were trying to convince manufacturers of piezoresistive cantilevers to make devices with $k \approx 500 \text{ N/m}$ - without success. However, the theoretical findings gave us enough confidence to modify a quartz tuning fork to a quartz cantilever sensor with a stiffness of roughly 2 kN/m (qPlus sensor, see Fig. 11 and Giessibl (1996, 1998)). Already the first experiments were successful, yielding AFM images of silicon with excellent resolution. For the first time, clear features within the image of a single atom were observed (see Fig. 41). The structure of these images was interpreted to originate from the orbitals of the tip atom, the first observation of charge structure within atoms in real space (Giessibl *et al.*, 2000). Figure 41 is an image of a single silicon adatom. Silicon adatoms display a single sp^3 dangling bond sticking out perpendicular from the surface. Thus, the image of this atom is expected to be spherically symmetric with respect to the vertical axis. We interpret the image as being caused by an overlap of two sp^3 dangling

bonds from the tip with the single dangling bond from the surface, for a detailed description see Refs. Giessibl *et al.* (2001a, 2000). On the subatomic level, the image is sensitive to the chemical identity and the structural surroundings of the front atom of the tip. First attempts to engineer tips with a known symmetry are under way Giessibl *et al.* (2001b). Figure 42 is an image of a Si(111)-(7×7) surface imaged with a qPlus sensor with a [111] oriented Si tip (see section 11) with extremely small amplitudes (2.5 Å) and even positive frequency shifts, i.e. repulsive forces. The tip was found to be extremely stable compared to [001] oriented tips.

It is noted, that the claim of subatomic resolution capability is under debate. Hug *et al.* (2001) proposed that the experimental observations of subatomic resolution could be artifacts due to feedback errors. However, Giessibl *et al.* (2001c) concluded that analysis of the feedback signals rules out feedback artifacts. So far, subatomic resolution has not been reported using classic non-contact AFM. The small amplitude technique with very stiff cantilevers allows to achieve tip-sample distances close to the bulk distances and obtains single-atom images with nontrivial internal structures (subatomic resolution) on silicon (Giessibl *et al.*, 2001a) and rare-earth metal atoms (Herz *et al.*, 2003). The enhanced resolution of short-range forces as a result of using small amplitudes was confirmed experimentally by Eguchi and Hasegawa (2002).

The capacity of the stiff cantilever – small amplitude technique to image standard insulators with moderate short-range forces is shown in Fig. 43, where a KCl (001) surface is imaged with a qPlus sensor with a silicon tip.

D. Dynamic lateral force microscopy

Experiments on atomic friction became possible with the invention of the lateral force microscope, introduced in 1987 by Mate *et al.* (1987). The resolution power of the lateral force microscope has been improving steadily, opening many applications in tribology studies including high-resolution wear studies on KBr (Gnecco *et al.*, 2002). However, the observation of single atomic defects has not been achieved by quasistatic lateral force microscopy. Because of the similarity of the challenges faced by normal-force and lateral-force microscopy, the FM method has been tried and Pfeiffer *et al.* (2002) have imaged atomic steps with this technique, and recently Giessibl *et al.* (2002) have achieved true atomic res-

olution with a large-stiffness, small amplitude lateral FM-AFM (see Fig. 12). In addition to the frequency shift, the dissipated power between tip and sample has been measured as the difference between the power required for maintaining a constant amplitude when the cantilever is close to the sample and the power required when the cantilever is far away from the sample, yielding a connection to friction forces. Figure 44 shows experimental data on the conservative and dissipative force components between a single adatom on a Si surface and a single atom tip. When the cantilever is vibrating laterally directly over an adatom, almost no extra dissipation occurs, while when approaching and retracting the tip from the side, a dissipation of the order of a few eV per oscillation cycle is measured. The data is interpreted with a theory going back to Tomlinson (1929).

XI. SUMMARY AND CONCLUSIONS

Imaging flat surfaces with atomic resolution in direct space - regardless of their electrical conductivity - is standard practice now thanks to atomic force microscopy. The theoretical understanding of AFM has been advanced considerably and a direct link between the experimental observables (frequency shift, damping and average tunneling current) and the underlying physical concepts (conservative and dissipative forces) has been established. Forces can be deconvoluted from frequency shift data easily and low-temperature spectroscopy experiments show an outstanding agreement of theoretical and experimental tip-sample forces. AFM yields information about the strength and geometry of chemical bonds between single atoms.

Four techniques for atomic resolution AFM in vacuum are in use today: the classic frequency modulation technique with large amplitudes (used by most experimenters) and soft cantilevers, frequency modulation with small amplitudes and stiff cantilevers, the off resonance technique originated by the Pethica group and the amplitude modulation method. The future will show if one of the techniques will survive as an optimal method or if all or some techniques will remain in use. Lateral force microscopy with true atomic resolution has been demonstrated using the small amplitude/stiff cantilever technique.

XII. OUTLOOK

While FM-AFM is an established experimental technique, applications in surface science of insulators are just starting to emerge. AFM is still more complicated than STM, and these complications appear to deter many scientists. However, significant progress has been made in the last years, and exciting results can be expected in the field of surface science of insulators, where the AFM is a unique tool for atomic studies in direct space. The possibilities of atomic resolution AFM are overwhelming: access to the very scaffolding of matter, the chemical bond. Progress in physical understanding and subsequent simplification of the implementation and interpretation AFM has been significant over the last years. AFM offers additional observables - forces and damping - that are even vectors with three spatial components - the tunneling current in STM is a scalar entity. There are strong indications that dynamic AFM (and STM) allows the imaging of features within single-atom images attributed to atomic valence orbitals. Thus the whole field of classic STM studies could be revisited with the enhanced resolution technique.

One of the greatest challenges of AFM is the preparation of well defined tips. Like in the early days of STM, tip preparation is a black magic with recipes ranging from sputtering to controlled collisions. Because the tip is closer to the sample in AFM than in STM, the stability of the front atom is more important in AFM than in STM. Also, the chemical identity and backbond geometry of the tip is crucial in AFM. The use of nanotubes as tips appeared to be promising, however, the observations expressed in Figure 4 of Binnig and Rohrer (1987) regarding the necessity of a rigid, cone-shaped tip are to be heeded especially in AFM, where forces between tip and sample are larger than in STM.

Atomic manipulation by scanning probe microscopes is an exciting challenge. Arranging atoms on conducting surfaces has been possible by STM since a decade (Crommie *et al.*, 1993; Eigler and Schweizer, 1990; Kliewer *et al.*, 2000; Manoharan *et al.*, 2000; Meyer *et al.*, 1996). Morita and Sugawara (2002) have successfully extracted single atoms from a Si(111)-(7 × 7) surface in a controlled fashion with a force microscope. An exciting extension of this work would be possible if atoms could also be deposited with atomic precision by AFM, because the construction of e.g. one dimensional conductors or semiconductors on insulating substrates would allow to build electronic circuits consisting only of a few atoms. While it appears difficult to manipulate atoms with a probe which oscillates to and from the surface

with amplitudes of the order of 10 nm, the continuous decrease of amplitudes used in dynamic AFM might allow to move atoms in a controlled manner by AFM in the future.

ACKNOWLEDGMENTS

The author thanks Jochen Mannhart for his longtime collaboration, enthusiastic support and inspiring discussions. Special thanks to all current and former colleagues in Augsburg for their contributions: H. Bielefeldt, Ph. Feldpausch, S. Hembacher, A. Herrnberger, M. Herz, U. Mair, Th. Ottenthal, Ch. Schiller and K. Wiedenmann.

Many thanks to G. Binnig, Ch. Gerber and C. F. Quate, who have contributed in many ways to the authors work on the AFM.

The author is indebted to the following colleagues for supplying figures and for discussions: T. Akitoshi, T. Albrecht, W. Allers, A. Baratoff, C. Barth, G. Binnig, U. Dürig, R. Erlandsson, Ch. Gerber, H.-J. Güntherodt, L. Howald, H. Hug, M. Lantz, R.B. Marcus, E. Meyer, O. Ohlsson, M. Reichling, C. F. Quate, A. Schwarz, U. D. Schwarz, M. Tortonese, R. Wiesendanger.

L. Howald and D. Brändlin from Nanosurf AG have made crucial contributions to our project by providing prototypes and final versions of their frequency-to-voltage converters and fruitful discussions about FM-AFM.

Special thanks to G. Binnig, K. Dransfeld, U. Dürig, S. Fain, S. Hembacher and J. Mannhart for editorial suggestions.

This work is supported by the Bundesministerium für Bildung und Forschung (project no. 13N6918).

References

- Abdurixit, A., A. Baratoff, and E. Meyer, 1999, “Molecular dynamics simulations of dynamic force microscopy: application to the Si(111)- 7×7 surface”, *Applied Surface Science* **157**(4), 355–360.
- Abramowitz, M. and I. Stegun, 1970, 9th ed., *Handbook of Mathematical Functions* (Dover Publications, New York).
- Akamine, S., R. C. Barrett, and C. F. Quate, 1990, “Improved atomic force microscopy images using cantilevers with sharp tips”, *Appl. Phys. Lett.* **57**, 316–318.

- Albrecht, T. R., 2000, “private communication”.
- Albrecht, T. R., S. Akamine, T. E. Carver, and C. F. Quate, 1990, “Microfabrication of cantilever styli for the atomic force microscope”, *J. Vac. Sci. Technol. A* **8**, 3386–3396.
- Albrecht, T. R., P. Grutter, H. K. Horne, and D. Rugar, 1991, “Frequency modulation detection using high-Q cantilevers for enhanced force microscope sensitivity”, *J. Appl. Phys.* **69**, 668–673.
- Allers, W., A. Schwarz, and U. D. Schwarz, 2002, in *Noncontact Atomic Force Microscopy*, edited by S. Morita, R. Wiesendanger, and E. Meyer (Springer Berlin Heidelberg New York), chapter 14, 233–256.
- Allers, W., A. Schwarz, U. D. Schwarz, and R. Wiesendanger, 1999a, “Dynamic scanning force microscopy at low temperatures on a van der Waals surface: graphite (0001)”, *Applied Surface Science* **140**, 247–252.
- Allers, W., U. D. Schwarz, A. Schwarz, and R. Wiesendanger, 1998, “A scanning force microscope with atomic resolution in ultrahigh vacuum and at low temperatures”, *Rev. Sci. Instrum.* **69**, 221–225.
- Allers, W., U. D. Schwarz, A. Schwarz, and R. Wiesendanger, 1999b, “Dynamic scanning force microscopy at low temperatures on a noble-gas crystal: Atomic resolution on the xenon (111) surface”, *Europhys. Lett.* **48**, 276–279.
- Anczykowski, B., B. Gotsmann, H. Fuchs, J. P. Cleveland, and V. B. Elings, 1999, “How to measure energy dissipation in dynamic mode atomic force microscopy”, *Applied Surface Science* **140**, 376–382.
- Anczykowski, B., D. Krüger, and H. Fuchs, 1996, “Cantilever dynamics in quasiconnontact force microscopy: Spectroscopic aspects”, *Phys. Rev. B* **53**, 15485–15488.
- Arai, T. and M. Tomitori, 2002, in *Noncontact Atomic Force Microscopy*, edited by S. Morita, R. Wiesendanger, and E. Meyer (Springer Berlin Heidelberg New York), chapter 4, 79–92.
- Ashcroft, N. W. and N. D. Mermin, 1981, *Solid State Physics* (Saunders College, Philadelphia).
- Bammerlin, M., R. Lüthi, E. Meyer, A. Baratoff, J. Lü, M. Guggisberg, C. Gerber, L. Howald, and H. J. Güntherodt, 1997, “True Atomic Resolution on the Surface of an Insulator via Ultrahigh Vacuum Dynamic Force Microscopy”, *Probe Microscopy* **1**, 3–9.
- Baratoff, A., 1997, “unpublished”.
- Barth, C. and M. Reichling, 2001, “Imaging the atomic arrangements on the high-temperature reconstructed α -Al₂O₃(0001) surface”, *Nature* **414**, 54–56.

- Barth, C. and M. Reichling, 2002, in *Noncontact Atomic Force Microscopy*, edited by S. Morita, R. Wiesendanger, and E. Meyer (Springer Berlin Heidelberg New York), chapter 8, 135–146.
- Bartzke, K., T. Antrick, K.-H. Schmidt, E. Dammann, and C. Schatterny, 1993, “The needle sensor - a micromechanical detector for atomic force microscopy”, *International Journal of Optoelectronics* **8**(5/6), 669–676.
- Baym, G., 1969, *Lectures on Quantum Mechanics* (Benjamin, New York).
- Bazant, M. Z. and E. Kaxiras, 1997, “Environment-dependent interatomic potential for bulk silicon”, *Phys. Rev. B* **56**(14), 8542–8552.
- Becker, R., 1969, *Theorie der Wärme* (Springer, Berlin, New York), 3rd ed. edition.
- Bennewitz, R., M. Bammerlin, and E. Meyer, 2002a, in *Noncontact Atomic Force Microscopy*, edited by S. Morita, R. Wiesendanger, and E. Meyer (Springer Berlin Heidelberg New York), chapter 5, 93–108.
- Bennewitz, R., C. Gerber, and E. Meyer, 2000, “Proceedings of the Second International Workshop on Noncontact Atomic Force Microscopy, Pontresina, Switzerland, September 1-4, 1999”, *Applied Surface Science* **157**(4), 207–428.
- Bennewitz, R., O. Pfeiffer, S. Schär, V. Barwich, E. Meyer, and L. Kantorovich, 2002b, “Atomic corrugation in nc-AFM of alkali halides”, *Applied Surface Science* **188**, 232–237.
- Bielefeldt, H. and F. J. Giessibl, 1999, “A Simplified but Intuitive Analytical Model for Intermittent-Contact Mode Force Microscopy Based on Hertzian Mechanics”, *Surface Science* **440**, L863–L867.
- Binnig, G., 1986, “Atomic Force Microscope and Method for Imaging Surfaces with Atomic Resolution”, US Patent 4,724,318 .
- Binnig, G., 1992, “Force microscopy”, *Ultramicroscopy* **42-44**, 7–15.
- Binnig, G., 1997, *Aus dem Nichts* (Piper, München, Zürich), 2nd edition.
- Binnig, G., C. F. Quate, and C. Gerber, 1986, “Atomic Force Microscope”, *Phys. Rev. Lett.* **56**, 930–933.
- Binnig, G. and H. Rohrer, 1985, “The scanning tunneling microscope”, *Scientific American* **253**(2), 40–46.
- Binnig, G. and H. Rohrer, 1987, “Scanning tunneling microscopy - from birth to adolescence”, *Rev. Mod. Phys.* **56**, 615–625.
- Binnig, G. and H. Rohrer, 1999, “In touch with atoms”, *Rev. Mod. Phys.* **71**, S324–S330.

- Binnig, G., H. Rohrer, C. Gerber, and E. Weibel, 1982, “Surface Studies by Scanning Tunneling Microscopy”, *Phys. Rev. Lett.* **49**, 57–61.
- Binnig, G., H. Rohrer, C. Gerber, and E. Weibel, 1983, “ 7×7 Reconstruction on Si(111) Resolved in Real Space”, *Phys. Rev. Lett.* **50**, 120–123.
- Burnham, N. and R. J. Colton, 1989, “Measuring the nanomechanical and surface forces of materials using an atomic force microscope”, *J. Vac. Sci. Technol. A* **7**, 2906–2913.
- Chen, C. J., 1993, *Introduction to Scanning Tunneling Microscopy* (Oxford University Press, New York).
- Ciraci, S., A. Baratoff, and I. P. Batra, 1990, “Tip-sample interaction effects in scanning-tunneling and atomic-force microscopy”, *Phys. Rev. B* **41**, 2763–2775.
- Coulson, C. A. and R. McWeeny, 1991, *Coulson’s Valence* (Oxford University Press, New York).
- Crommie, M. F., C. P. Lutz, and D. M. Eigler, 1993, “Confinement of Electrons to Quantum Corrals on a Metal Surface”, *Science* **262**, 218–220.
- Denk, W. and D. W. Pohl, 1991, “Local electrical dissipation imaged by scanning force microscopy”, *Appl. Phys. Lett.* **59**(17), 2171–2173.
- Drakova, D., 2001, “Theoretical modelling of scanning tunneling microscopy, scanning tunneling spectroscopy and atomic force microscopy”, *Reports on Progress in Physics* **64**, 205–290.
- Dürig, U., 1999a, “Conservative and dissipative interactions in dynamic force microscopy”, *Surf. and Interf. Anal.* **27**, 467–473.
- Dürig, U., 1999b, “Relations between interaction force and frequency shift in large-amplitude dynamic force microscopy”, *Appl. Phys. Lett.* **75**, 433–435.
- Dürig, U., 2000, “Interaction sensing in dynamic force microscopy”, *New Journal of Physics* **2**, 5.1–5.12.
- Dürig, U., J. K. Gimzewski, and D. W. Pohl, 1986, “Experimental Observation of Forces Acting during Scanning Tunneling Microscopy”, *Phys. Rev. Lett.* **57**(19), 2403–2406.
- Dürig, U., H. P. Steinauer, and N. Blanc, 1997, “Dynamic force microscopy by means of the phase-controlled oscillator method”, *J. Appl. Phys.* **82**, 3641–3651.
- Dürig, U., O. Züger, and D. W. Pohl, 1990, “Observation of Metallic Adhesion Using the Scanning Tunneling Microscope”, *Phys. Rev. Lett.* **65**(3), 349–352.
- Dürig, U., O. Züger, and A. Stalder, 1992, “Interaction force detection in scanning probe microscopy: Methods and applications”, *Journal of Applied Physics* **72**(3), 1788–1798.

- Edwards, H., L. Taylor, and W. Duncan, 1997, “Fast, high resolution atomic force microscopy using a quartz tuning fork as actuator and sensor”, *J. Appl. Phys.* **82**(3), 980–984.
- Eguchi, T. and Y. Hasegawa, 2002, “High Resolution Atomic Force Microscopic Imaging of the Si(111)(7×7) Surface: Contribution of Short-Range Force to the Images”, *Phys. Rev. Lett.* **89**(26), 266105–1–4.
- Eigler, D. M. and E. K. Schweizer, 1990, “Positioning single atoms with a scanning tunnelling microscope”, *Nature* **344**, 524–526.
- Erlandsson, R., L. Olsson, and P. Martensson, 1997, “Inequivalent atoms and imaging mechanisms in ac-mode atomic-force microscopy of Si(111)7×7”, *Phys. Rev. B* **54**, R8309–R8312.
- Foster, A., A. Shluger, C. Barth, and M. Reichling, 2002, in *Noncontact Atomic Force Microscopy*, edited by S. Morita, R. Wiesendanger, and E. Meyer (Springer Berlin Heidelberg New York), chapter 17, 305–348.
- French, R. H., 2000, “Origins and Applications of London Dispersion Forces and Hamaker Constants in Ceramics”, *Journal of the American Ceramic Society* **83**(9), 2117–2146.
- Fukui, K. and Y. Iwasawa, 2002, in *Noncontact Atomic Force Microscopy*, edited by S. Morita, R. Wiesendanger, and E. Meyer (Springer Berlin Heidelberg New York), chapter 10, 167–182.
- Fukui, K., H. Onishi, and Y. Iwasawa, 1997, “Atom-Resolved Image of the TiO₂(110) Surface by Noncontact Atomic Force Microscopy”, *Phys. Rev. Lett.* **79**(21), 4202–4205.
- Garcia, R. and R. Perez, 2002, “Dynamic atomic force microscopy methods”, *Surface Science Reports* **47**, 197–301.
- Gauthier, M., L. Kantorovich, and M. Tsukada, 2002a, in *Noncontact Atomic Force Microscopy*, edited by S. Morita, R. Wiesendanger, and E. Meyer (Springer Berlin Heidelberg New York), chapter 19, 371–394.
- Gauthier, M., R. Perez, T. Arai, M. Tomitori, and M. Tsukada, 2002b, “Interplay between Nonlinearity, Scan Speed, Damping, and Electronics in Frequency Modulation Atomic-Force Microscopy”, *Phys. Rev. Lett.* **89**(14), 146104–1–4.
- Gauthier, M., N. Sasaki, and M. Tsukada, 2001, “Dynamics of the cantilever in noncontact dynamic force microscopy: The steady-state approximation and beyond”, *Phys. Rev. B* **64**(16), 085409–1–9.
- Gauthier, M. and M. Tsukada, 1999, “Theory of noncontact dissipation force microscopy”, *Phys. Rev. B* **60**(16), 11716–11722.

- Giessibl, F., C. Gerber, and G. Binnig, 1991, “A low-temperature atomic force/scanning tunneling microscope for ultrahigh vacuum”, *J. Vac. Sci. Technol. B* **9**, 984–988.
- Giessibl, F. J., 1991, *Rastertunnel- und Rasterkraftmikroskopie bei 4,2 K im Ultrahochvakuum*, Ph.D. thesis, Ludwig-Maximilians-Universität München, Germany.
- Giessibl, F. J., 1992, “Theory for an electrostatic imaging mechanism allowing atomic resolution of ionic crystals by atomic force microscopy”, *Phys. Rev. B (RC)* **45**, 13815–13818.
- Giessibl, F. J., 1994, “Atomic Force Microscopy in Ultrahigh Vacuum”, *Jpn. J. Appl. Phys.* **33**, 3726–3734.
- Giessibl, F. J., 1995, “Atomic Resolution of the Silicon (111)-(7×7) Surface by Atomic Force Microscopy”, *Science* **267**(5194), 68–71.
- Giessibl, F. J., 1996, “Vorrichtung zum berührungslosen Abtasten einer Oberfläche und Verfahren dafür”, *Offenlegungsschrift German Patent Office DE 196 33 546*.
- Giessibl, F. J., 1997, “Forces and Frequency Shifts in Atomic Resolution Dynamic Force Microscopy”, *Physical Review B* **56**, 16011–16015.
- Giessibl, F. J., 1998, “High-Speed Force Sensor for Force Microscopy and Profilometry Utilizing a Quartz Tuning Fork”, *Applied Physics Letters* **73**, 3956–3958.
- Giessibl, F. J., 2000, “Atomic Resolution on Si(111)-(7×7) by Noncontact Atomic Force Microscopy with a Force Sensor based on a Quartz Tuning Fork”, *Applied Physics Letters* **76**, 1470–1472.
- Giessibl, F. J., 2001, “A Direct Method to Calculate Tip-sample Forces from Frequency Shifts in Frequency-modulation Atomic Force Microscopy”, *Applied Physics Letters* **78**, 123–125.
- Giessibl, F. J., 2002, in *Noncontact Atomic Force Microscopy*, edited by S. Morita, R. Wiesendanger, and E. Meyer (Springer Berlin Heidelberg New York), chapter 2, 11–46.
- Giessibl, F. J. and H. Bielefeldt, 2000, “Physical Interpretation of Frequency-modulation Atomic Force Microscopy”, *Physical Review B* **61**, 9968–9971.
- Giessibl, F. J., H. Bielefeldt, S. Hembacher, and J. Mannhart, 1999, “Calculation of the Optimal Imaging Parameters for Frequency Modulation Atomic Force Microscopy”, *Applied Surface Science* **140**, 352–357.
- Giessibl, F. J., H. Bielefeldt, S. Hembacher, and J. Mannhart, 2001a, “Imaging of atomic orbitals with the atomic force microscope - experiments and simulations”, *Annalen der Physik (Leipzig)* **10**(11-12), 887–910.
- Giessibl, F. J. and G. Binnig, 1992a, Atomic Resolution of Potassium Bromide (001) with an

- Atomic Force Microscope and Calculation of Tip Shape, unpublished.
- Giessibl, F. J. and G. Binnig, 1992b, “True atomic resolution on KBr with a low-temperature atomic force microscope in ultrahigh vacuum”, *Ultramicroscopy* **42-44**, 281–286.
- Giessibl, F. J., S. Hembacher, H. Bielefeldt, and J. Mannhart, 2000, “Subatomic Features on the Silicon(111)-(7×7) Surface Observed by Atomic Force Microscopy”, *Science* **289**, 422–425.
- Giessibl, F. J., S. Hembacher, H. Bielefeldt, and J. Mannhart, 2001b, “Imaging Silicon with Crystallographically Oriented Tips by Atomic Force Microscopy”, *Applied Physics A* **72**, 15–17.
- Giessibl, F. J., S. Hembacher, H. Bielefeldt, and J. Mannhart, 2001c, “Response to Technical Comment: Subatomic Features in Atomic Force Microscopy Images”, *Science* **291**, 2509a.
- Giessibl, F. J., M. Herz, and J. Mannhart, 2002, “Friction traced to the single atom”, *Proceedings of the National Academy of Sciences (USA)* **99**(19), 12006–12010.
- Giessibl, F. J. and M. Tortonese, 1997, “Self Oscillating Mode for Frequency Modulation Non-Contact Atomic Force Microscopy”, *Applied Physics Letters* **70**, 2529–2531.
- Giessibl, F. J. and B. M. Trafton, 1994, “Piezoresistive cantilevers utilized for scanning tunneling and scanning force microscope in ultrahigh vacuum”, *Rev. Sci. Instrum.* **65**, 1923–1929.
- Gnecco, E., R. Bennewitz, and E. Meyer, 2002, “Abrasive Wear on the Atomic Scale”, *Phys. Rev. Lett.* **88**(21), 215501–1–4.
- Güntherodt, H.-J. and R. Wiesendanger (eds.), 1991, *Scanning tunneling microscopy I-III* (Springer Berlin, Heidelberg, New York).
- Goldstein, H., 1980, *Classical Mechanics* (Addison Wesley, Reading MA).
- Gotsmann, B., C. Schmidt, C. Seidel, and H. Fuchs, 1998, “Molecular resolution of an organic monolayer by dynamic AFM”, *Eur. Phys. J. B* **4**, 267–268.
- Gotsmann, B., C. Schmidt, C. Seidel, and H. Fuchs, 1999, “Determination of tip-sample interaction forces from measured dynamic force spectroscopy curves”, *Applied Surface Science* **140**(3-4), 314–319.
- Güthner, P., 1992, *Untersuchung der lokalen elektrischen Eigenschaften dünner ferroelektrischer Polymere*, Ph.D. thesis, University of Konstanz, konstanzer Dissertationen Vol. 357.
- Güthner, P., 1996, “Simultaneous imaging of Si(111) 7×7 with atomic resolution in scanning tunneling microscopy, atomic force microscopy, and atomic force microscopy noncontact mode”, *J. Vac. Sci. Technol. B* **14**, 2428–2431.
- Güthner, P., U. C. Fischer, and K. Dransfeld, 1989, “Scanning Near-Field Acoustic Microscopy”,

- Appl. Phys. B **48**, 89–92.
- Hamaker, H. C., 1937, “The London - van der Waals attraction between spherical particles”, *Physica* **4**(10), 1058–1072.
- Hartmann, U., 1991, “Theory of van der Waals microscopy”, *J. Vac. Sci. Technol. B* **9**, 465–469.
- Hembacher, S., F. J. Giessibl, and J. Mannhart, 2002, “Evaluation of a force sensor based on a quartz tuning fork for operation at low temperatures and ultra-high vacuum”, *Applied Surface Science* **188**, 445–449.
- Herz, M., F. J. Giessibl, and J. Mannhart, 2003, Probing the Shape of Atoms in Real Space, unpublished.
- Hölscher, H., 2002, in *Noncontact Atomic Force Microscopy*, edited by S. Morita, R. Wiesendanger, and E. Meyer (Springer Berlin Heidelberg New York), chapter 18, 349–370.
- Hölscher, H., W. Allers, U. D. Schwarz, A. Schwarz, and R. Wiesendanger, 1999a, “Calculation of the frequency shift in dynamic force microscopy”, *Appl. Surf. Sci.* **140**, 344–351.
- Hölscher, H., A. Schwarz, W. Allers, U. D. Schwarz, and R. Wiesendanger, 2000, “Quantitative analysis of dynamic-force-spectroscopy data on graphite(0001) in the contact and noncontact regimes”, *Physical Review B* **81**(19), 12678–12681.
- Hölscher, H., U. D. Schwarz, and R. Wiesendanger, 1999b, “Determination of Tip-Sample Interaction Potentials by Dynamic Force Spectroscopy”, *Physical Review Letters* **83**(23), 4780–4783.
- Hoffmann, P., 2003, “Proceedings of the Fifth International Conference on Noncontact Atomic Force Microscopy, Montreal, Canada, August 12-14, 2002”, *Applied Surface Science* .
- Hoffmann, P. M., S. Jeffery, J. B. Pethica, H. Özgr Özer, and A. Oral, 2001a, “Energy Dissipation in Atomic Force Microscopy and Atomic Loss Processes”, *Physical Review Letters* **87**, 265502–1–4.
- Hoffmann, P. M., A. Oral, R. A. Grimsdale, H. . Özer, S. Jeffery, and J. B. Pethica, 2001b, “Direct measurement of interatomic force gradients using an ultra-low-amplitude atomic force microscope”, *Proc. R. Soc. London A* **457**, 1161–1174.
- Horowitz, P. and W. Hill, 1989, 2nd ed., *The Art of Electronics* (Cambridge University Press, Cambridge, New York).
- Hosoi, H., K. Sueoka, K. Hayakawa, and K. Mukasa, 2002, in *Noncontact Atomic Force Microscopy*, edited by S. Morita, R. Wiesendanger, and E. Meyer (Springer Berlin Heidelberg New York), chapter 7, 125–134.
- Howald, L., 1994, *Rasterkraftmikroskopie an Silizium und Ionenkristallen im Ultrahochvakuum*,

- Ph.D. thesis, Universität Basel, Switzerland.
- Howald, L., R. Lüthi, E. Meyer, P. Güthner, and H.-J. Güntherodt, 1994, “Scanning force microscopy on the Si(111)7×7 surface reconstruction”, *Z. Phys. B* **93**, 267–268.
- Huang, M., M. Cuma, and F. Liu, 2003, Seeing the atomic orbital: First-principles study of the effect of tip geometry on atomic force microscopy, unpublished.
- Hug, H. J. and A. Baratoff, 2002, in *Noncontact Atomic Force Microscopy*, edited by S. Morita, R. Wiesendanger, and E. Meyer (Springer Berlin Heidelberg New York), chapter 20, 395–432.
- Hug, H. J., M. A. Lantz, A. Abdurixit, P. J. A. van Schendel, R. Hoffmann, P. Kappenberger, and A. Baratoff, 2001, “Technical Comment: Subatomic Features in Atomic Force Microscopy Images”, *Science* **291**, 2509a.
- Israelachvili, J., 1991, *Intermolecular and Surface Forces*, 2nd ed. (Academic Press, London).
- Itoh, T., C. Lee, and T. Suga, 1996, “Deflection detection and feedback actuation using a self-excited piezoelectric Pb(Zr,Ti)O₃ microcantilever for dynamic scanning force microscopy”, *Applied Physics Letters* **69**(14), 2036–2038.
- Jarvis, M. R., R. Prez, and M. C. Payne, 2001, “Can Atomic Force Microscopy Achieve Atomic Resolution in Contact Mode?”, *Physical Review Letters* **86**, 1287–1290.
- Jarvis, S. P., H. Tokumoto, and J. B. Pethica, 1997, “Measurement and Interpretation of Forces in the Atomic Force Microscope”, *Probe Microscopy* **1**, 65–79.
- Jarvis, S. P., H. Yamada, H. Tokumoto, and J. B. Pethica, 1996, “Direct mechanical measurement of interatomic potentials”, *Nature* **384**(6606), 247–249.
- Jeol, 2002, *JEOL UHV STM AFM*, JEOL Ltd., 1-2 Musashino 3-chome Akishima Tokyo, Japan.
- Kantorovich, L. N., 2001, “A simple non-equilibrium theory of non-contact dissipation force microscopy”, *Journal of Physics-Condensed Matter* **13**(5), 945–958.
- Karrai, K. and R. D. Grober, 1995, “Piezoelectric tip-sample distance control for near field optical microscopes”, *Appl. Phys. Lett.* **66**(14), 1842–1844.
- Ke, S. H., T. Uda, I. Stich, and K. Terakura, 2001, “First-principles simulation of atomic force microscopy image formation on a GaAs(110) surface: Effect of tip morphology”, *Phys. Rev. B* **63**, 245323.
- Ke, S.-H., T. Uda, K. Terakura, R. Perez, and I. Stich, 2002, in *Noncontact Atomic Force Microscopy*, edited by S. Morita, R. Wiesendanger, and E. Meyer (Springer Berlin Heidelberg New York), chapter 16, 279–304.

- Kitamura, S. and M. Iwatsuki, 1995, “Observation of 7×7 Reconstructed Structure on the Silicon (111) Surface using Ultrahigh Vacuum Noncontact Atomic Force Microscopy”, Jpn. J. Appl. Phys. **34**, L145–L148.
- Kitamura, S. and M. Iwatsuki, 1996, “Observation of Silicon Surfaces using Ultrahigh-Vacuum Noncontact Atomic Force Microscopy”, Jpn. J. Appl. Phys. **35**, L668–L671.
- Kitamura, S. and M. Iwatsuki, 1998, “High-resolution imaging of contact potential difference with ultrahigh-vacuum noncontact atomic force microscopy”, Appl. Phys. Lett. **72**(24), 3154–3156.
- Kliever, J., R. Berndt, and S. Crampin, 2000, “Controlled Modification of Individual Adsorbate Electronic Structure”, Phys. Rev. Lett. **85**(23), 4936–4939.
- Kobayashi, K., H. Yamada, H. Itoh, T. Horiuchi, and K. Matsushige, 2001, “Analog frequency modulation detector for dynamic force microscopy”, Rev. Sci. Instrum. **72**(12), 4383–4387.
- Krupp, H., 1967, “Particle Adhesion Theory and Experiment”, Advances Colloid Interface Sci. **1**, 111–239.
- Kuchling, H., 1982, *Taschenbuch der Physik* (Deutsch, Thun and Frankfurt/Main).
- Kuk, Y. and P. J. Silverman, 1988, “Scanning tunneling microscope instrumentation”, Reviews of Scientific Instruments **60**, 165–180.
- Landau, L. and E. M. Lifshitz, 1990, 13th ed., *Lehrbuch der Theoretischen Physik I* (Akademie Verlag, Berlin).
- Landolt-Börnstein, 1982, *Numerical Data and Functional Relationships in Science and Technology, Vol. 17a, edited by O. Madelung, M. Schultz and H. Weiss* (Springer, Berlin Heidelberg New York).
- Lantz, M., H. J. Hug, R. Hoffmann, P. van Schendel, P. Kappenberger, S. Martin, A. Baratoff, and H.-J. Güntherodt, 2001, “Quantitative Measurement of Short-range Chemical Bonding Forces”, Science **291**, 2580–2583.
- Lantz, M., H. J. Hug, P. van Schendel, R. Hoffmann, S. Martin, A. Baratoff, A. Abdurixit, and H.-J. Güntherodt, 2000, “Low Temperature Scanning Force Microscopy of the Si(111)-(77) Surface”, Phys. Rev. Lett. **84**, 2642–2645.
- Law, B. M. and F. Rieutord, 2002, “Electrostatic forces in atomic force microscopy”, Phys. Rev. B **66**, 035402–1–6.
- Livshits, A., A. Shluger, and A. Rohl, 1999a, “Contrast mechanism in non-contact SFM images of ionic surfaces”, Appl. Surf. Sci. **140**, 327–332.

- Livshits, A., A. Shluger, A. Rohl, and A. Foster, 1999b, “Model of noncontact scanning force microscopy on ionic surfaces”, *Phys. Rev. B* **59**(3), 2436–2448.
- Loppacher, C., R. Bennewitz, O. Pfeiffer, M. Guggisberg, M. Bammerlin, S. Schär, V. Barwich, A. Baratoff, and E. Meyer, 1998, “Phase variation experiments in non-contact dynamic force microscopy using phased-locked-loop techniques”, *Appl. Surf. Sci.* **140**, 287–292.
- Loppacher, C., R. Bennewitz, O. Pfeiffer, M. Guggisberg, M. Bammerlin, S. Schär, V. Barwich, A. Baratoff, and E. Meyer, 2000, “Quantitative Measurement of Short-range Chemical Bonding Forces”, *Phys. Rev. B* **62**, 13674–13679.
- de Lozanne, A., 2001, “Atomic force microscopy: You may squeeze the atoms but don’t mangle the surface!”, *Science* **291**, 2561–2562.
- Lüthi, R., E. Meyer, M. Bammerlin, A. Baratoff, L. Howald, C. Gerber, and H.-J. Güntherodt, 1997, “Ultrahigh Vacuum Atomic Force Microscopy: True Atomic Resolution”, *Surface Review and Letters* **4**(5), 1025–1029.
- Lüthi, R., E. Meyer, M. Bammerlin, T. Lehmann, L. Howald, C. Gerber, and H.-J. Güntherodt, 1996, “Atomic resolution in dynamic force microscopy across steps on Si(111)7×7”, *Z. Phys. B* **100**, 165–167.
- Manoharan, H., C. Lutz, and D. Eigler, 2000, “Quantum mirages formed by coherent projection of electronic structure”, *Nature* **403**, 512–515.
- Marcus, R., T. Ravi, T. Gmitter, K. Chin, D. Liu, W. Orvis, D. Ciarlo, C. Hunt, and J. Trujillo, 1990, “Formation of silicon tips with ≈ 1 nm radius”, *Appl. Phys. Lett.* **56**(3), 236–238.
- Martin, Y., C. C. Williams, and H. K. Wickramasinghe, 1987, “Atomic force microscope - force mapping and profiling on a sub 100-Å scale”, *J. Appl. Phys.* **61**, 4723–4729.
- Mate, M., G. M. McClelland, R. Erlandsson, and C. Chiang, 1987, “Atomic-Scale Friction of a Tungsten Tip on a Graphite Surface”, *Phys. Rev. Lett.* **59**, 1942–1945.
- McClelland, G. M., R. Erlandsson, and S. Chiang, 1987, “Atomic force microscopy: general principles and a new implementation”, *Progress in Quantitative Non-destructive Evaluation* **6B**, 1307–1314.
- Meyer, E., H. Heinzelmann, D. Brodbeck, G. Overney, L. Howald, H. Hug, T. Jung, H.-R. Hidber, and H.-J. Güntherodt, 1990a, “Atomic resolution on the surface of LiF (001) by atomic force microscopy”, *J. Vac. Sci. Technol. B* **9**, 1329–1332.
- Meyer, E., H. Heinzelmann, H. Rudin, and H.-J. Güntherodt, 1990b, “Atomic resolution on LiF

- (001) by atomic force microscopy”, Z. Phys. B **79**, 3–4.
- Meyer, G. and N. M. Amer, 1990, “Optical-beam-deflection atomic force microscopy: The NaCl(100) surface”, Appl. Phys. Lett. **56**(21), 2100–2101.
- Meyer, G., S. Zöphel, and K.-H. Rieder, 1996, “Scanning Tunneling Microscopy Manipulation of Native Substrate Atoms: A New Way to Obtain Registry Information on Foreign Adsorbates”, Phys. Rev. Lett. **77**(10), 2113–2116.
- Minobe, S. O. T., T. Uchihashi, Y. Sugawara, and S. Morita, 1999, “The atomic resolution imaging of metallic Ag(111) surface by noncontact atomic force microscopy”, Appl. Surf. Sci. **140**, 243–246.
- Mody, C., 2002, Probe Microscopists at Work and at Play: The Growth of American STM in the 1980s, unpublished.
- Momosaki, E., 1997, “A brief review of progress in quartz tuning fork resonators”, Proc. 1997 IEEE Interntl. Freq. Contr. Symp. **56**, 552–565.
- Morita, S., 2002, in *Noncontact Atomic Force Microscopy*, edited by S. Morita, R. Wiesendanger, and E. Meyer (Springer Berlin Heidelberg New York), chapter 1, 1–10.
- Morita, S. and Y. Sugawara, 2002, in *Noncontact Atomic Force Microscopy*, edited by S. Morita, R. Wiesendanger, and E. Meyer (Springer Berlin Heidelberg New York), chapter 3, 47–78.
- Morita, S. and M. Tsukada, 1999, “Proceedings of the First International Workshop on Noncontact Atomic Force Microscopy, Osaka, Japan, July 21–23, 1998”, Applied Surface Science **140**(3–4), 243–456.
- Morita, S., R. Wiesendanger, and E. Meyer (eds.), 2002, *Noncontact Atomic Force Microscopy*, Nanoscience and Technology (Springer Berlin Heidelberg New York).
- Nakagiri, N., M. Suzuki, K. Okiguchi, and H. Sugimura, 1997, “Site discrimination of adatoms in Si(111)-7×7 by noncontact atomic force microscopy”, Surface Science Letters **373**, L329–L332.
- Nanosensors, 2002, *POINTPROBE sensors*, Nanosensors AG, NANOSENSORS GmbH und Co. KG, Koogstraat 4, 25870 Norderfriedrichskoog, Germany.
- Nanosurf, 2002, *easyPLL, easyPLL Sensor Controller*, Nanosurf AG, Grammetstr. 14, CH-8804 Liestal.
- Ohnesorge, F. and G. Binnig, 1993, “True Atomic Resolution by Atomic Force Microscopy Through Repulsive and Attractive Forces”, Science **260**, 1451–1456.
- Olsson, L., N. Lin, V. Yakimov, and R. Erlandsson, 1998, “A method for *in situ* characterization

- of tip shape in ac-mode atomic force microscopy using electrostatic interaction”, J. Appl. Phys. **84**, 4060–4064.
- Olympus, 2002, *Olympus microcantilever*, OLYMPUS Opt.Co.,LTD., 2951 Ishikawa-cho Hachioji Tokyo 192-8507 Japan.
- Omicron, 2002, *Omicron UHV AFM/STM*, Omicron Nanotechnology GmbH, Limburger Str. 75, D-65232 Taunusstein, Germany.
- Oral, A., R. A. Grimsdale, H. Özgür Özer, P. M. Hoffmann, and J. B. Pethica, 2001, “Quantitative atom-resolved force gradient imaging using noncontact atomic force microscopy”, Appl. Phys. Lett. **79**, 1915–1917.
- Pang, C. L. and G. Thornton, 2002, in *Noncontact Atomic Force Microscopy*, edited by S. Morita, R. Wiesendanger, and E. Meyer (Springer Berlin Heidelberg New York), chapter 9, 147–166.
- Park, S. I. and R. C. Barrett, 1993, in *Scanning Tunneling Microscopy*, edited by J. A. Stroscio and W. J. Kaiser (Academic Press Boston), chapter 2, 31–76.
- Patrin, J., 1995, Atomic resolution of an insulator by noncontact AFM, Presentation at the 12th International Conference on Scanning Tunneling Microscopy 1995 (Snowmass, Colorado, USA).
- Pauling, L., 1957, *The Nature of the Chemical Bond* (Cornell Univ. Press, Ithaca, New York).
- Perez, R., I. Stich, M. C. Payne, and K. Terakura, 1997, “Role of Covalent Tip-Surface Interactions in Noncontact Atomic Force Microscopy on Reactive Surfaces”, Phys. Rev. Lett. **78**, 678–681.
- Perez, R., I. Stich, M. C. Payne, and K. Terakura, 1998, “Surface-tip interactions in noncontact atomic-force microscopy on reactive surfaces: Si(111)”, Phys. Rev. B **58**, 10835–10849.
- Pethica, J. B., 1986, “Comment on ‘Interatomic Forces in Scanning Tunneling Microscopy: Giant Corrugations of the Graphite Surface ’”, Phys. Rev. Lett. **57**, 3225.
- Pethica, J. B. and R. Egdell, 2001, “The insulator uncovered”, Nature **414**, 27–29.
- Pfeiffer, O., R. Bennewitz, A. Baratoff, and E. Meyer, 2002, “Lateral-force measurements in dynamic force microscopy”, Phys. Rev. B **65**, 161403(R)–1–4.
- Raza, H., C. L. Pang, S. A. Haycock, and G. Thornton, 1999, “Evidence of Concrete Bond Breaking Steps in the 1×1 to 1×3 Phase transition of $\text{TiO}_2(100)$ ”, Phys. Rev. Lett. **82**, 5265–5268.
- Reichling, M. and C. Barth, 1999, “Scanning Force Imaging of Atomic Size Defects on the $\text{CaF}_2(111)$ Surface”, Phys. Rev. Lett. **83**, 768–771.
- Reichling, M. and C. Barth, 2002, in *Noncontact Atomic Force Microscopy*, edited by S. Morita, R. Wiesendanger, and E. Meyer (Springer Berlin Heidelberg New York), chapter 6, 109–124.

- Rensen, W. H. J., N. F. van der Hulst, A. G. T. Ruiter, and P. E. West, 1999, “Atomic steps with tuning-fork-based noncontact atomic force microscopy”, *Appl. Phys. Lett.* **75**(11), 1640–1642.
- Rugar, D. and P. Hansma, 1990, “Atomic force microscopy”, *Physics Today* **43**(10), 23–30.
- Ruiter, A., J. Veerman, K. O. van der Werf, and N. van Hulst, 1997, “Dynamic behavior of tuning fork shear-force feedback”, *Appl. Phys. Lett.* **71**(1), 28–30.
- Rychen, J., T. Ihn, P. Studerus, A. Herrmann, and K. Ensslin, 1999, “A low-temperature dynamic mode scanning force microscope operating in high magnetic fields”, *Rev. Sci. Instr.* **70**(6), 2765–2768.
- Sarid, D., 1994, 2nd ed., *Scanning Force Microscopy* (Oxford University Press, New York).
- Sasahara, A. and H. Onishi, 2002, in *Noncontact Atomic Force Microscopy*, edited by S. Morita, R. Wiesendanger, and E. Meyer (Springer Berlin Heidelberg New York), chapter 13, 215–232.
- Sasaki, N. and M. Tsukada, 1998, “The Relation between Resonance Curves and Tip-Surface Interaction Potential in Noncontact Atomic-Force Microscopy”, *Jpn. J. Appl. Phys.* **37**, L533–L535.
- Sasaki, N. and M. Tsukada, 1999, “Theory for the effect of the tip-surface interaction potential on atomic resolution in forced vibration system of noncontact AFM”, *Appl. Surf. Sci.* **140**, 339–343.
- Sasaki, N. and M. Tsukada, 2000, “Effect of microscopic nonconservative process on noncontact atomic force microscopy”, *Jpn. J. Appl. Phys.* **39**(12B), L1334–L1337.
- Schiller, C., 2003, Crystallographically oriented tips for scanning probe microscopes, Diploma thesis, University of Augsburg.
- Schimmel, T., T. Koch, J. Küppers, and M. Lux-Steiner, 1999, “True atomic resolution under ambient conditions obtained by atomic force microscopy in the contact mode”, *Appl. Phys. A* **68**, 399–402.
- Schirmeisen, A., G. Cross, A. Stalder, P. Grütter, and U. Dürig, 2000, “Metallic adhesion and tunnelling at the atomic scale”, *New Journal of Physics* **2**, 29.1–29.10.
- Schwarz, A., W. Allers, U. Schwarz, and R. Wiesendanger, 1999, “Simultaneous imaging of the In and As sublattice on InAs(110)-(1×1) with dynamic scanning force microscopy”, *Appl. Surf. Sci.* **140**, 293–297.
- Schwarz, U. D., H. Hölscher, and R. Wiesendanger, 2001, “Proceedings of the Third International Conference on Non-Contact Atomic Force Microscopy, Hamburg, Germany, July 16-19, 2000”, *Applied Physics A* **72**(Supplement), S1–S141.

- Shluger, A. L., L. N. Kantorovich, A. I. Livshits, and M. J. Gillan, 1997, “Ionic and electronic processes at ionic surfaces induced by atomic-force-microscope tips”, *Phys. Rev. B* **56**(23), 15332–15344.
- Shluger, A. L., A. I. Livshits, A. S. Foster, and C. R. A. Catlow, 1999, “Models of image contrast in scanning force microscopy on insulators”, *J. Phys.: Condens. Matter* **11**, R295–R322.
- Smith, D. P. E., 1995, “Limits of force microscopy”, *Review of Scientific Instruments* **66**(5), 3191–3195.
- Sokolov, I. Y., G. S. Henderson, and F. J. Wicks, 1999, “Pseudo-non-contact AFM imaging?”, *Appl. Surf. Sci.* **140**, 362–365.
- Stillinger, F. H. and T. A. Weber, 1985, “Computer simulation of local order in condensed phases of silicon”, *Phys. Rev. B* **31**(8), 5262–5271.
- Stroscio, J. A. and W. J. Kaiser (eds.), 1994, *Scanning tunneling microscopy, 2nd ed.* (Academic Press Boston 1993).
- Sugawara, Y., 2002, in *Noncontact Atomic Force Microscopy*, edited by S. Morita, R. Wiesendanger, and E. Meyer (Springer Berlin Heidelberg New York), chapter 11, 183–192.
- Sugawara, Y., M. Ohta, H. Ueyama, and S. Morita, 1995, “Defect Motion on an InP(110) Surface Observed with Noncontact Atomic Force Microscopy”, *Science* **270**, 1646–1648.
- Sugawara, Y., H. Ueyama, T. Uchihashi, M. Ohta, Y. Yanase, T. Shigematsu, M. Suzuki, and S. Morita, 1997, “”, *Materials Research Society 1996 Fall Meeting* (Boston, December 1996), *Proceedings E: Defects in Electric Materials II*, Editors: J. Michel, T. Kennedy, K. Wada and K. Thonke 16.
- Tabor, D. and R. H. S. Winterton, 1969, “”, *Proc. R. Soc. London A* **312**, 435.
- Takayanagi, K., Y. Tanishiro, M. Takahashi, and S. Takahashi, 1985, “Structural analysis of Si(111)-7×7 by UHV-transmission electron diffraction and microscopy”, *J. Vac. Sci. Technol. A* **3**(3), 1502–1506.
- Tobik, J., I. Stich, and K. Terakura, 2001, “Effect of tip morphology on image formation in noncontact atomic force microscopy: InP(110)”, *Phys. Rev. B* **63**, 245324.
- Todorovic, M. and S. Schulz, 1998, “Magnetic force microscopy using nonoptical piezoelectric quartz tuning fork detection design with applications to magnetic recording studies”, *J. Appl. Phys.* **83**(11), 6229–6231.
- Tomlinson, G. A., 1929, “A Molecular Theory of Friction”, *Philos. Mag.* **7**(46), 905–939.

- Tortonese, M., R. C. Barrett, and C. Quate, 1993, “Atomic resolution with an atomic force microscope using piezoresistive detection”, *Appl. Phys. Lett.* **62**, 834–836.
- Tsai, D. P. and Y. Y. Lu, 1998, “Tapping-mode tuning fork force sensing for near-field scanning optical microscopy”, *Appl. Phys. Lett.* **73**(19), 2724–2726.
- Tsukada, M. and S. Morita, 2002, “Proceedings of the Forth International Conference on Noncontact Atomic Force Microscopy, Kyoto, Japan, September 21-23, 2001”, *Applied Surface Science* **188**(3-4), 231–554.
- Tsukada, M., N. Sasaki, M. Gauthier, K. Tagami, and S. Watanabe, 2002, in *Noncontact Atomic Force Microscopy*, edited by S. Morita, R. Wiesendanger, and E. Meyer (Springer Berlin Heidelberg New York), chapter 15, 257–278.
- Ueyama, H., Y. Sugawara, and S. Morita, 1998, “Stable operation mode for dynamic noncontact atomic force microscopy”, *Appl. Phys. A* **66**(Supplement), S295–S297.
- Walls, F. L., 1985, in *Precision Frequency Control*, edited by E. Gerber and A. Ballato (Academic Press, Orlando a.o.), 276–279.
- Wang, L., 1998, “Analytical descriptions of the tapping-mode atomic force microscopy response”, *Appl. Phys. Lett.* **73**(25), 3781–3783.
- Wickramasinghe, H. K., 1989, “Scanned-Probe Microscopes”, *Scientific American* **October 1989**, 74–81.
- Wiesendanger, R., 1994, *Scanning Probe Microscopy and Spectroscopy: Methods and Applications* (Cambridge University Press).
- Wiesendanger, R., 1998, *Scanning Probe Microscopy: Analytical Methods* (Springer Berlin Heidelberg New York).
- Wolter, O., T. Bayer, and J. Greschner, 1991, “Micromachined silicon sensors for scanning force microscopy”, *J. Vac. Sci. Technol.* **9**(2), 1353–1357.
- Yamada, H., 2002, in *Noncontact Atomic Force Microscopy*, edited by S. Morita, R. Wiesendanger, and E. Meyer (Springer Berlin Heidelberg New York), chapter 12, 193–214.
- Yokoyama, K., T. Ochi, Y. Sugawara, and S. Morita, 1999, “Atomically Resolved Silver Imaging on the Si(111)-($\sqrt{3} \times \sqrt{3}$)-Ag Surface Using a Noncontact Atomic Force Microscope”, *Physical Review Letters* **83**(24), 5023–5026.
- Zhong, Q., D. Innis, K. Kjoller, and V. B. Elings, 1993, “Fractured polymer silica fiber surface studied by tapping mode atomic-force microscopy”, *Surface Science* **290**, L688–L692.

Figures

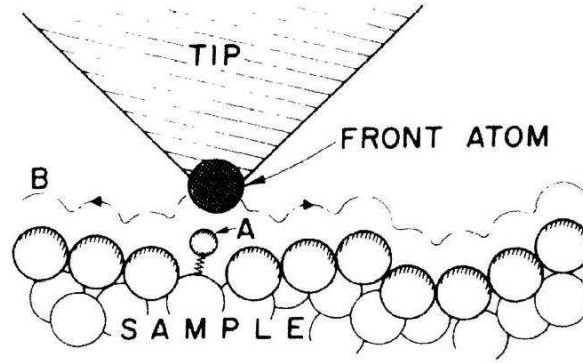


FIG. 1 STM or AFM tip close to a sample (Fig. 1a of Binnig *et al.* (1986)).

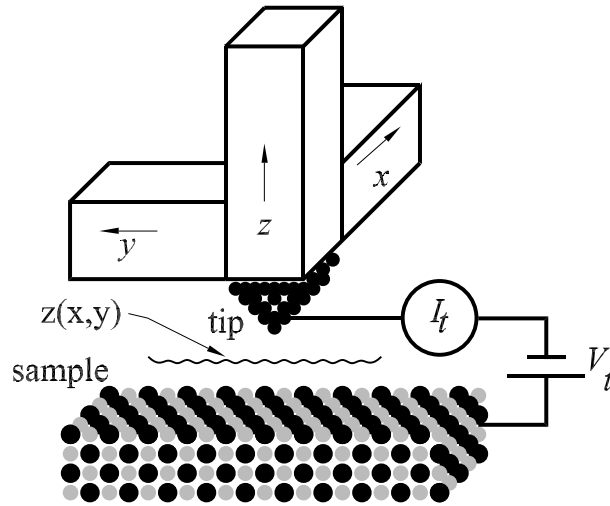


FIG. 2 A scanning tunneling microscope (schematic).

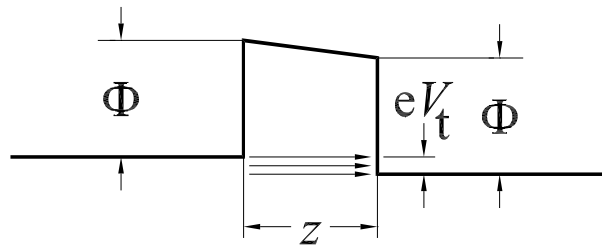


FIG. 3 Energy diagram of an idealized tunneling gap. The image charge effect (see Chen (1993)) is not taken into account here.

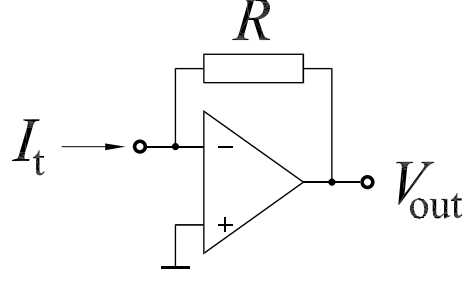


FIG. 4 A simple current-to-voltage converter for an STM and for the qPlus sensor shown in Fig. 11. It consists of an operational amplifier with high speed, low noise and low input bias current with a feedback resistor (typical impedance $R \approx 10^8 \Omega$) with low parasitic capacitance. The output voltage is given by $V_{out} = -R \times I_t$.

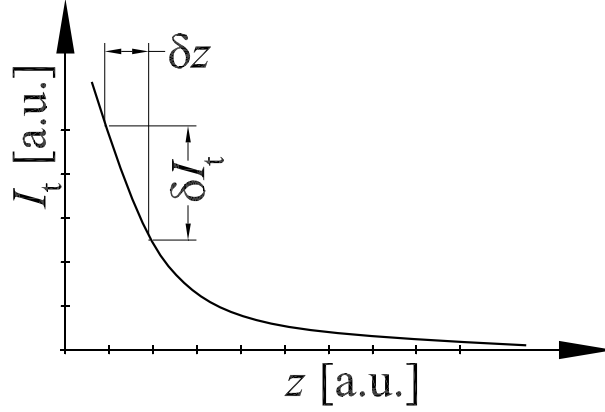


FIG. 5 Tunneling current as a function of distance and relation between current noise δI_t and vertical noise δz (arbitrary units).

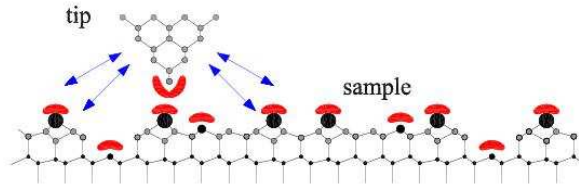


FIG. 6 Schematic view of an AFM tip close to a sample. Chemical short range forces act when tip and sample orbitals (red crescents) overlap. Long range forces (indicated with blue arrows) originate in the full volume and surface of the tip and are a critical function of the mesoscopic tip shape.

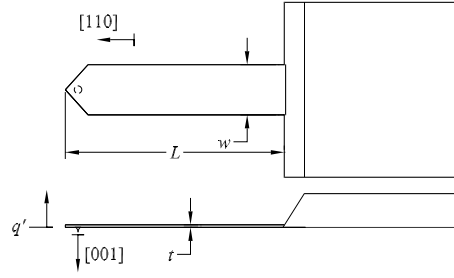


FIG. 7 Top view and side view of a microfabricated cantilever (schematic). Most cantilevers have this diving board geometry.

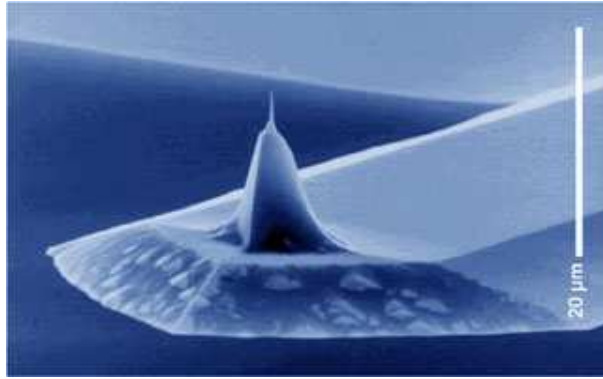


FIG. 8 Scanning electron micrograph of a micromachined silicon cantilever with an integrated tip pointing in the $[001]$ crystal direction. Source: Nanosensors (2002), see (Wolter *et al.*, 1991).

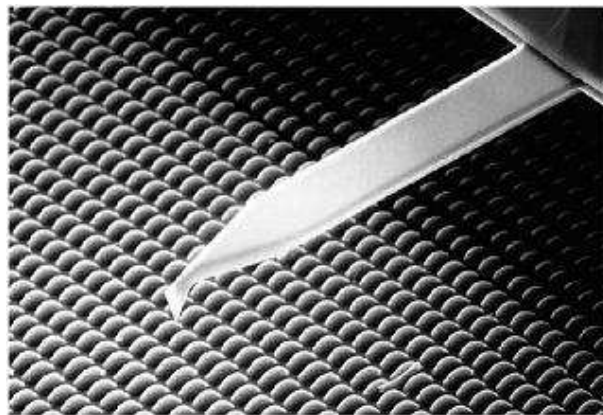


FIG. 9 Scanning electron micrograph of a micromachined silicon cantilever with an integrated tip pointing in the $[001]$ crystal direction. In this type, the tip is etched free such that the sample area which is adjacent to the tip is visible in an optical microscope. Length: $120\text{ }\mu\text{m}$, width: $30\text{ }\mu\text{m}$, thickness: $2.8\text{ }\mu\text{m}$, $k = 15\text{ N/m}$, $f_0 = 300\text{ kHz}$. Source: Olympus (2002).

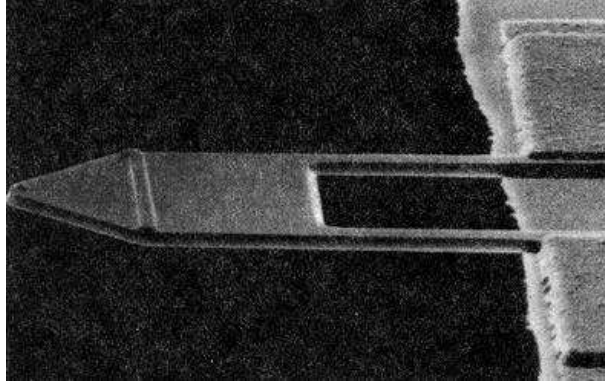


FIG. 10 Scanning electron micrograph of a piezoresistive cantilever built from silicon. Length: $250\text{ }\mu\text{m}$, full width: $80\text{ }\mu\text{m}$, thickness: $2\text{ }\mu\text{m}$. Source: Tortonese *et al.* (1993).

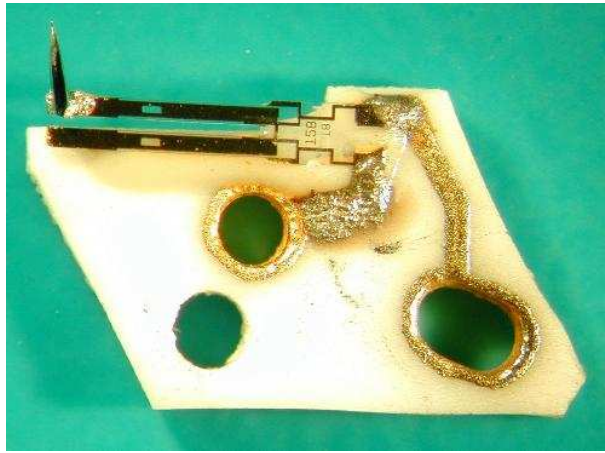


FIG. 11 Micrograph of a 'qPlus' sensor - a cantilever made from a quartz tuning fork. One of the prongs is fixed to a large substrate and a tip is mounted to the free prong. Because the fixed prong is attached to a heavy mass, the device is mechanically equivalent to a traditional cantilever. The dimensions of the free prong are: Length: $2\,400\text{ }\mu\text{m}$, width: $130\text{ }\mu\text{m}$, thickness: $214\text{ }\mu\text{m}$.

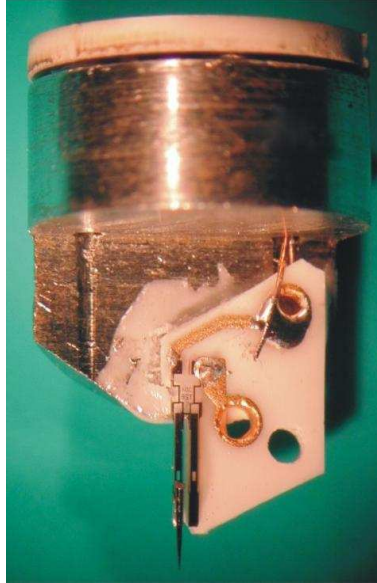


FIG. 12 Micrograph of a 'qPlus' lateral force sensor. The lateral force sensor is similar to the normal force sensor in Fig. 11. It is rotated 90° with respect to the normal force sensor and its tip is aligned parallel to the free prong.

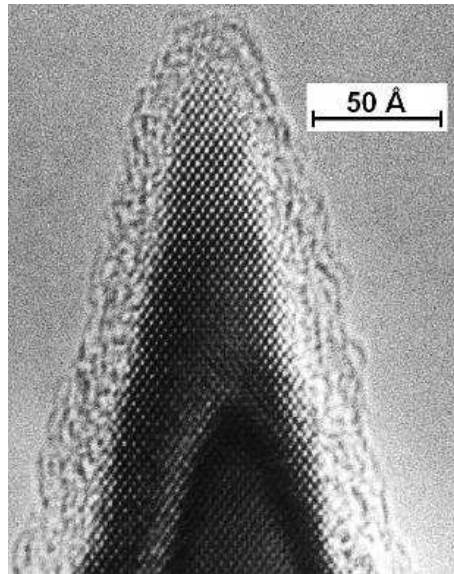


FIG. 13 Transmission Electron Micrograph of an extremely sharp silicon tip. The native oxide has been etched away with hydrofluoric acid before imaging. The $15 - 20 \text{ \AA}$ thick coating of the tip is mostly due to hydrocarbons which have been polymerized by the electron beam. Interestingly, the crystal structure appears to remain bulk-like up to the apex of the tip. Source: Marcus *et al.* (1990).

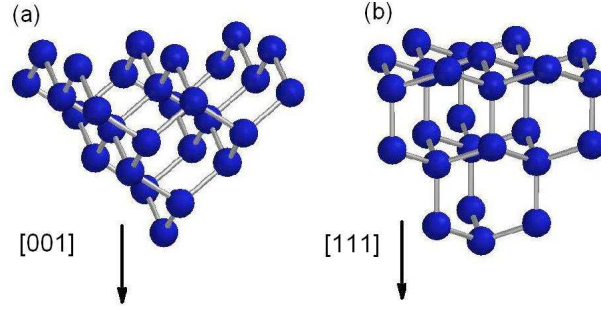


FIG. 14 Model of atomic arrangements for bulk-like terminated silicon tips, pointing in a $[001]$ direction (a) and in a $[111]$ direction (b).

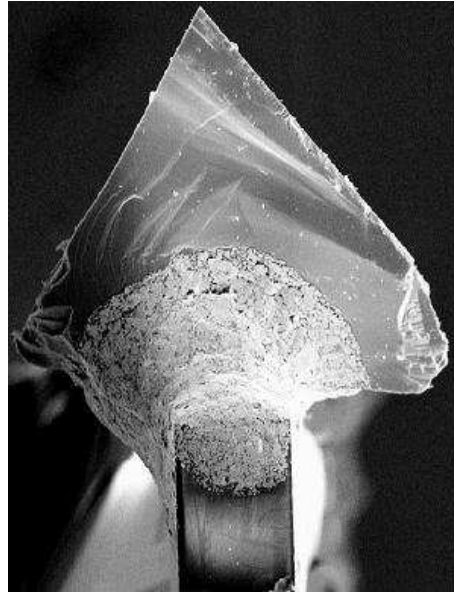


FIG. 15 Scanning Electron Micrograph of a cleaved single crystal silicon tip attached to the free prong of a qPlus sensor. The rectangular section is the end of the free prong with a width of $130\ \mu\text{m}$ and a thickness of $214\ \mu\text{m}$. The tip is pointed in the $[111]$ direction and bounded by $(\bar{1}\bar{1}\bar{1})$, $(1\bar{1}\bar{1})$ and $(\bar{1}1\bar{1})$ planes after Giessibl *et al.* (2001b). Source: Schiller (2003).

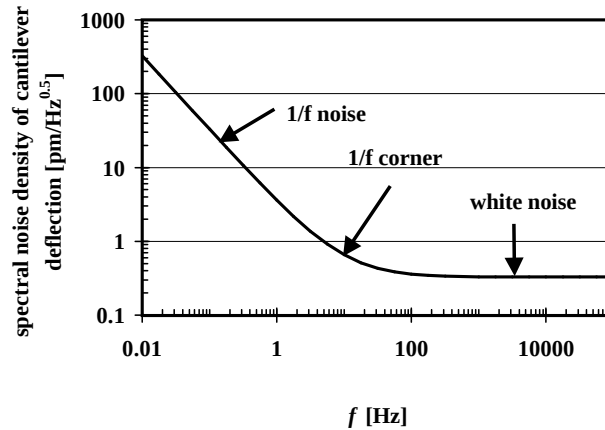


FIG. 16 Noise spectrum of a typical cantilever deflection detector (schematic), characterized by $1/f$ noise for low frequencies and white noise for intermediate frequencies. For very high frequencies, the deflection noise density of typical cantilever deflection sensors goes up again ('blue noise', not shown here).

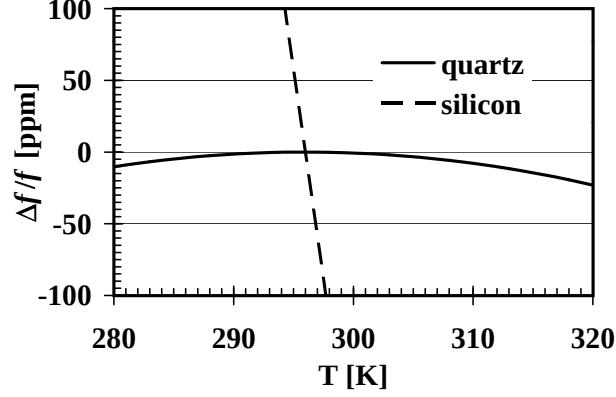


FIG. 17 Frequency variation as a function of temperature for silicon [110] oriented cantilevers and quartz tuning forks in X+5 ° -cut (see Momosaki (1997)).

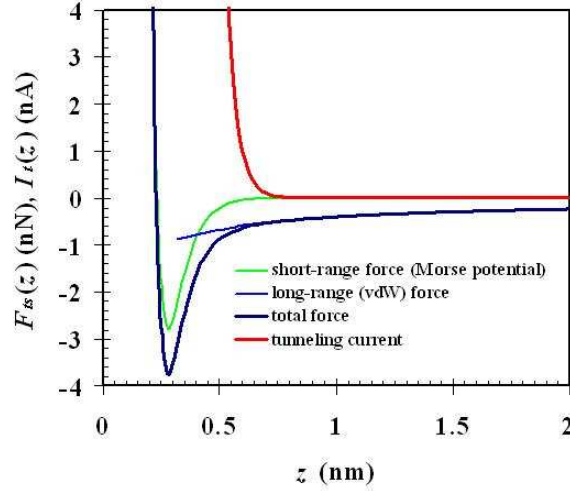


FIG. 18 Plot of tunneling current I_t and force F_{ts} (typical values) as a function of distance z between center of front atom and plane defined by the centers of surface atom layer.

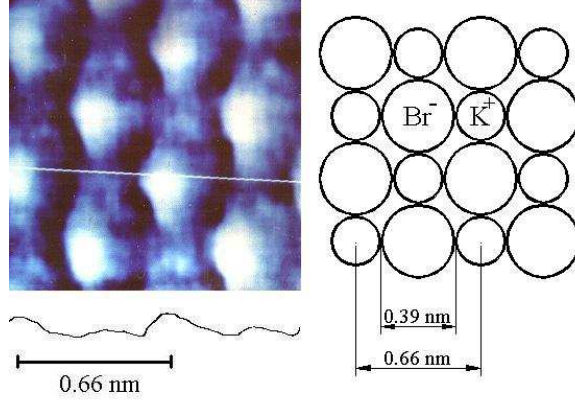


FIG. 19 Atomically resolved image of KBr (001) in contact AFM mode. The small and large protrusions are attributed to K^+ - and Br^- -ions, respectively. Source: Giessibl and Binnig (1992b).

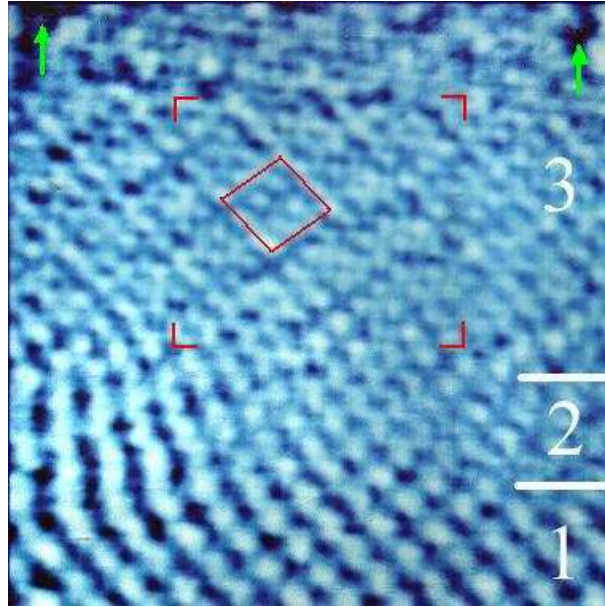


FIG. 20 Atomically resolved image of KBr (001) in contact AFM mode. Scan width 5 nm in region 1, continuously increased from 5 nm to 10 nm in region 2 and 10 nm in region 3, see text. The $\sqrt{3} \times \sqrt{3} \text{R} 45^\circ$ superstructure and the slight depression in the central $5 \text{ nm} \times 5 \text{ nm}$ area (enclosed by red angles) is probably caused by the repulsive force of 1 nN between the front atom of the tip and the sample. The red square shows the unit-cell of the $\sqrt{3} \times \sqrt{3} \text{R} 45^\circ$ reconstruction, the green arrows indicate atomic-size defects. Source: Giessibl and Binnig (1992a).

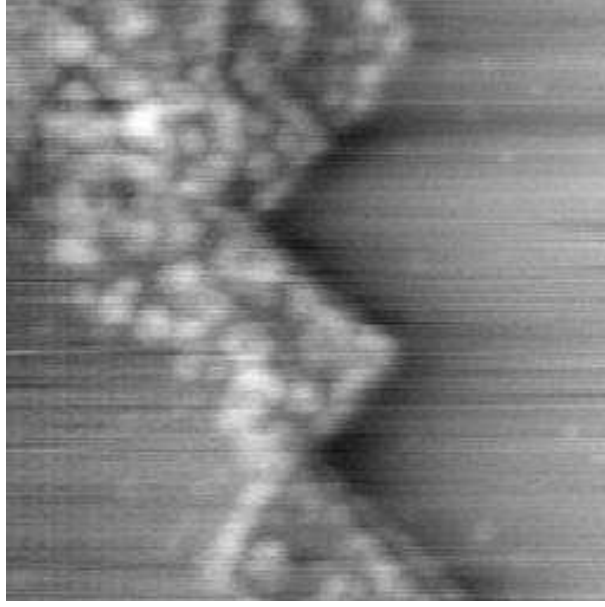


FIG. 21 non-contact AFM image of a cleavage face of KCl (001) with mono- and double steps of a height of 3.1 and 6.2 Å respectively. Image size 120 nm $\times$ 120 nm. Source: Giessibl and Trafas (1994)

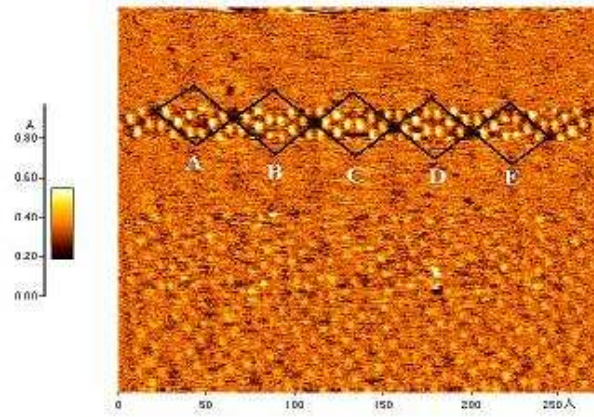


FIG. 22 First AFM image of the silicon 7 $\times$ 7 reconstruction with true atomic resolution. Parameters: $k = 17$ N/m, $f_0 = 114$ kHz, $A = 34$ nm, $\Delta f = -70$ Hz and $Q = 28\,000$. Source: Giessibl (1995)

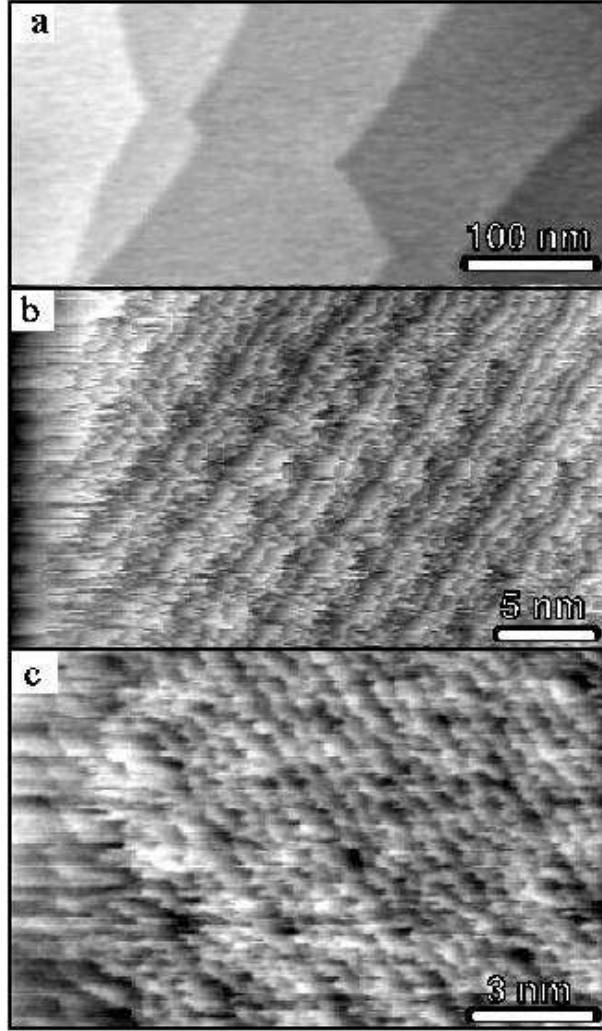


FIG. 23 (a) Normal-force image on the surface of Si(111)7 $\times$ 7. The step heights are 3 and 6 Å. (b),(c) Lateral-force image on Si(111)7 $\times$ 7. A repulsive force of 10^{-9} N is applied between the probing tip and sample. Variations of the lateral force are digitized while keeping the normal force constant. Source: Howald *et al.* (1994).

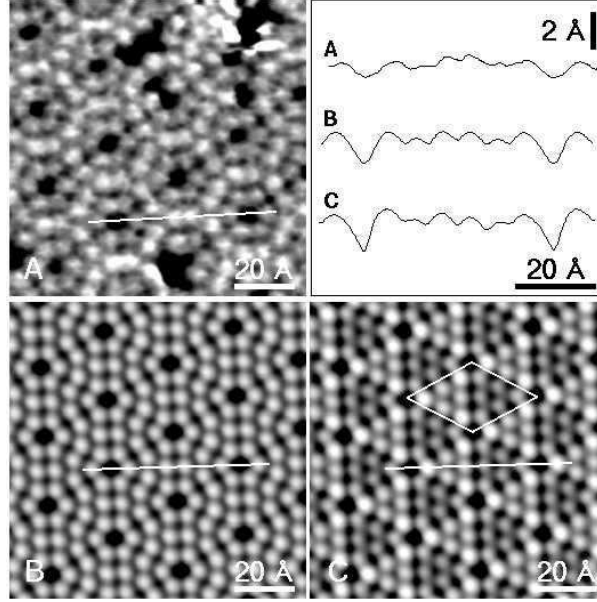


FIG. 24 AFM image of the silicon 7×7 reconstruction with AM mode. Image size $100 \text{ \AA} \times 100 \text{ \AA}$. A comparison between (A) an AFM image and (B) empty- and (C) filled-state STM images. The grey scales in the images correspond to a height difference of $1 \text{ \AA}$. The STM images were recorded with tip voltages of -2 and $+2.2 \text{ V}$, respectively, and a constant current of 0.1 nA . The AFM image has been low-pass filtered using a 3×3 convolution filter while the STM images show unfiltered data. The cross sections through the four inequivalent adatoms are obtained from raw data. The 7×7 unit cell is outlined in the filled-state STM image. The faulted and unfaulted halves correspond to the left-hand and right-hand side, respectively. Source: Erlandsson *et al.* (1997)

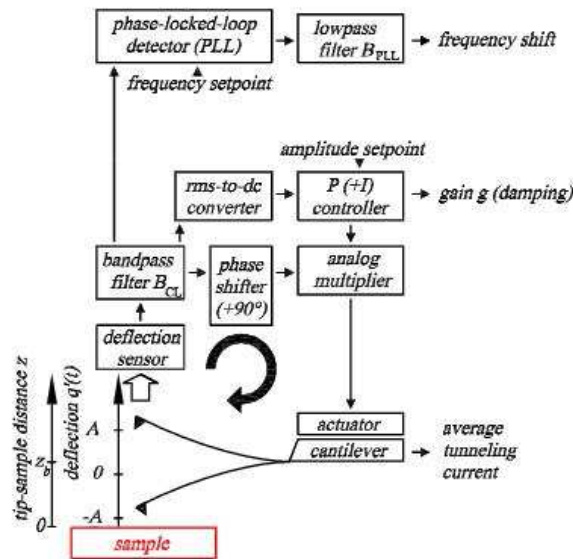


FIG. 25 Block diagram of the frequency-modulation AFM feedback loop for constant amplitude control and frequency shift measurement. Three physical observables are available: frequency shift, damping signal and (average) tunneling current.

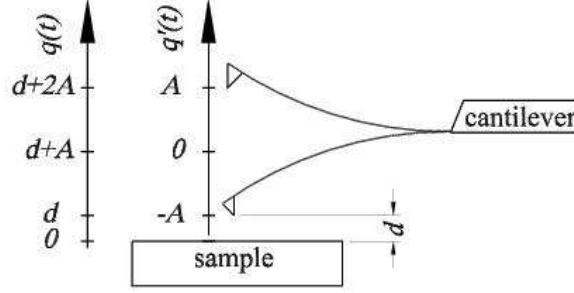


FIG. 26 Schematic view of an oscillating cantilever at its upper and lower turnaround points. The minimum tip-sample distance is d and the amplitude is A .

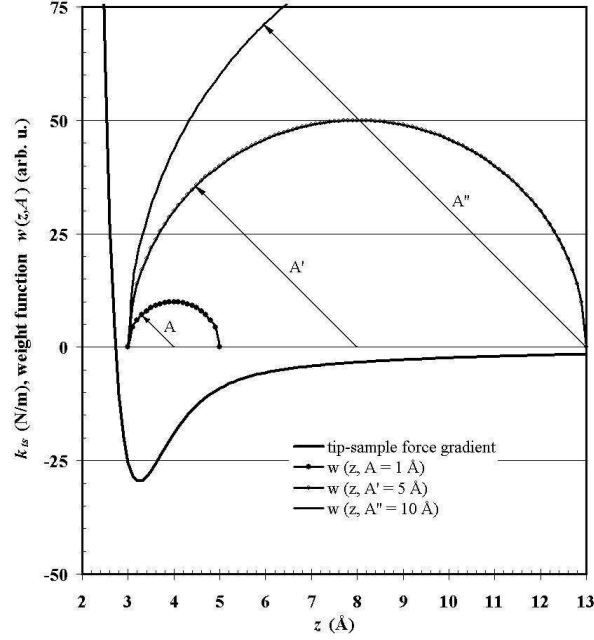


FIG. 27 Calculation of the frequency shift Δf : Δf is a convolution of a semi-spherical weight function with the tip-sample force gradient. The radius A of the weight function is equal to the oscillation amplitude of the cantilever. The weight function w is plotted in arbitrary units in this scheme – w has to be divided by $\pi A^2/2$ for normalization (see Fig. 28).

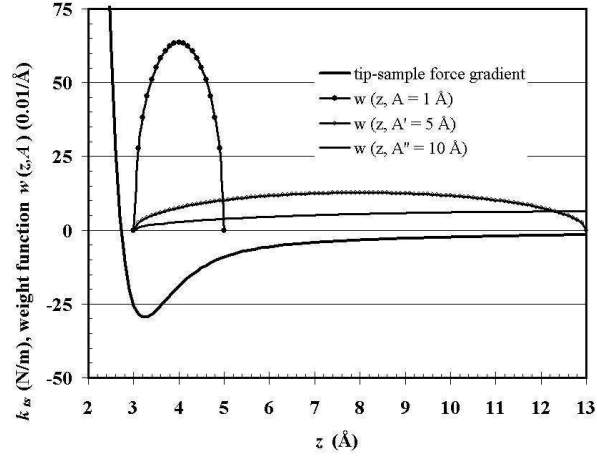


FIG. 28 Calculation of the frequency shift Δf : Δf is a convolution of a weight function w with the tip-sample force gradient. For small amplitudes, short-range interactions contribute heavily to the frequency shift, while long-range interactions are attenuated. However, for large amplitudes the long-range interactions cause the main part of the frequency shift, and short-range interactions play a minor role.

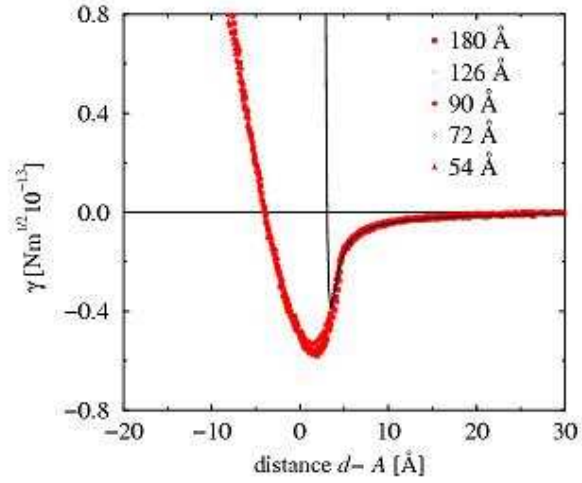


FIG. 29 Experimental normalized frequency-shift versus distance data acquired with a low-temperature UHV AFM with a graphite sample surface and a silicon cantilever. The average distance between the center of the tip's front atom and the plane defined by the centers of the surface atom layer is d , thus the minimal tip-sample distance is $d - A$. Five experimental frequency shift versus distance data sets with amplitudes from $54 \text{ \AA}$ to $180 \text{ \AA}$ are expressed in normalized frequency shift $\gamma = kA^{3/2}\Delta f/f_0$. The five experimental data sets match exactly, proving the validity of the concept of a normalized frequency shift. The black curve is a simulated $\gamma(d - A)$ -curve using a Lennard-Jones short-range force and a $1/(d - A)$ long-range force. In the repulsive regime, the deviation between the experimental dots and the simulated curve is substantial, because the $1/(d - A)^{12}$ -dependence of the repulsive Lennard-Jones potential only describes the interaction of the tip- and sample atom. The sample atom is embedded in a lattice with finite stiffness, and in particular graphite is a very soft material. Hertzian contact theory (see e.g. Chen (1993)) is an appropriate model when the repulsive forces are large enough to cause overall sample deformations. Source: Hölscher *et al.* (2000).

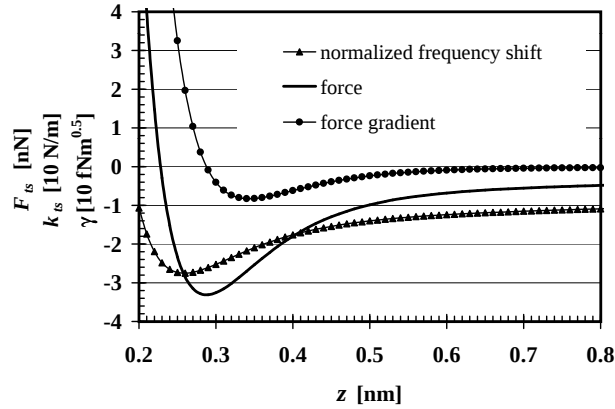


FIG. 30 Force $F_{ts}(z)$, force gradient $k_{ts}(z)$ and large-amplitude normalized frequency shift $\gamma_{LA}(z)$ for the tip-sample force defined in Eq. 38. When the cantilevers oscillation amplitude A is small compared to the range of the tip-sample forces λ , the frequency shift is proportional to the force gradient, while for $A \gg \lambda$, the frequency shift is proportional to $\gamma_{LA}(z)$.

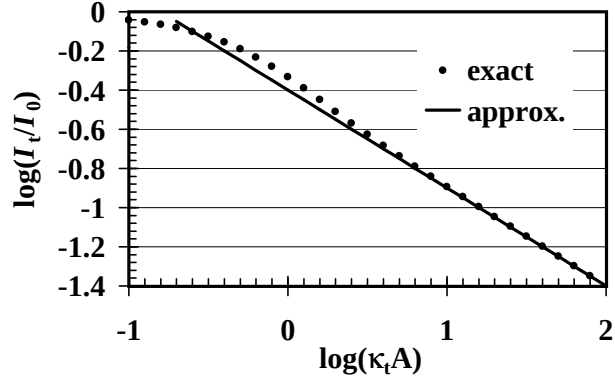


FIG. 31 Averaged tunneling current as a function of amplitude for a fixed minimum tip-sample distance.

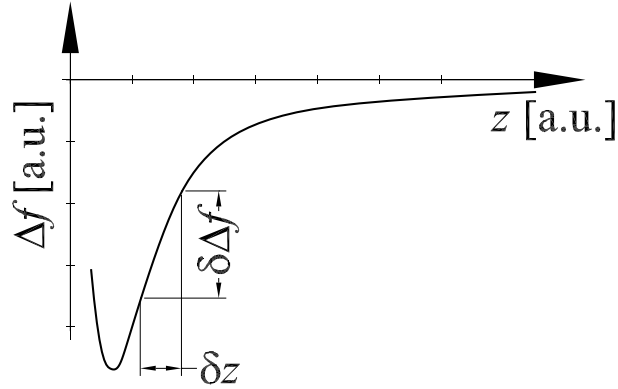


FIG. 32 Schematic plot of frequency shift Δf as a function of tip-sample distance z . The noise in the tip-sample distance measurement is given by the noise of the frequency measurement Δf divided by the slope of the frequency shift curve.

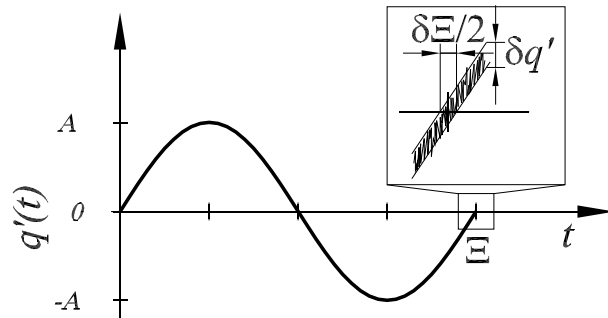


FIG. 33 Typical cantilever deflection signal as it appears on an oscilloscope. The oscillation frequency is given by the inverse time lag between two consecutive zero-crossings with positive velocity.

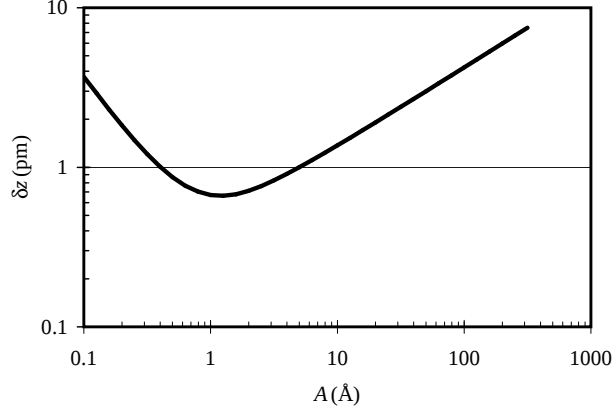


FIG. 34 Vertical noise as a function of amplitude for the tip-sample potential (Morse type) described in the text. The amplitude value where minimal noise results (here $A_{\text{optimal}} \approx 1 \text{ \AA}$) is approximately equal to the range of the tip-sample force. The absolute noise figure for this optimal amplitude is a function of bandwidth, noise performance of the cantilever deflection sensor and temperature.

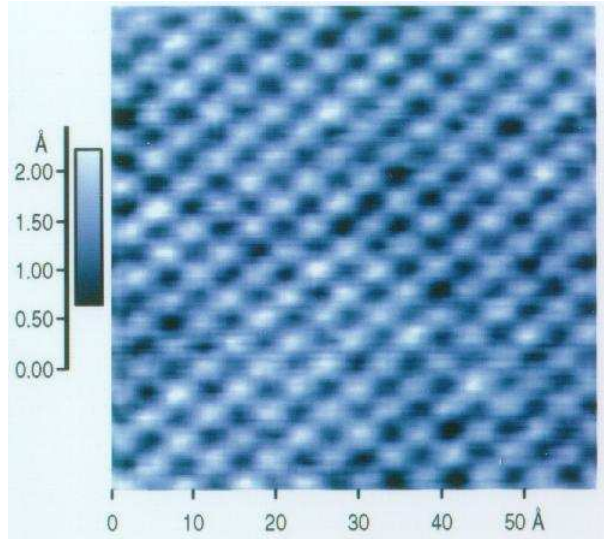


FIG. 35 First FM-AFM image of an insulator (KCl) with true atomic resolution. Instrument and parameters similar to Fig. 22. Source: Patrin (1995).

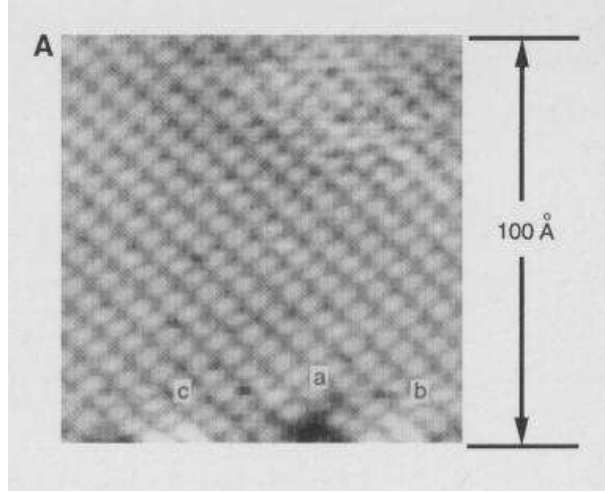


FIG. 36 Non-contact UHV AFM image of the cleaved InP(110) surface. The scan area was $100 \text{ \AA}$ by $100 \text{ \AA}$. Experimental conditions: spring constant of the cantilever $k = 34 \text{ N/m}$, mechanical resonant frequency $\nu_0 = 151 \text{ kHz}$, vibration amplitude $A = 20 \text{ nm}$ and frequency shift $\Delta\nu = -6 \text{ Hz}$. Atomic defects (a) and adsorbates (b and c) are visible. After Sugawara *et al.* (1995).

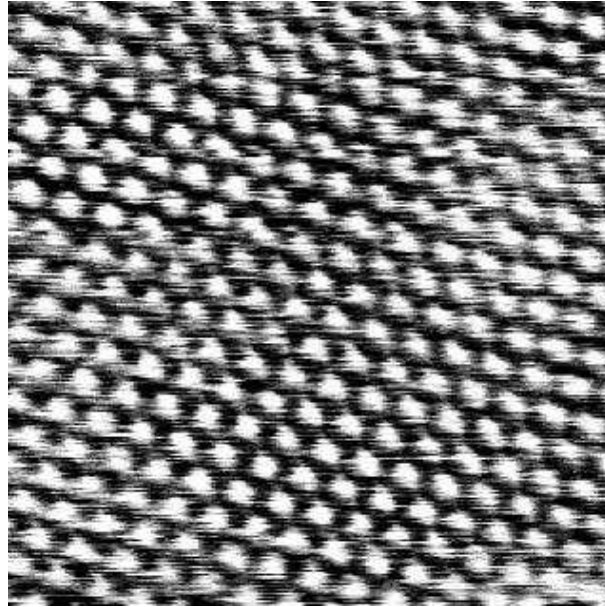


FIG. 37 FM-AFM image of a xenon thin film. Image size $70 \text{ \AA} \times 70 \text{ \AA}$. The maxima correspond to individual Xe atoms. Sputtered Si-tip, $f_0 = 160 \text{ kHz}$, $\Delta f = -92 \text{ Hz}$, $A = 9.4 \text{ nm}$, $T = 22 \text{ K}$, approx. 20 pm corrugation. Source: Allers *et al.* (1999b)

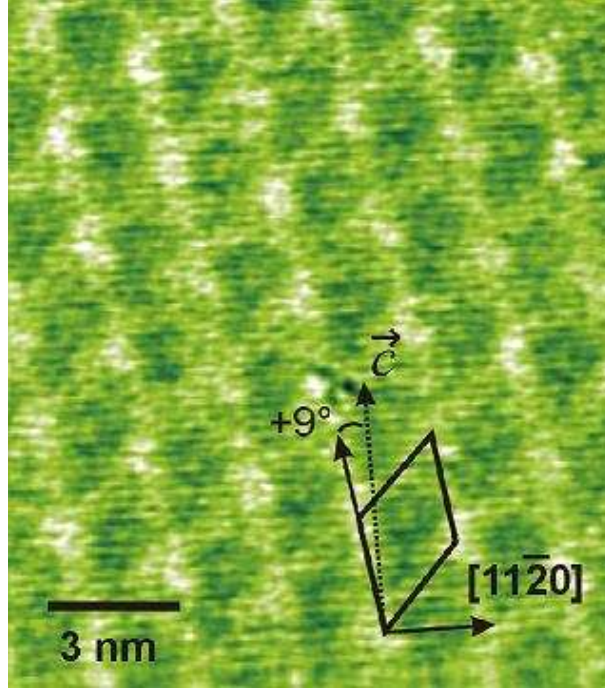


FIG. 38 FM-AFM image of an Al_2O_3 surface. Si-tip, $f_0 = 75$ kHz, $\Delta f = -92$ Hz, $k = 3$ N/m, $A = 76$ nm, ambient temperature. Source: Barth and Reichling (2001)

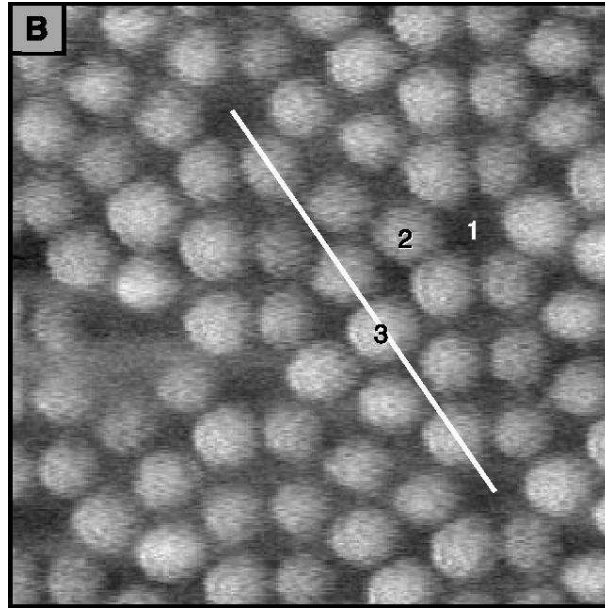


FIG. 39 $6\text{ nm} \times 6\text{ nm}$ constant frequency shift image ($\Delta f = -38$ Hz, rms error 1.15 Hz, scan speed 2 nm/s). The labels 1, 2, and 3 indicate the position of frequency distance measurements in Fig. 40. Source: Lantz *et al.* (2001).

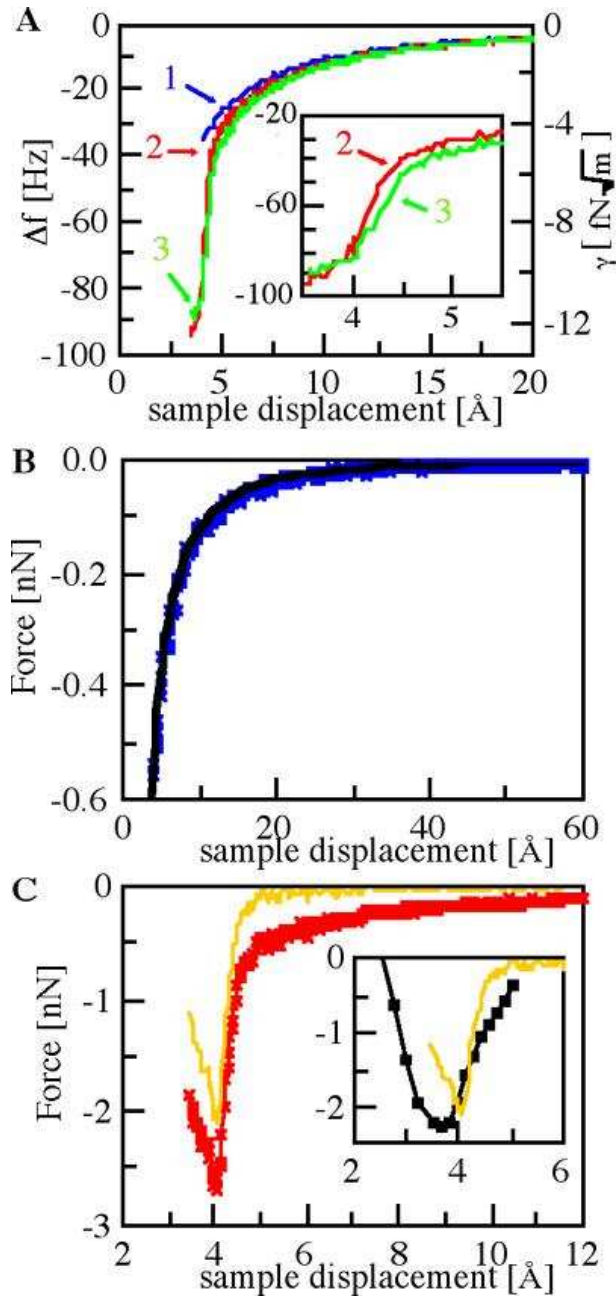


FIG. 40 Frequency shift versus distance data measured above the positions labeled 1,2 and 3 in Fig. 39. Source: Lantz *et al.* (2001).

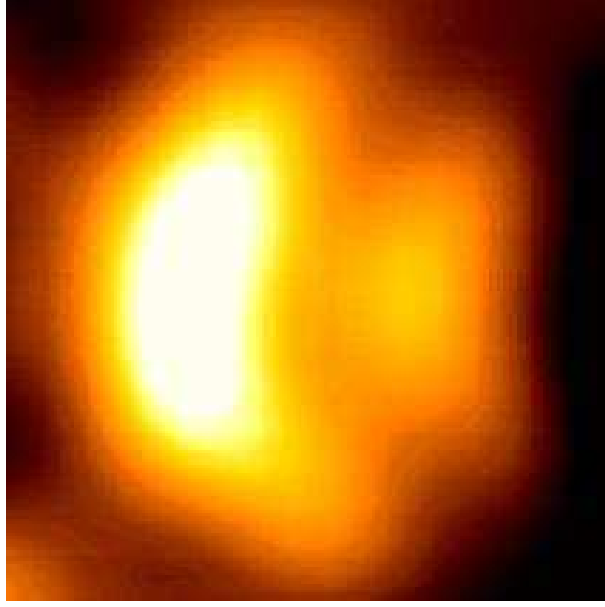


FIG. 41 Image of a single adatom on Si (111)-(7 × 7). A $3sp^3$ state points towards the surface normal on the Si (111) surface, and the image of this atom should be symmetric with respect to the z -axis. Because images in AFM are a convolution of tip and sample states, and the sample state is well known in this case, the tip state is most likely to be two $3sp^3$ states originating in a single Si tip atom, see Giessibl *et al.* (2000). Image size: $6.6 \text{ \AA} \times 6.6 \text{ \AA}$ lateral, $1.4 \text{ \AA}$ vertical.

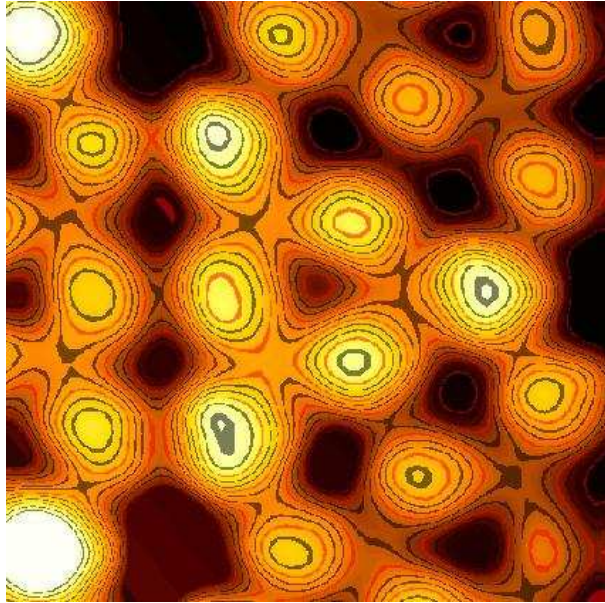


FIG. 42 Image of a Si(111)-(7×7) surface imaged with a qPlus sensor. Parameters: $k = 1800 \text{ N/m}$, $A = 2.5 \text{ \AA}$, $f_0 = 14772 \text{ Hz}$, $\Delta f = +4 \text{ Hz}$, $\gamma = 28 \text{ fN}\sqrt{\text{m}}$. Image size: $40 \text{ \AA}$ lateral, $1.4 \text{ \AA}$ vertical. Source: Giessibl *et al.* (2001a)

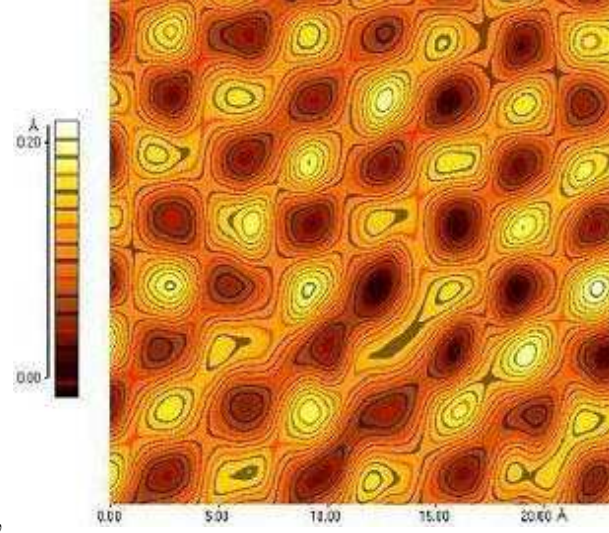


FIG. 43 Image of a KCl(001) surface imaged with a qPlus sensor. Parameters: $k = 1800 \text{ N/m}$, $A = 9 \text{ Å}$, $f_0 = 14772 \text{ Hz}$, $\Delta f = -4 \text{ Hz}$, $\gamma = -13 \text{ fN}\sqrt{\text{m}}$. Image size: 23.5 Å lateral, 0.3 Å vertical. The contour lines are spaced vertically by approximately 3 pm .

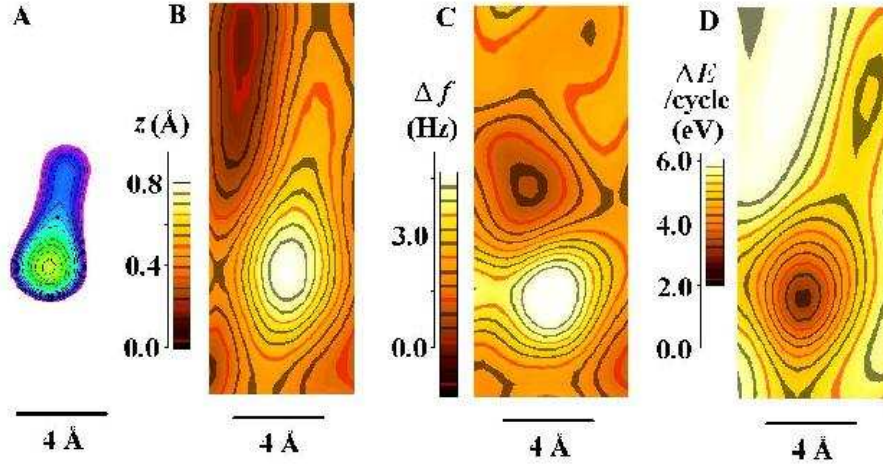


FIG. 44 Lateral force microscopy data on a single adatom on Si (111) imaged with a qPlus lateral sensor. A) Simulated constant average current topographic image, B) Experimental topographic image of a single adatom, C) Experimental data of frequency shift, D) Experimental data of dissipation energy.

Tables

year	k	f_0	Δf	A	γ	kA	E	ΔE_{CL}	sample	Ref.
------	-----	-------	------------	-----	----------	------	-----	-----------------	--------	------

	N/m	kHz	Hz	nm	fN $\sqrt{m}$	nN	keV	eV***		
1994*	2.5	60.0	-16	15.0	-1.26	37.5	1.8	0.06	KCl(001)	Giessibl and Trafas (1994)
1994*	2.5	60.0	-32	3.3	-0.29	8.25	0.1	0.4	Si(111)	Giessibl (1994)
1995	17.0	114.0	-70	34.0	-66.3	544	61	14	Si(111)	Giessibl (1995)
1995	43.0	276.0	-60	40.0	-75.6	1720	215	27	Si(111)	Kitamura and Iwatsuki (1995)
1995	34.0	151.0	-6	20.0	-3.91	680	42	5	InP(110)	Sugawara <i>et al.</i> (1995)
1996	23.5	153.0	-70	19.0	-28.8	447	27	3.3	Si(111)	Lüthi <i>et al.</i> (1996)
1996	33.0	264.0	-670	4.0	-23.6	132	12	1.45	Si(001)	Kitamura and Iwatsuki (1996)
1996	10.0	290.0	-95	10.0	-3.42	100	3.1	0.4	Si(111)	Güthner (1996)
1997	30.0	168.0	-80	13.0	-21.9	390	16	2	NaCl(001)	Bammerlin <i>et al.</i> (1997)
1997	28.0	270.0	-80	15.0	-15.7	420	20	2.5	TiO ₂ (110)	Fukui <i>et al.</i> (1997)
1997	41.0	172.0	-10	16.0	-4.96	654	33	4	Si(111)	Sugawara <i>et al.</i> (1997)
1999	35.0	160.0	-63	8.8	-10.1	338	10	1.4	HOPG(0001)	Allers <i>et al.</i> (1999a)
1999	36.0	160.0	-60.5	12.7	-18.1	457	18	2.3	InAs(110)	Schwarz <i>et al.</i> (1999)
1999	36.0	160.0	-92	9.4	-19.8	338	10	1.2	Xe(111)	Allers <i>et al.</i> (1999b)
1999	27.4	152.3	-10	11.4	-2.2	312	11	1.4	Ag(111)	Minobe <i>et al.</i> (1999)
2000	28.6	155.7	-31	5.0	-4.1	143	2.2	0.04	Si(111)	Lantz <i>et al.</i> (2000)
2000	30.0	168.0	-70	6.5	-6.6	195	4.0	0.5	Cu(111)	Loppacher <i>et al.</i> (2000)
2001	3.0	75.0	-56	76	-46.9	228	54.1	7	Al ₂ O ₃ (0001)	Barth and Reichling (2001)
2002	24.0	164.7	-8	12.0	-1.5	288	2.2	1.4	KCl _{0.6} Br _{0.4}	Bennewitz <i>et al.</i> (2002b)
2002	46.0	298.0	-20	2.8	-0.46	129	1.1	0.13	Si(111)	Eguchi and Hasegawa (2002)
2000**	1800	16.86	-160	0.8	-387	1440	3.6	11	Si(111)	Giessibl <i>et al.</i> (2000)
2001**	1800	20.53	85	0.25	+29.5	450	0.4	1	Si(111)	Giessibl <i>et al.</i> (2001a)

TABLE I Operating parameters of various FM-AFM experiments: *early experiments with nearly atomic resolution, experiments with standard parameters (classic NC-AFM) on semiconductors, metals and insulators and **small amplitude experiments. *** Internal cantilever damping calculated from $\Delta E = 2\pi E/Q$. When Q is not quoted in the original publication, a Q -value of 50 000 is used as an estimate.